

R01DS0355EJ0110 RA4M1 Group Rev.1.10

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High efficiency 48-MHz Arm® Cortex®-M4 core, 256-KB code flash memory, 32-KB SRAM, Segment LCD Controller, Capacitive Touch Sensing Unit, USB 2.0 Full-Speed Module, 14-bit A/D Converter, 12-bit D/A Converter, security and safety features

Features

■ Arm Cortex-M4 Core with Floating Point Unit (FPU)

- Armv7E-M architecture with DSP instruction set
- Maximum operating frequency: 48 MHz
- Support for 4-GB address space
- Arm Memory Protection Unit (Arm MPU) with 8 regions
- Debug and Trace: ITM, DWT, FPB, TPIU, ETB
- CoreSight™ Debug Port: JTAG-DP and SW-DP

- 256-KB code flash memory
- 8-KB data flash memory (100,000 program/erase (P/E) cycles)
- 32-KB SRAM
- Flash Cache (FCACHE)
- Memory Protection Unit (MPU)
- 128-bit unique ID

■ Connectivity

- USB 2.0 Full-Speed Module (USBFS)
 - On-chip transceiver with voltage regulator
 - Compliant with USB Battery Charging Specification 1.2
- Serial Communications Interface (SCI) × 4
 - UART
 - Simple IIC
 - Simple SPI
- Serial Peripheral Interface (SPI) × 2
- I²C bus interface (IIC) × 2
- · Controller Area Network (CAN) module
- Serial Sound Interface Enhanced (SSIE)

■ Analog

- 14-bit A/D Converter (ADC14)
- 12-bit D/A Converter (DAC12)
- 8-bit D/A Converter (DAC8) ×2 (for ACMPLP)
- Low-Power Analog Comparator (ACMPLP) × 2
- Operational Amplifier (OPAMP) × 4
- Temperature Sensor (TSN)

■ Timers

- General PWM Timer 32-Bit (GPT32) × 2
- General PWM Timer 16-Bit (GPT16) × 6
- Low Power Asynchronous General-Purpose Timer (AGT) × 2
- Watchdog Timer (WDT)

■ Safety

- Error Correction Code (ECC) in SRAM
- SRAM parity error check
- · Flash area protection
- ADC self-diagnosis function
- Clock Frequency Accuracy Measurement Circuit (CAC)
- Cyclic Redundancy Check (CRC) calculator
- Data Operation Circuit (DOC)
- Port Output Enable for GPT (POEG)
- Independent Watchdog Timer (IWDT)
- GPIO readback level detection
- Register write protection
- Main oscillator stop detection
- Illegal memory access

System and Power Management

- · Low power modes
- Realtime Clock (RTC) with calendar and Battery Backup support
- Event Link Controller (ELC)
- DMA Controller (DMAC) × 4
- Data Transfer Controller (DTC)
- Key Interrupt Function (KINT)
- Power-on reset
- · Low Voltage Detection (LVD) with voltage settings

■ Security and Encryption

- AES128/256
- GHASH
- True Random Number Generator (TRNG)

■ Human Machine Interface (HMI)

- Segment LCD Controller (SLCDC)
 - Up to 38 segments × 4 commons
- Up to 34 segments × 8 commons
- Capacitive Touch Sensing Unit (CTSU)

Multiple Clock Sources

- Main clock oscillator (MOSC)
 - (1 to 20 MHz when VCC = 2.4 to 5.5 V)
 - (1 to 8 MHz when VCC = 1.8 to 2.4 V)
- (1 to 4 MHz when VCC = 1.6 to 1.8 V)
- Sub-clock oscillator (SOSC) (32.768 kHz) • High-speed on-chip oscillator (HOCO)
- (24, 32, 48, 64 MHz when VCC = 2.4 to 5.5 V)
- (24, 32, 48 MHz when VCC = 1.8 to 5.5 V)(24, 32 MHz when VCC = 1.6 to 5.5 V)
- Middle-speed on-chip oscillator (MOCO) (8 MHz)
- Low-speed on-chip oscillator (LOCO) (32.768 kHz)
- IWDT-dedicated on-chip oscillator (15 kHz)
- Clock trim function for HOCO/MOCO/LOCO
- Clock out support

■ General Purpose I/O Ports

- Up to 84 input/output pins
 - Up to 3 CMOS input
 - Up to 81 CMOS input/output
 - Up to 9 input/output 5-V tolerant
 - Up to 2 high current (20 mA)

■ Operating Voltage

• VCC: 1.6 to 5.5 V

Operating Temperature and Packages

- $Ta = -40^{\circ}C \text{ to } +85^{\circ}C$
- 100-pin LGA (7 mm × 7 mm, 0.65 mm pitch)
- $Ta = -40^{\circ}C \text{ to } +105^{\circ}C$
- 100-pin LQFP (14 mm × 14 mm, 0.5 mm pitch)
- 64-pin LOFP (10 mm × 10 mm, 0.5 mm pitch)
- 64-pin QFN (8 mm × 8 mm, 0.4 mm pitch)
- 48-pin LQFP (7 mm × 7 mm, 0.5 mm pitch) 48-pin QFN (7 mm × 7 mm, 0.5 mm pitch)
- 40-pin QFN (6 mm × 6 mm, 0.5 mm pitch)

1. Overview

The MCU integrates multiple series of software- and pin-compatible Arm®-based 32-bit cores that share a common set of Renesas peripherals to facilitate design scalability and efficient platform-based product development.

The MCU provides an optimal combination of low-power, high-performance Arm Cortex®-M4 core running up to 48 MHz with the following features:

- 256-KB code flash memory
- 32-KB SRAM
- Segment LCD Controller (SLCDC)
- Capacitive Touch Sensing Unit (CTSU)
- USB 2.0 Full-Speed Module (USBFS)
- 14-bit A/D Converter (ADC14)
- 12-bit D/A Converter (DAC12)
- Security features.

1.1 Function Outline

Table 1.1 Arm core

Feature	Functional description
Arm Cortex-M4 core	Maximum operating frequency: up to 48 MHz Arm Cortex-M4 core Revision: r0p1-01rel0 Armv7E-M architecture profile Single precision floating-point unit compliant with the ANSI/IEEE Std 754-2008. Arm Memory Protection Unit (Arm MPU) Armv7 Protected Memory System Architecture 8 protected regions. SysTick timer Driven by SYSTICCLK (LOCO) or ICLK.

Table 1.2 Memory

Feature	Functional description
Code flash memory	Maximum 256-KB code flash memory. See section 44, Flash Memory in User's Manual.
Data flash memory	8-KB data flash memory. See section 44, Flash Memory in User's Manual.
Option-setting memory	The option-setting memory determines the state of the MCU after a reset. See section 6, Option-Setting Memory in User's Manual.
SRAM	On-chip high-speed SRAM with either parity bit or Error Correction Code (ECC). An area in SRAM0 provides error correction capability using ECC. See section 43, SRAM in User's Manual.

Table 1.3 System (1 of 2)

Feature	Functional description
Operating modes	Two operating modes: • Single-chip mode • SCI/USB boot mode. See section 3, Operating Modes in User's Manual.
Resets	14 resets: RES pin reset Power-on reset VBATT-selected voltage power-on reset Independent watchdog timer reset Voltage monitor 0 reset Voltage monitor 1 reset Voltage monitor 2 reset SRAM parity error reset SRAM ECC error reset Bus master MPU error reset Bus slave MPU error reset CPU stack pointer error reset Software reset. See section 5, Resets in User's Manual.
Low Voltage Detection (LVD)	Low Voltage Detection (LVD) function monitors the voltage level input to the VCC pin, and the detection level can be selected using a software program. See section 7, Low Voltage Detection (LVD) in User's Manual.
Clocks	Main clock oscillator (MOSC) Sub-clock oscillator (SOSC) High-speed on-chip oscillator (HOCO) Middle-speed on-chip oscillator (MOCO) Low-speed on-chip oscillator (LOCO) PLL frequency synthesizer IWDT-dedicated on-chip oscillator Clock out support. See section 8, Clock Generation Circuit in User's Manual.
Clock Frequency Accuracy Measurement Circuit (CAC)	The Clock Frequency Accuracy Measurement Circuit (CAC) counts pulses of the clock to be measured (measurement target clock) within the time generated by the clock to be used as a measurement reference (measurement reference clock), and determines the accuracy depending on whether the number of pulses is within the allowable range. When measurement is complete or the number of pulses within the time generated by the measurement reference clock is not within the allowable range, an interrupt request is generated. See section 9, Clock Frequency Accuracy Measurement Circuit (CAC) in User's Manual.
Interrupt Controller Unit (ICU)	The Interrupt Controller Unit (ICU) controls which event signals are linked to the NVIC/DTC module and DMAC module. The ICU also controls NMI interrupts. See section 13, Interrupt Controller Unit (ICU) in User's Manual.
Key Interrupt Function (KINT)	A key interrupt can be generated by setting the Key Return Mode Register (KRM) and inputting a rising or falling edge to the key interrupt input pins. See section 20, Key Interrupt Function (KINT) in User's Manual.
Low power modes	Power consumption can be reduced in multiple ways, such as by setting clock dividers, stopping modules, selecting power control mode in normal operation, and transitioning to low power modes. See section 10, Low Power Modes in User's Manual.
Battery backup function	A battery backup function is provided for partial powering by a battery. The battery powered area includes RTC, SOSC, LOCO, wakeup control, backup memory, VBATT_R low voltage detection, and switches between VCC and VBATT. During normal operation, the battery powered area is powered by the main power supply, which is the VCC pin. When a VCC voltage drop is detected, the power source is switched to the dedicated battery backup power pin, the VBATT pin. When the voltage rises again, the power source is switched from the VBATT pin to the VCC pin. See section 11, Battery Backup Function in User's Manual.
Register write protection	The register write protection function protects important registers from being overwritten because of software errors. See section 12, Register Write Protection in User's Manual.

Table 1.3 System (2 of 2)

Feature	Functional description
Memory Protection Unit (MPU)	Four Memory Protection Units (MPUs) and a CPU stack pointer monitor function are provided for memory protection. See section 15, Memory Protection Unit (MPU) in User's Manual.
Watchdog Timer (WDT)	The Watchdog Timer (WDT) is a 14-bit down-counter. It can be used to reset the MCU when the counter underflows because the system has run out of control and is unable to refresh the WDT. In addition, a non-maskable interrupt or interrupt can be generated by an underflow. A refresh-permitted period can be set to refresh the counter and used as the condition to detect when the system runs out of control. See section 25, Watchdog Timer (WDT) in User's Manual.
Independent Watchdog Timer (IWDT)	The Independent Watchdog Timer (IWDT) consists of a 14-bit down-counter that must be serviced periodically to prevent counter underflow. It can be used to reset the MCU or to generate a non-maskable interrupt/interrupt for a timer underflow. Because the timer operates with an independent, dedicated clock source, it is particularly useful in returning the MCU to a known state as a fail-safe mechanism when the system runs out of control. The IWDT can be triggered automatically on a reset, underflow, refresh error, or by a refresh of the count value in the registers. See section 26, Independent Watchdog Timer (IWDT) in User's Manual.

Table 1.4 Event link

Feature	Functional description
Event Link Controller (ELC)	The Event Link Controller (ELC) uses the interrupt requests generated by various peripheral modules as event signals to connect them to different modules, enabling direct interaction between the modules without CPU intervention. See section 18, Event Link Controller (ELC) in User's Manual.

Table 1.5 Direct memory access

Feature	Functional description
Data Transfer Controller (DTC)	A Data Transfer Controller (DTC) module is provided for transferring data when activated by an interrupt request. See section 17, Data Transfer Controller (DTC) in User's Manual.
DMA Controller (DMAC)	A 4-channel DMA Controller (DMAC) module is provided for transferring data without the CPU. When a DMA transfer request is generated, the DMAC transfers data stored at the transfer source address to the transfer destination address. See section 16, DMA Controller (DMAC) in User's Manual.

Table 1.6 Timers

Feature	Functional description
General PWM Timer (GPT)	The General PWM Timer (GPT) is a 32-bit timer with 2 channels and a 16-bit timer with 6 channels. PWM waveforms can be generated by controlling the up-counter, down-counter, or the up- and down-counter. In addition, PWM waveforms can be generated for controlling brushless DC motors. The GPT can also be used as a general-purpose timer. See section 22, General PWM Timer (GPT) in User's Manual.
Port Output Enable for GPT (POEG)	Use the Port Output Enable for GPT (POEG) function to place the General PWM Timer (GPT) output pins in the output disable state. See section 21, Port Output Enable for GPT (POEG) in User's Manual.
Low Power Asynchronous General Purpose Timer (AGT)	The Low Power Asynchronous General Purpose Timer (AGT) is a 16-bit timer that can be used for pulse output, external pulse width or period measurement, and counting of external events. This 16-bit timer consists of a reload register and a down-counter. The reload register and the down-counter are allocated to the same address, and they can be accessed with the AGT register. See section 23, Low Power Asynchronous General Purpose Timer (AGT) in User's Manual.
Realtime Clock (RTC)	The Realtime Clock (RTC) has two counting modes, calendar count mode and binary count mode, that are controlled by the register settings. For calendar count mode, the RTC has a 100-year calendar from 2000 to 2099 and automatically adjusts dates for leap years. For binary count mode, the RTC counts seconds and retains the information as a serial value. Binary count mode can be used for calendars other than the Gregorian (Western) calendar. See section 24, Realtime Clock (RTC) in User's Manual.

Table 1.7 Communication interfaces (1 of 2)

Feature	Functional description
Serial Communications Interface (SCI)	The Serial Communications Interface (SCI) is configurable to five asynchronous and synchronous serial interfaces: • Asynchronous interfaces (UART and asynchronous communications interface adapter (ACIA)) • 8-bit clock synchronous interface • Simple IIC (master-only) • Simple SPI • Smart card interface. The smart card interface complies with the ISO/IEC 7816-3 standard for electronic signals and transmission protocol. SCI0 and SCI1 have FIFO buffers to enable continuous and full-duplex communication, and the data transfer speed can be configured independently using an on-chip baud rate generator. See section 28, Serial Communications Interface (SCI) in User's Manual.
I ² C Bus Interface (IIC)	The 3-channel I ² C Bus Interface (IIC) module conforms with and provides a subset of the NXP I ² C bus (Inter-Integrated Circuit bus) interface functions. See section 29, I ² C Bus Interface (IIC) in User's Manual.
Serial Peripheral Interface (SPI)	Two independent Serial Peripheral Interface (SPI) channels are capable of high-speed, full-duplex synchronous serial communications with multiple processors and peripheral devices. See section 31, Serial Peripheral Interface (SPI) in User's Manual.
Serial Sound Interface Enhanced (SSIE)	The Serial Sound Interface Enhanced (SSIE) peripheral provides functionality to interface with digital audio devices for transmitting PCM audio data over a serial bus with the MCU. The SSIE supports an audio clock frequency of up to 50 MHz, and can be operated as a slave or master receiver, transmitter, or transceiver to suit various applications. The SSIE includes 8-stage FIFO buffers in the receiver and transmitter, and supports interrupts and DMA-driven data reception and transmission. See section 33, Serial Sound Interface Enhanced (SSIE) in User's Manual.
Controller Area Network (CAN) module	The Controller Area Network (CAN) module provides functionality to receive and transmit data using a message-based protocol between multiple slaves and masters in electromagnetically noisy applications. The CAN module complies with the ISO 11898-1 (CAN 2.0A/CAN 2.0B) standard and supports up to 32 mailboxes, which can be configured for transmission or reception in normal mailbox and FIFO modes. Both standard (11-bit) and extended (29-bit) messaging formats are supported. See section 30, Controller Area Network (CAN) Module in User's Manual.

Table 1.7 Communication interfaces (2 of 2)

Feature	Functional description
USB 2.0 Full-Speed Module (USBFS)	The USB 2.0 Full-Speed Module (USBFS) can operate as a host controller or device controller. The module supports full-speed and low-speed (only for the host controller) transfer as defined in the Universal Serial Bus Specification 2.0. The module has an internal USB transceiver and supports all of the transfer types defined in the Universal Serial Bus Specification 2.0. The USB has buffer memory for data transfer, providing a maximum of 10 pipes. Pipes 1 to 9 can be assigned any endpoint number based on the peripheral devices used for communication or based on the user system. The MCU supports revision 1.2 of the Battery Charging specification. Because the MCU can be powered at 5 V, the USB LDO regulator provides the internal USB transceiver power supply at 3.3 V. See section 27, USB 2.0 Full-Speed Module (USBFS) in User's Manual.

Table 1.8 Analog

Feature	Functional description
14-bit A/D Converter (ADC14)	A 14-bit successive approximation A/D converter is provided. Up to 25 analog input channels are selectable. Temperature sensor output and internal reference voltage are selectable for conversion. The A/D conversion accuracy is selectable from 12-bit and 14-bit conversion making it possible to optimize the tradeoff between speed and resolution in generating a digital value. See section 35, 14-Bit A/D Converter (ADC14) in User's Manual.
12-Bit D/A Converter (DAC12)	The 12-Bit D/A Converter (DAC12) converts data and includes an output amplifier. See section 36, 12-Bit D/A Converter (DAC12) in User's Manual.
8-Bit D/A Converter (DAC8) for ACMPLP	The 8-Bit D/A Converter (DAC8) converts data and does not include an output amplifier (DAC8). The DAC8 is used only as the reference voltage for ACMPLP. See section 40, 8-Bit D/A Converter (DAC8) in User's Manual.
Temperature Sensor (TSN)	The on-chip Temperature Sensor (TSN) determines and monitors the die temperature for reliable operation of the device. The sensor outputs a voltage directly proportional to the die temperature, and the relationship between the die temperature and the output voltage is linear. The output voltage is provided to the ADC14 for conversion and can be further used by the end application. See section 37, Temperature Sensor (TSN) in User's Manual.
Low-Power Analog Comparator (ACMPLP)	The Low-Power Analog Comparator (ACMPLP) compares the reference input voltage and analog input voltage. The comparison result can be read through software and also be output externally. The reference voltage can be selected from an input to the CMPREFi(i = 0,1) pin, an internal 8-bit D/A converter output, or the internal reference voltage (Vref) generated internally in the MCU. The ACMPLP response speed can be set before starting an operation. Setting the high-speed mode decreases the response delay time, but increases current consumption. Setting the low-speed mode increases the response delay time, but decreases current consumption. See section 39, Low-Power Analog Comparator (ACMPLP) in User's Manual.
Operational Amplifier (OPAMP)	The Operational Amplifier (OPAMP) amplifies small analog input voltages and outputs the amplified voltages. A total of four differential operational amplifier units with two input pins and one output pin are provided. See section 38, Operational Amplifier (OPAMP) in User's Manual.

Table 1.9 Human machine interfaces

Feature	Functional description
Segment LCD Controller (SLCDC)	The Segment LCD Controller (SLCDC) provides the following functions: • Waveform A or B selectable • The LCD driver voltage generator can switch between an internal voltage boosting method, a capacitor split method, and an external resistance division method • Automatic output of segment and common signals based on automatic display data register read • The reference voltage generated when operating the voltage boost circuit can be selected in 16 steps (contrast adjustment) • The LCD can be made to blink. See section 45, Segment LCD Controller (SLCDC) in User's Manual.
Capacitive Touch Sensing Unit (CTSU)	The Capacitive Touch Sensing Unit (CTSU) measures the electrostatic capacitance of the touch sensor. Changes in the electrostatic capacitance are determined by software, which enables the CTSU to detect whether a finger is in contact with the touch sensor. The electrode surface of the touch sensor is usually enclosed within an electrical insulator so that fingers do not come into direct contact with the electrode. See section 41, Capacitive Touch Sensing Unit (CTSU) in User's Manual.

Table 1.10 Data processing

Feature	Functional description
Cyclic Redundancy Check (CRC) calculator	The Cyclic Redundancy Check (CRC) calculator generates CRC codes to detect errors in the data. The bit order of CRC calculation results can be switched for LSB-first or MSB-first communication. Additionally, various CRC generation polynomials are available. The snoop function allows monitoring reads from and writes to specific addresses. This function is useful in applications that require CRC code to be generated automatically in certain events, such as monitoring writes to the serial transmit buffer and reads from the serial receive buffer. See section 32, Cyclic Redundancy Check (CRC) Calculator in User's Manual.
Data Operation Circuit (DOC)	The Data Operation Circuit (DOC) compares, adds, and subtracts 16-bit data. See section 42, Data Operation Circuit (DOC) in User's Manual.

Table 1.11 Security

Feature	Functional description
Secure Crypto Engine 5 (SCE5)	Security algorithm Symmetric algorithm: AES. Other support features TRNG (True Random Number Generator) Hash-value generation: GHASH.

Table 1.12 I/O ports

Feature	Functional description
I/O ports	 I/O ports for the 100-pin LQFP, 100-pin LGA - I/O pins: 81 - Input pins: 3 - Pull-up resistors: 79 - N-ch open-drain outputs: 64 - 5-V tolerance: 9 I/O ports for the 64-pin LQFP, 64-pin QFN - I/O pins: 49 - Input pins: 3 - Pull-up resistors: 47 - N-ch open-drain outputs: 36 - 5-V tolerance: 7 I/O ports for the 48-pin LQFP, 48-pin QFN - I/O pins: 33 - Input pins: 3 - Pull-up resistors: 31 - N-ch open-drain outputs: 22 - 5-V tolerance: 4 I/O ports for the 40-pin QFN - I/O pins: 25 - Input pins: 3 - Pull-up resistors: 23 - N-ch open-drain outputs: 15 - 5-V tolerance: 2

1.2 Block Diagram

Figure 1.1 shows a block diagram of the MCU superset. Some individual devices within the group have a subset of the features.

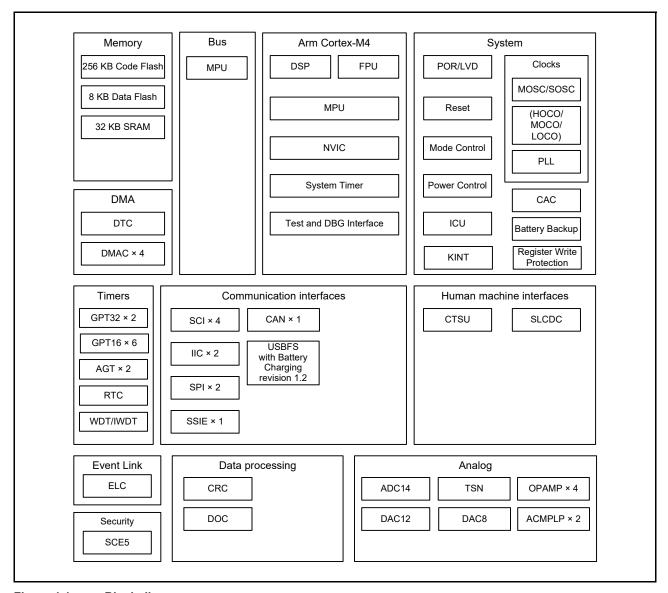


Figure 1.1 Block diagram

1.3 Part Numbering

Figure 1.2 shows the product part number information, including memory capacity, and package type. Table 1.13 shows a product list.

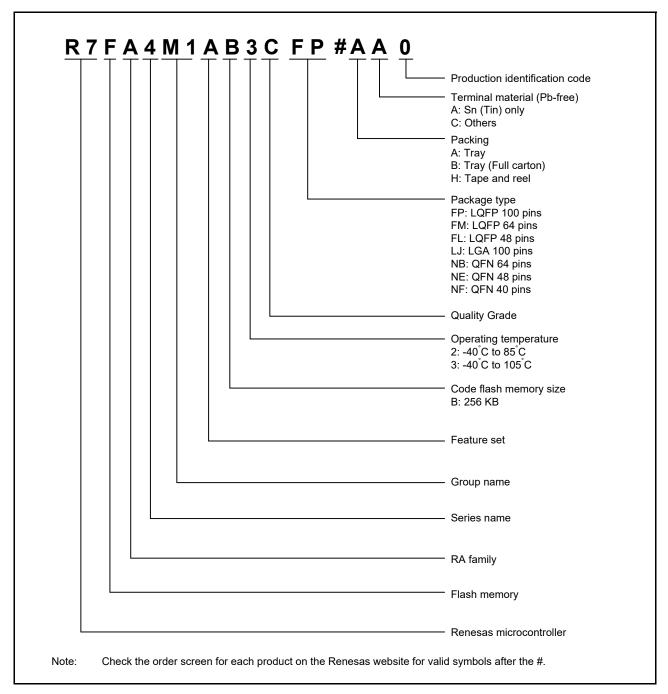


Figure 1.2 Part numbering scheme

Table 1.13 Product list

Product part number	Package code	Code flash	Data flash	SRAM	Operating temperature
R7FA4M1AB3CFP	PLQP0100KB-B	256 KB	8 KB	32 KB	-40 to +105°C
R7FA4M1AB2CLJ	PTLG0100JA-A				-40 to +85°C
R7FA4M1AB3CFM	PLQP0064KB-C				-40 to +105°C
R7FA4M1AB3CNB	PWQN0064LA-A				-40 to +105°C
	PWQN0064LB-B				
R7FA4M1AB3CFL	PLQP0048KB-B				-40 to +105°C
R7FA4M1AB3CNE	PWQN0048KB-A				-40 to +105°C
	PWQN0048KC-A				
R7FA4M1AB3CNF	PWQN0040KC-A				-40 to +105°C
	PWQN0040KD-A				

1.4 Function Comparison

Table 1.14 Function comparison

Part numbers		R7FA4M1AB3CFP	R7FA4M1AB2CLJ	R7FA4M1AB3CFM/ R7FA4M1AB3CNB	R7FA4M1AB3CFL/ R7FA4M1AB3CNE	R7FA4M1AB3CNF								
Pin count		100	100	64	48	40								
Package		LQFP	LGA	LQFP/QFN	LQFP/QFN	QFN								
Code flash memo	ory			256 KB										
Data flash memo	ory			8 KB										
SRAM				32 KB										
	Parity			16 KB										
	ECC			16 KB										
System	CPU clock			48 MHz										
	Backup registers			512 bytes	512 bytes									
	ICU			Yes										
	KINT		8		5	3								
Event control	ELC			Yes										
DMA	DTC			Yes										
	DMAC	4 No												
Bus	External bus													
Timers	GPT32			2										
	GPT16		4	2										
	AGT		2			No								
Communication	RTC	Yes												
	WDT/IWDT	Yes												
	SCI	4												
	IIC			2										
	SPI			2		1								
	SSIE		1		No									
	QSPI			No										
	SDHI			No										
	CAN			1										
	USBFS			Yes										
Analog	ADC14		25	18	14	11								
	DAC12			1										
	DAC8			2										
	ACMPLP			2		1								
	OPAMP	4	4	3	1	No								
	TSN			Yes										
НМІ	SLCDC	4 com × 38 se	eg or 8 com × 34 seg	4 com × 21 seg or 8 com × 17 seg		No								
	CTSU		27	24	15	10								
Data	CRC			Yes										
processing	DOC			Yes										
Security				SCE5										
I/O ports	I/O pins		81	49	33	25								
	Input pins		3	3	3	3								
	Pull-up resistors		79	47	31	23								
	N-ch open- drain outputs		64	36	36 22									
	5-V tolerance		9	7	4	2								

1.5 Pin Functions

Table 1.15 Pin functions (1 of 4)

Function	Signal	I/O	Description
Power supply	VCC	Input	Power supply pin. Connect this pin to the system power supply. Connect it to VSS through a 0.1-μF capacitor. The capacitor should be placed close to the pin.
	VCL	I/O	Connect this pin to the VSS pin through the smoothing capacitor used to stabilize the internal power supply. Place the capacitor close to the pin.
	VSS	Input	Ground pin. Connect to the system power supply (0 V).
	VBATT	Input	Backup power supply pin
Clock	XTAL	Output	Pins for a crystal resonator. An external clock signal can be input through the
	EXTAL	Input	EXTAL pin.
	XCIN	Input	Input/output pins for the sub-clock oscillator. Connect a crystal resonator
	XCOUT	Output	between XCOUT and XCIN.
	CLKOUT	Output	Clock output pin
Operating mode control	MD	Input	Pins for setting the operating mode. The signal levels on these pins must not be changed during operation mode transition on release from the reset state
System control	RES	Input	Reset signal input pin. The MCU enters the reset state when this signal goes low.
CAC	CACREF	Input	Measurement reference clock input pin
Interrupt	NMI	Input	Non-maskable interrupt request pin
	IRQ0 to IRQ12, IRQ14, IRQ15	Input	Maskable interrupt request pins
KINT	KR00 to KR07	Input	Key interrupt input pins. A key interrupt (KINT) can be generated by inputting a falling edge to the key interrupt input pins.
On-chip debug	TMS	I/O	On-chip emulator or boundary scan pins
	TDI	Input	
	TCK	Input	
	TDO	Output	
	SWDIO	I/O	Serial wire debug data input/output pin
	SWCLK	Input	Serial wire clock pin
	SWO	Output	Serial wire trace output pin
Battery Backup	VBATWIO0 to VBATWIO2	I/O	Output wakeup signal for the VBATT wakeup control function. External event input for the VBATT wakeup control function.
GPT	GTETRGA, GTETRGB	Input	External trigger input pin
	GTIOCOA to GTIOC7A, GTIOCOB to GTIOC7B	I/O	Input capture, output capture, or PWM output pin
	GTIU	Input	Hall sensor input pin U
	GTIV	Input	Hall sensor input pin V
	GTIW	Input	Hall sensor input pin W
	GTOUUP	Output	3-phase PWM output for BLDC motor control (positive U phase)
	GTOULO	Output	3-phase PWM output for BLDC motor control (negative U phase)
	GTOVUP	Output	3-phase PWM output for BLDC motor control (positive V phase)
	GTOVLO	Output	3-phase PWM output for BLDC motor control (negative V phase)
	GTOWUP	Output	3-phase PWM output for BLDC motor control (positive W phase)
	GTOWLO	Output	3-phase PWM output for BLDC motor control (negative W phase)

Table 1.15 Pin functions (2 of 4)

Function	Signal	I/O	Description
AGT	AGTEE0, AGTEE1	Input	External event input enable signals
	AGTIO0, AGTIO1	I/O	External event input and pulse output pins
	AGTO0, AGTO1	Output	Pulse output pins
	AGTOA0, AGTOA1	Output	Output compare match A output pins
	AGTOB0, AGTOB1	Output	Output compare match B output pins
RTC	RTCOUT	Output	Output pin for 1-Hz/64-Hz clock
	RTCIC0 to RTCIC2	Input	Time capture event input pins
SCI	SCK0 to SCK2, SCK9	I/O	Clock (clock synchronous mode) input/output pins
	RXD0 to RXD2, RXD9	Input	Received data (asynchronous mode/clock synchronous mode) input pins
	TXD0 to TXD2, TXD9	Output	Transmitted data (asynchronous mode/clock synchronous mode) output pins
	CTS0_RTS0 to CTS2_RTS2, CTS9_RTS9	I/O	Input/output pins for controlling the start of transmission and reception (asynchronous mode/clock synchronous mode), active-low
	SCL0 to SCL2, SCL9	I/O	I ² C clock (simple IIC) input/output pins
	SDA0 to SDA2, SDA9	I/O	I ² C data (simple IIC) input/output pins
	SCK0 to SCK2, SCK9	I/O	Clock (simple SPI) input/output pins
	MISO0 to MISO2, MISO9	I/O	Slave transmission of data (simple SPI) input/output pins
	MOSI0 to MOSI2, MOSI9	I/O	Master transmission of data (simple SPI) input/output pins
	SS0 to SS2, SS9	Input	Slave-select input pins (simple SPI), active-low
IIC	SCL0, SCL1	I/O	Clock input/output pins
	SDA0, SDA1	I/O	Data input/output pins
SSIE	SSIBCK0	I/O	SSIE serial bit clock pin
	SSILRCK0/SSIFS0	I/O	Word select pins
	SSITXD0	Output	Serial data output pin
	SSIRXD0	Input	Serial data input pin
	AUDIO_CLK	Input	External clock pin for audio (input oversampling clock)
SPI	RSPCKA, RSPCKB	I/O	Clock input/output pin
	MOSIA, MOSIB	I/O	Input/output pins for data output from the master
	MISOA, MISOB	I/O	Input/output pins for data output from the slave
	SSLA0, SSLB0	I/O	Input/output pins for slave selection
	SSLA1, SSLA2, SSLA3, SSLB1, SSLB2, SSLB3	Output	Output pins for slave selection
CAN	CRX0	Input	Receive data
	CTX0	Output	Transmit data

Table 1.15 Pin functions (3 of 4)

Function	Signal	I/O	Description
USBFS	VSS_USB	Input	Ground pin
	VCC_USB_LDO	Input	Power supply pin for USB LDO regulator
	VCC_USB	I/O	Input: USB transceiver power supply pin. Output: USB LDO regulator output pin. This pin should be connected to an external capacitor.
	USB_DP	I/O	D+ I/O pin of the USB on-chip transceiver. This pin should be connected to the D+ pin of the USB bus.
	USB_DM	I/O	D- I/O pin of the USB on-chip transceiver. This pin should be connected to the D- pin of the USB bus.
	USB_VBUS	Input	USB cable connection monitor pin. This pin should be connected to VBUS of the USB bus. The VBUS pin status (connected or disconnected) can be detected when the USB module is operating as a device controller.
	USB_EXICEN	Output	Low power control signal for external power supply (OTG) chip
	USB_VBUSEN	Output	VBUS (5 V) supply enable signal for external power supply chip
	USB_OVRCURA, USB_OVRCURB	Input	Connect the external overcurrent detection signals to these pins. Connect the VBUS comparator signals to these pins when the OTG power supply chip is connected.
	USB_ID	Input	Connect the MicroAB connector ID input signal to this pin during operation in OTG mode
Analog power	AVCC0	Input	Analog voltage supply pin
supply	AVSS0	Input	Analog voltage supply ground pin
	VREFH0	Input	Analog reference voltage supply pin
	VREFL0	Input	Reference power supply ground pin
	VREFH	Input	Analog reference voltage supply pin for D/A converter
	VREFL	Input	Analog reference ground pin for D/A converter
ADC14	AN000 to AN014, AN016 to AN025	Input	Input pins for the analog signals to be processed by the A/D converter
	ADTRG0	Input	Input pins for the external trigger signals that start the A/D conversion, active low
DAC12	DA0	Output	Output pins for the analog signals to be processed by the D/A converter
Comparator output	VCOUT	Output	Comparator output pin
ACMPLP	CMPREF0, CMPREF1	Input	Reference voltage input pin
	CMPIN0, CMPIN1	Input	Analog voltage input pins
OPAMP	AMP0+ to AMP3+	Input	Analog voltage input pins
	AMP0- to AMP3-	Input	Analog voltage input pins
	AMP0O to AMP3O	Output	Analog voltage output pins
CTSU	TS00 to TS13, TS17 to TS22, TS27 to TS31, TS34, TS35	Input	Capacitive touch detection pins (touch pins)
	TSCAP	-	Secondary power supply pin for the touch driver

Table 1.15 Pin functions (4 of 4)

Function	Signal	I/O	Description
I/O ports	P000 to P008, P010 to P015	I/O	General-purpose input/output pins
	P100 to P115	I/O	General-purpose input/output pins
	P200	Input	General-purpose input pin
	P201 to P206, P212, P213	I/O	General-purpose input/output pins
	P214, P215	Input	General-purpose input pins
	P300 to P307	I/O	General-purpose input/output pins
	P400 to P415	I/O	General-purpose input/output pins
	P500 to P505	I/O	General-purpose input/output pins
	P600 to P603, P608 to P610	I/O	General-purpose input/output pins
	P708	I/O	General-purpose input/output pins
	P808, P809	I/O	General-purpose input/output pins
	P914, P915	I/O	General-purpose input/output pins
SLCDC	VL1, VL2, VL3, VL4	I/O	Voltage pin for driving the LCD
	CAPH, CAPL	I/O	Capacitor connection pin for the LCD controller/driver
	COM0 to COM7	Output	Common signal output pins for the LCD controller/driver
	SEG00 to SEG37	Output	Segment signal output pins for the LCD controller/driver

1.6 Pin Assignments

Figure 1.3 to Figure 1.6 show the pin assignments.

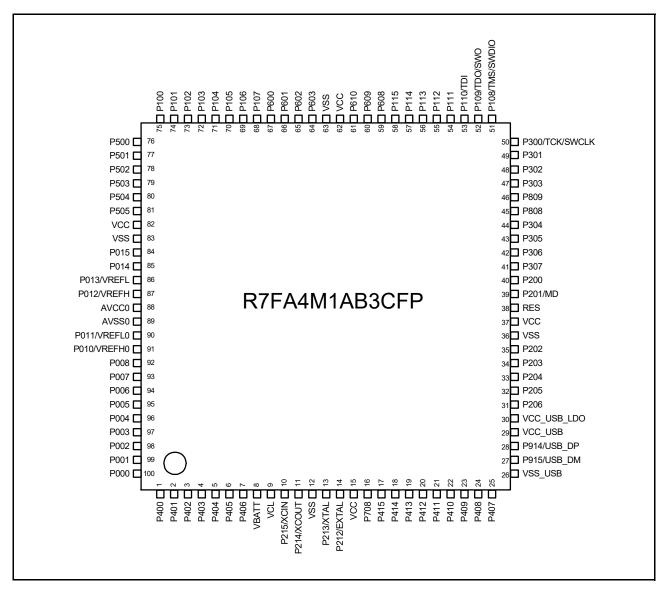


Figure 1.3 Pin assignment for 100-pin LQFP (top view)

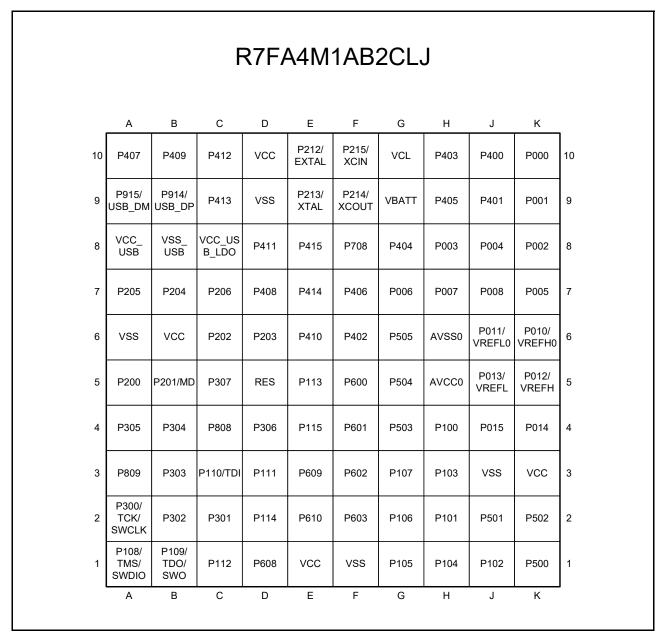


Figure 1.4 Pin assignment for 100-pin LGA (top view)

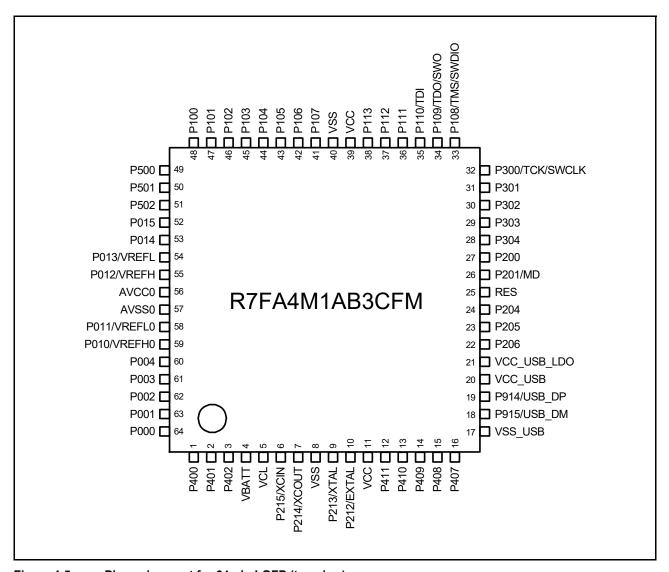


Figure 1.5 Pin assignment for 64-pin LQFP (top view)

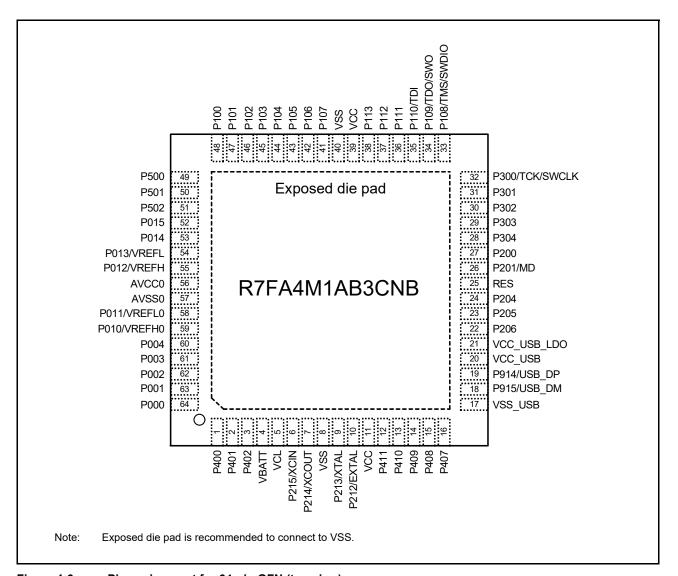


Figure 1.6 Pin assignment for 64-pin QFN (top view)

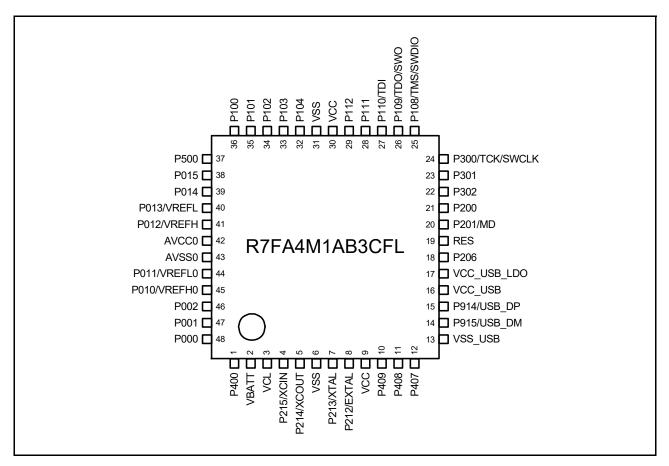


Figure 1.7 Pin assignment for 48-pin LQFP (top view)

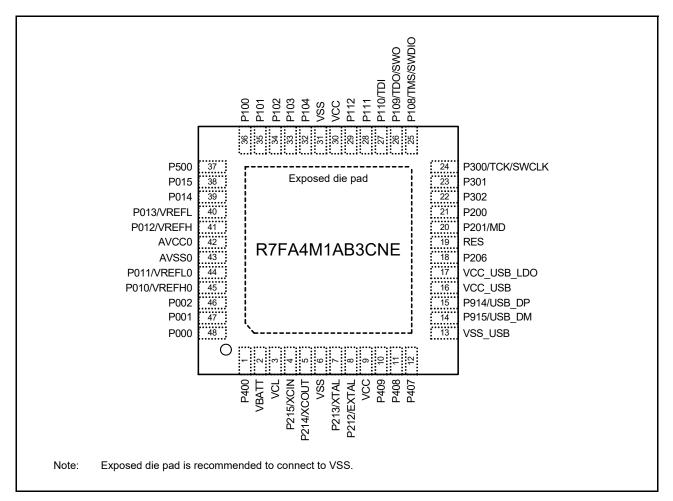


Figure 1.8 Pin assignment for 48-pin QFN (top view)

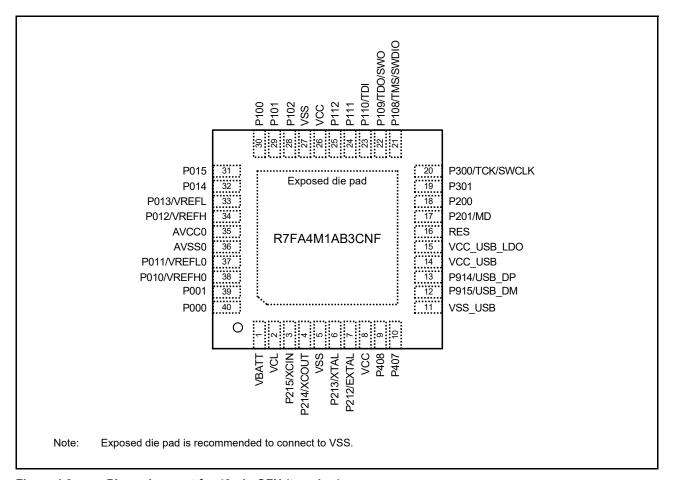


Figure 1.9 Pin assignment for 40-pin QFN (top view)

1.7 Pin Lists

Pin	Pin number						1	Timers				Commu	ınicatio	n interl	aces		Analogs			НМІ			
LQFP100	LGA100	LQFP64	QFN64	LQFP48	QFN48	QFN40	Power, System, Clock, Debug, CAC, VBATT	Interrupt	VO ports		GPT_OPS, POEG	_		USBFS,CAN				u	4	DAC12, OPAMP	ACMPLP	SLCDC	ns
<u>5</u>	/97 J10	ַם 1	<u>ٿ</u>	ΓÖ	الَّا 1	Ŗ	CACREF	IRQ0		AGTIO1	g.	GTIOC6A	RTC	nse	SCK0	SCL0	P	AUDIO_C		ΔĀ	ACI	SEG04	TS20
	010	ľ	ľ	ľ			ONONLI	ii (QO	1 400	Action		CHOOOK			SCK1	0020		K				02004	1020
2	J9	2	2					IRQ5	P401		GTETRGA	GTIOC6B		CTX0	CTS0_	SDA0						SEG05	TS19
															RTS0/ SS0 TXD1/ MOSI1/ SDA1								
3	F6	3	3				VBATWIO0	IRQ4	P402	AGTIO0/ AGTIO1			RTCIC0	CRX0	RXD1/ MISO1/							SEG06	TS18
4	H10						VBATWIO1		P403	AGTIO0/		GTIOC3A	RTCIC1		SCL1 CTS1_			SSIBCK0					TS17
5	Co						VPATMIO		P404	AGTIO1		GTIOC3B	RTCIC2		RTS1/ SS1			SSII DOV	,				
	G8						VBATWIO2						RTGIGZ					SSILRCKI SSIFS0	,				
6	H9								P405			GTIOC1A						SSITXD0					
7	F7								P406			GTIOC1B						SSIRXD0					
8	G9	4	4	2	2	1	VBATT																
9	G10	5	5	3	3	2	VCL																
10	F10	6	6	4	4	3	XCIN		P215														
11	F9	7	7	5	5	4	XCOUT		P214														
12	D9	8	8	6	6	5	VSS																
13	E9	9	9	7	7	6	XTAL	IRQ2	P213		GTETRGA	GTIOC0A			TXD1/ MOSI1/								
14	E10	10	10	8	8	7	EXTAL	IRQ3	P212	AGTEE1	GTETRGB	GTIOC0B			SDA1 RXD1/								
15	D10	11	11	9	9	8	VCC								MISO1/ SCL1								
16	F8	"		3	3	0	V00		P708						RXD1/		SSLA3						
10	го								F700						MISO1/ SCL1		SSLAS						
17	E8							IRQ8	P415			GTIOC0A					SSLA2						
18	E7							IRQ9	P414			GTIOC0B					SSLA1						
19	C9								P413						CTS0_ RTS0/		SSLA0						
20	C10								P412						SS0 SCK0		RSPCKA						
21	D8	12	12					IRQ4	P411	AGTOA1	GTOVUP	GTIOC6A			TXD0/		MOSIA					SEG07	TS07
															MOSI0/ SDA0								
22	E6	13	13					IRQ5	P410	AGTOB1	GTOVLO	GTIOC6B			RXD0/		MISOA					SEG08	TS06
															MISO0/ SCL0								
23	B10	14	14	10	10			IRQ6	P409		GTOWUP	GTIOC5A		USB_EXI	TXD9/							SEG09	TS05
														CEN	MOSI9/ SDA9								
24	D7	15	15	11	11	9		IRQ7	P408		GTOWLO	GTIOC5B		USB_ID	CTS1_ RTS1/ SS1	SCL0						SEG10	TS04
															RXD9/ MISO9/								
															SCL9								
25	A10	16	16	12	12	10		İ	P407	AGTIO0			RTCOUT	USB_VB US	RTS0/	SDA0	SSLB3		ADTRG0	İ		SEG11	TS03
26	B8	17	17	13	13	11	VSS_USB								SS0								
27	A9	18	18	14	14	12			P915					USB_DM									
28	В9	19	19	15	15	13			P914					USB_DP				-					
		<u> </u>		<u> </u>																			

Pin	num	ber					¥, _	Γ		Timers				Commu	nicatio	n interf	aces		Analogs	}		нмі	
LQFP100	LGA100	LQFP64	QFN64	LQFP48	QFN48	QFN40	Power, System, Clock, Debug, CAC, VBATT	Interrupt	I/O ports	AGT	GPT_OPS, POEG	GPT	RTC	USBFS,CAN	SCI	IIC	SPI	SSIE	ADC14	DAC12, OPAMP	ACMPLP	SLCDC	CTSU
29		20	20	16	16		VCC_USB																
30		21	21	17		15	VCC_USB_ LDO																
31	C7	22	22	18	18			IRQ0	P206		GTIU			USB_VB USEN	RXD0/ MISO0/ SCL0	SDA1	SSLB1					SEG12	TS01
32	A7	23	23				CLKOUT	IRQ1	P205	AGTO1	GTIV	GTIOC4A		USB_OV RCURA	TXD0/ MOSI0/ SDA0 CTS9_ RTS9/ SS9	SCL1	SSLB0					SEG13	TSCAP
33	B7	24	24				CACREF		P204	AGTIO1	GTIW	GTIOC4B		USB_OV RCURB	SCK0 SCK9	SCL0	RSPCKB					SEG14	TS00
34	D6								P203			GTIOC5A			CTS2_ RTS2/ SS2 TXD9/ MOSI9/ SDA9		MOSIB					SEG15	TSCAP
35	C6								P202			GTIOC5B			SCK2 RXD9/ MISO9/ SCL9		MISOB					SEG16	
36	A6						VSS																
37	В6						VCC																
38	D5	25	25	19	19	16	RES																
39	B5	26	26	20	20	17	MD		P201														
40	A5	27	27	21	21	18		NMI	P200														
41	C5								P307													SEG17	
42	D4								P306													SEG18	
43	A4							IRQ8	P305													SEG19	
44	B4	28	28					IRQ9	P304			GTIOC7A										SEG20	TS11
45	C4								P808													SEG21	
46	A3								P809													SEG22	
47	В3	29	29						P303			GTIOC7B										SEG03/ COM7	TS02
48		30	30	22		10		IRQ5	P302	A OTION	GTOUUP	GTIOC4A			TXD2/ MOSI2/ SDA2		SSLB3					SEG02/ COM6	TS08
49	02	31	31	23	123	18		IRQ6	P301	AGTIO0	GTOULO	GTIOC4B			RXD2/ MISO2/ SCL2 CTS9_ RTS9/ SS9		SSLB2					SEG01/ COM5	1308
50	A2	32	32	24	24	20	TCK/ SWCLK		P300		GTOUUP	GTIOC0A					SSLB1						
51	A1	33	33	25	25	21	TMS/ SWDIO		P108		GTOULO	GTIOC0B			CTS9_ RTS9/		SSLB0						
52	B1	34	34	26	26	22	TDO/SWO/ CLKOUT		P109		GTOVUP	GTIOC1A		CTX0	SS9 SCK1 TXD9/ MOSI9/ SDA9		MOSIB					SEG23	TS10
53	C3	35	35	27	27	23	TDI	IRQ3	P110		GTOVLO	GTIOC1B		CRX0	CTS2_ RTS2/ SS2 RXD9/ MISO9/ SCL9		MISOB				VCOUT	SEG24	

Pin	num	ber					¥.	l		Timers				Commu	ınicatio	n interf	aces		Analogs	i		нмі	
LQFP100	LGA100	LQFP64	QFN64	LQFP48	QFN48	QFN40	Power, System, Clock, Debug, CAC, VBATT		I/O ports	AGT	GPT_OPS, POEG	GPT	RTC	USBFS,CAN	SCI	IIC	SPI	SSIE	ADC14	DAC12, OPAMP	ACMPLP	SLCDC	стѕи
54	D3	36	36	28	28	24		IRQ4	P111			GTIOC3A			SCK2 SCK9		RSPCKB					CAPH	TS12
	0.4	07	07	00	00	0.5			D440			OTIOOOD			TYPO		001.00	OOLDONO				0.4.01	TOOLD
55	C1	37	37	29	29	25			P112			GTIOC3B			TXD2/ MOSI2/ SDA2 SCK1		SSLB0	SSIBCK0				CAPL	TSCAP
56	E5	38	38						P113			GTIOC2A						SSILRCK0/					TS27
57	D2								P114			GTIOC2B						SSIFS0 SSIRXD0				COM4 SEG25	TS29
58	E4								P115			GTIOC4A						SSITXD0				SEG26	TS35
59	D1								P608			GTIOC4B										SEG27	
60	E3								P609			GTIOC5A										SEG28	
61	E2								P610			GTIOC5B										SEG29	
62	E1	39	39	30	30	26	VCC																
63	F1	40	40	31	31	27	VSS																
64	F2								P603			GTIOC7A			CTS9_ RTS9/ SS9							SEG30	
65	F3								P602			GTIOC7B			TXD9/ MOSI9/							SEG31	
66	F4								P601			GTIOC6A			SDA9 RXD9/ MISO9/							SEG32	
67	F5								P600			GTIOC6B			SCL9 SCK9							SEG33	
68	G3	41	41					KR07	P107			GTIOC0A										СОМЗ	
69	G2	42	42					KR06	P106			GTIOC0B					SSLA3					COM2	
70	G1	43	43					KR05/ IRQ0	P105		GTETRGA	GTIOC1A					SSLA2					COM1	TS34
71	H1	44	44	32	32			KR04/ IRQ1	P104		GTETRGB	GTIOC1B			RXD0/ MISO0/		SSLA1					СОМ0	TS13
72	НЗ	45	45	33	33			KR03	P103		GTOWUP	GTIOC2A		CTX0	SCL0 CTS0_		SSLA0		AN019		CMPREF1	VL4	
73	J1	46	46	34	34	28		KR02	P102	AGTO0	GTOWLO	GTIOC2B		CRX0	RTS0/ SS0 SCK0		RSPCKA		AN020/		CMPIN1	VL3	
															TXD2/ MOSI2/ SDA2				ADTRG0				
74	H2	47	47	35	35	29		KR01/ IRQ1	P101	AGTEE0	GTETRGB	GTIOC5A			TXD0/ MOSI0/ SDA0 CTS1_ RTS1/ SS1	SDA1	MOSIA		AN021		CMPREF0	VL2	
75	H4	48	48	36	36	30		KR00/ IRQ2	P100	AGTIO0	GTETRGA	GTIOC5B			RXD0/ MISO0/ SCL0 SCK1	SCL1	MISOA		AN022		CMPIN0	VL1	
76	K1	49	49	37	37				P500	AGTOA0	GTIU	GTIOC2A		USB_VB					AN016		CMPREF1	SEG34	
77	J2	50	50					IRQ11	P501	AGTOB0	GTIV	GTIOC2B		USB_OV RCURA	TXD1/ MOSI1/				AN017		CMPIN1	SEG35	
78	K2	51	51					IRQ12	P502		GTIW	GTIOC3B		USB_OV	SDA1 RXD1/				AN018		CMPREF0	SEG36	
79									P503					RCURB USB_EXI	MISO1/ SCL1				AN023		CMPIN0	SEG37	<u> </u>
80	G4 G5								P503					CEN	CTS1_				AN023		CIVIPIINU	3EG3/	
														200_10	RTS1/ SS1								
81	G6							IRQ14	P505										AN025				
82	K3						VCC																

Pin	num	ber					بد	1	I	Timers				Commu	nicatio	n interf	aces		Analogs	3		нмі	
E8 LQFP100	LGA100	LQFP64	QFN64	LQFP48	QFN48	QFN40	Power, System, Clock, Debug, CAC, VBATT	Interrupt	I/O ports	AGT	GPT_OPS, POEG	GPT	RTC	USBFS, CAN	SCI)II	SPI	SSIE	ADC14	DAC12, OPAMP	ACMPLP	SLCDC	CTSU
83	J3						VSS																
84	J4	52	52	38	38	31		IRQ7	P015										AN010				TS28
85	K4	53	53	39	39	32			P014										AN009	DA0			
86	J5	54	54	40	40	33	VREFL		P013										AN008	AMP1+			
87	K5	55	55	41	41	34	VREFH		P012										AN007	AMP1-			
88	H5	56	56	42	42	35	AVCC0																
89	H6	57	57	43	43	36	AVSS0																
90	J6	58	58	44	44	37	VREFL0	IRQ15	P011										AN006	AMP2+			TS31
91	K6		59	45	45	38	VREFH0		P010										AN005	AMP2-			TS30
	ΝO	59	59	45	45	30	VKEFHU		P010										ANUUS	AIVIP2-			1530
92	J7								P008										AN014				
93	H7								P007										AN013	AMP3O			
94	G7								P006										AN012	AMP3-			
95	K7							IRQ10	P005										AN011	AMP3+			
96	J8	60	60					IRQ3	P004										AN004	AMP2O			
90	Jo	60	60					IKQ3	P004										ANUU4	AMP20			
97	H8	61	61						P003										AN003	AMP10			
98	K8	62	62	46	46			IRQ2	P002										AN002	AMP0O			
99	K9	63	63	47	47	39		IRQ7	P001										AN001	AMP0-			TS22
100	K10	64	64	48	48	40		IRQ6	P000										AN000	AMP0+			TS21
100	rk IU	04	04	40	40	40		IKUD	-000										ANUUU	AWPU+			1021

2. Electrical Characteristics

Unless otherwise specified, the electrical characteristics of the MCU are defined under the following conditions:

 $VCC^{*1} = AVCC0 = VCC_USB^{*2} = VCC_USB_LDO^{*2} = 1.6$ to 5.5V, VREFH = VREFH0 = 1.6 to AVCC0, VBATT = 1.6 to 3.6V, VSS = AVSS0 = VREFL = VREFL0 = VSS_USB = 0V, T_a = T_{opr}

Note 1. The typical condition is set to VCC = 3.3V.

Note 2. When USBFS is not used.

Figure 2.1 shows the timing conditions.

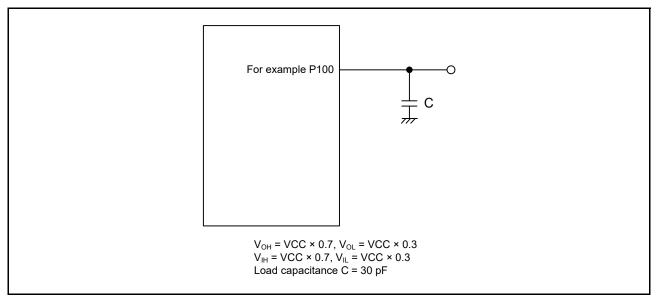


Figure 2.1 Input or output timing measurement conditions

The recommended measurement conditions for the timing specification of each peripheral provided are for the best peripheral operation. Make sure to adjust the driving abilities of each pin to meet your conditions.

Each function pin used for the same function must select the same drive ability. If the I/O drive ability of each function pin is mixed, the AC specification of each function is not guaranteed.

2.1 Absolute Maximum Ratings

Table 2.1 Absolute maximum ratings

Parameter		Symbol	Value	Unit
Power supply voltage		VCC	-0.5 to +6.5	V
Input voltage	5 V-tolerant ports*1	V _{in}	-0.3 to +6.5	V
	P000 to P008, P010 to P015	V _{in}	-0.3 to AVCC0 + 0.3	V
	Others	V _{in}	-0.3 to VCC + 0.3	V
Reference power supply	voltage	VREFH0	-0.3 to +6.5	V
		VREFH		V
VBATT power supply volt	age	VBATT	-0.5 to +6.5	V
Analog power supply volt	age	AVCC0	-0.5 to +6.5	V
USB power supply voltag	е	VCC_USB	-0.5 to +6.5	V
		VCC_USB_LDO	-0.5 to +6.5	V
Analog input voltage	When AN000 to AN014 are used	V _{AN}	-0.3 to AVCC0 + 0.3	V
	When AN016 to AN025 are used		-0.3 to VCC + 0.3	V
LCD voltage	VL1 voltage	V_{L1}	-0.3 to +2.8	V
	VL2 voltage	V _{L2}	-0.3 to +6.5	V
	VL3 voltage	V _{L3}	-0.3 to +6.5	V
	VL4 voltage	V_{L4}	-0.3 to +6.5	V
Operating temperature*2,*3,*4		T _{opr}	-40 to +105	°C
			-40 to +85	
Storage temperature		T _{stg}	-55 to +125	°C

Caution: Permanent damage to the MCU may result if absolute maximum ratings are exceeded.

To preclude any malfunctions due to noise interference, insert capacitors of high frequency characteristics between the VCC and VSS pins, between the AVCC0 and AVSS0 pins, between the VCC_USB and VSS_USB pins, between the VREFH0 and VREFL0 pins, and between the VREFH and VREFL pins. Place capacitors of about 0.1 μF as close as possible to every power supply pin and use the shortest and heaviest possible traces. Also, connect capacitors as stabilization capacitance.

Connect the VCL pin to a VSS pin by a 4.7 µF capacitor. The capacitor must be placed close to the pin. Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up might cause malfunction and the abnormal current that passes in the device at this time might cause degradation of internal elements.

- Note 1. Ports P205, P206, P400 to P404, P407, P408 are 5 V tolerant.
- Note 2. See section 2.2.1, Tj/Ta Definition.
- Note 3. Contact a Renesas Electronics sales office for information on derating operation under $T_a = +85^{\circ}\text{C}$ to $+105^{\circ}\text{C}$. Derating is the systematic reduction of load for improved reliability.
- Note 4. The upper limit of operating temperature is +85°C or +105°C, depending on the product. For details, see section 1.3, Part Numbering.

Table 2.2 Recommended operating conditions

Parameter	Symbol	Value	Min	Тур	Max	Unit
Power supply voltages	VCC*1, *2	When USBFS is not used	1.6	-	5.5	V
		When USBFS is used USB Regulator Disable	VCC_USB	-	3.6	V
		When USBFS is used USB Regulator Enable	VCC_USB _LDO	-	5.5	V
	VSS		-	0	-	V
USB power supply voltages	VCC_USB	When USBFS is not used	-	VCC	-	V
		When USBFS is used USB Regulator Disable (Input)	3.0	3.3	3.6	V
	VCC_USB_LDO	When USBFS is not used	-	VCC	-	V
		When USBFS is used USB Regulator Disable	-	VCC	-	V
		When USBFS is used USB Regulator Enable	3.8	-	5.5	V
	VSS_USB	•	-	0	-	V
VBATT power supply voltage	VBATT	When the battery backup function is not used	-	VCC	-	V
		When the battery backup function is used	1.6	-	3.6	V
Analog power supply voltages	AVCC0*1, *2	- 1	1.6	-	5.5	V
	AVSS0		-	0	-	V
	VREFH0	When used as	1.6	-	AVCC0	V
	VREFL0	ADC14 Reference	-	0	-	V
	VREFH	When used as	1.6	-	AVCC0	V
	VREFL	DAC12 Reference	-	0	-	V

Note 1. Use AVCC0 and VCC under the following conditions:

AVCC0 and VCC can be set individually within the operating range when VCC ≥ 2.2 V and AVCC0 ≥ 2.2 V.

AVCC0 = VCC when VCC < 2.2 V or AVCC0 < 2.2 V.

Note 2. When powering on the VCC and AVCC0 pins, power them on at the same time, or power the VCC pin first and then the AVCC0 pin.

2.2 **DC** Characteristics

2.2.1 Tj/T_a Definition

Table 2.3 **DC Characteristics**

Conditions: Products with operating temperature (T_a) -40 to +105°C

Parameter	Symbol	Тур	Max	Unit	Test conditions
Permissible junction temperature	Tj	-	125	°C	High-speed mode
			105*1		Middle-speed mode Low-voltage mode Low-speed mode Subosc-speed mode

Note: Make sure that $Tj = T_a + \theta ja \times total power consumption (W),$

where total power consumption = (VCC - V_{OH}) × ΣI_{OH} + V_{OL} × ΣI_{OL} + I_{CC} max × VCC.

The upper limit of operating temperature is +85°C or +105°C, depending on the product. For details, see section 1.3, Part Numbering. If the part number shows the operation temperature at 85° C, then the maximum value of T_i is +105°C, otherwise, it is +125°C.

2.2.2 $I/O V_{IH}, V_{IL}$

Table 2.4 $I/O V_{IH}, V_{IL} (1)$

Conditions: VCC = AVCC0 = VCC_USB = VCC_USB_LDO = 2.7 to 5.5V, VBATT = 1.6 to 3.6 V, VSS = AVSS0 = 0 V

Parameter	Parameter		Min	Тур	Max	Unit	Test conditions
Schmitt trigger	IIC*1 (except for SMBus)	V _{IH}	VCC × 0.7	-	5.8	V	-
input voltage		V _{IL}	-	-	VCC × 0.3		
		ΔV_T	VCC × 0.05	-	-		
	RES, NMI	V _{IH}	VCC × 0.8	-	-		
	Other peripheral input pins excluding IIC	V _{IL}	-	-	VCC × 0.2		
	excluding no	ΔV_T	VCC × 0.1	-	-		
Input voltage	IIC (SMBus)*2	V _{IH}	2.2	-	-		VCC = 3.6 to 5.5 V
(except for Schmitt trigger input pin)		V _{IH}	2.0	-	-		VCC = 2.7 to 3.6 V
		V _{IL}	-	-	0.8		-
	5 V-tolerant ports*3	V _{IH}	VCC × 0.8	-	5.8		
		V _{IL}	-	-	VCC × 0.2		
	P914, P915	V _{IH}	VCC_USB × 0.8	-	VCC_USB + 0.3		
		V _{IL}	-	-	VCC_USB × 0.2		
	P000 to P008, P010 to P015	V _{IH}	AVCC0 × 0.8	-	-		
		V _{IL}	-	-	AVCC0 × 0.2		
	EXTAL	V _{IH}	VCC × 0.8	-	-		
	Input ports pins except for P000 to P008, P010 to P015, P914, P915	V _{IL}	-	-	VCC × 0.2		
When V _{BATT}	P402, P403, P404	V _{IH}	V _{BATT} × 0.8	-	V _{BATT} + 0.3		
power supply is selected		V _{IL}	-	-	V _{BATT} × 0.2		
Selected		ΔV_{T}	V _{BATT} × 0.05	-	-		

Note 1. P205, P206, P400, P401, P407, P408 (total 6 pins). Note 2. P100, P101, P204, P205, P206, P400, P401, P407, P408 (total 9 pins).

Note 3. P205, P206, P400 to P404, P407, P408 (total 9 pins).

Table 2.5 I/O V_{IH} , V_{IL} (2) Conditions: VCC = AVCC0 = VCC_USB = VCC_USB_LDO = 1.6 to 2.7 V, VBATT = 1.6 to 3.6 V, VSS = AVSS0 = 0 V

Parameter		Symbol	Min	Тур	Max	Unit	Test conditions
Schmitt trigger	RES, NMI	V _{IH}	VCC × 0.8	-	-	V	-
input voltage	Peripheral input pins	V _{IL}	-	-	VCC × 0.2		
		ΔV_{T}	VCC × 0.01	-	-		
Input voltage	5 V-tolerant ports*1	V _{IH}	VCC × 0.8	-	5.8		
(except for Schmitt trigger		V _{IL}	-	-	VCC × 0.2		
input pin)	P914, P915	V _{IH}	VCC_USB × 0.8	-	VCC_USB + 0.3		
		V _{IL}	-	-	VCC_USB × 0.2	- - -	
	P000 to P008, P010 to P015	V _{IH}	AVCC0 × 0.8	-	-		
		V _{IL}	-	-	AVCC0 × 0.2		
	EXTAL	V _{IH}	VCC × 0.8	-	-		
	Input ports pins except for P000 to P008, P010 to P015, P914, P915	V _{IL}	-	-	VCC × 0.2		
When V _{BATT}	P402, P403, P404	V _{IH}	V _{BATT} × 0.8	-	V _{BATT} + 0.3		
power supply is selected		V _{IL}	-	-	V _{BATT} × 0.2		
selected		ΔV_{T}	V _{BATT} × 0.01	-	-		

Note 1. P205, P206, P400 to P404, P407, P408 (total 9 pins)

I/O I_{OH} , I_{OL} 2.2.3

Table 2.6 I/O I_{OH} , I_{OL} (1 of 2) Conditions: VCC = AVCC0 = VCC_USB = VCC_USB_LDO = 1.6 to 5.5 V

Parameter			Symbol	Min	Тур	Max	Unit
Permissible output current	Ports P212, P213	-	I _{OH}	-	-	-4.0	mA
(average value per pin)			I _{OL}	-	-	4.0	mA
	Port P408	Low drive*1	I _{OH}	-	-	-4.0	mA
			I _{OL}	-	-	4.0	mA
		Middle drive for IIC	I _{OH}	-	-	-8.0	mA
		Fast-mode*4 VCC = 2.7 to 5.5 V	I _{OL}	-	-	8.0	mA
		Middle drive*2	I _{OH}	-	-	-20.0	mA
		VCC = 3.0 to 5.5 V	I _{OL}	-	-	20.0	mA
	Port P409	Low drive*1	I _{OH}	-	-	-4.0	mA
			I _{OL}	-	-	4.0	mA
		Middle drive*2	I _{OH}	-	-	-8.0	mA
		VCC = 2.7 to 3.0 V	I _{OL}	-	-	8.0	mA
		Middle drive*2 VCC = 3.0 to 5.5 V	I _{OH}	-	-	-20.0	mA
			I _{OL}	-	-	20.0	mA
	Ports P100 to P115, P201 to P204, P300 to P307,	Low drive*1	I _{OH}	-	-	-4.0	mA
	P500 to P503, P600 to P603,		I _{OL}	-	-	4.0	mA
	P608 to P610, P808, P809 (total 41 pins)	Middle drive*2	I _{OH}	-	-	-4.0	mA
			I _{OL}	-	-	8.0	mA
	Ports P914, P915	-	I _{OH}	-	-	-4.0	mA
			I _{OL}	-	-	4.0	mA
	Other output pin*3	Low drive*1	I _{OH}	-	-	-4.0	mA
			I _{OL}	-	-	4.0	mA
		Middle drive*2	I _{ОН}	-	-	-8.0	mA
			I _{OL}	-	-	8.0	mA

Table 2.6 I/O I_{OH} , I_{OL} (2 of 2) Conditions: VCC = AVCC0 = VCC_USB = VCC_USB_LDO = 1.6 to 5.5 V

Parameter		Symbol	Min	Тур	Max	Unit	
Permissible output current	Ports P212, P213	-	I _{OH}	-	-	-4.0	mA
(Max value per pin)			I _{OL}	-	-	4.0	mA
	Port P408	Low drive*1	I _{OH}	-	-	-4.0	mA
			I _{OL}	-	-	4.0	mA
		Middle drive for IIC	I _{OH}	-	-	-8.0	mA
		Fast-mode*4 VCC = 2.7 to 5.5 V	I _{OL}	-	-	8.0	mA
		Middle drive*2	I _{OH}	-	-	-20.0	mA
		VCC = 3.0 to 5.5 V	I _{OL}	-	-	20.0	mA
	Port P409	Low drive*1	I _{OH}	-	-	-4.0	mA
			I _{OL}	-	-	4.0	mA
		Middle drive*2	I _{OH}	-	-	-8.0	mA
		VCC = 2.7 to 3.0 V	I _{OL}	-	-	8.0	mA
		Middle drive*2	I _{OH}	-	-	-20.0	mA
		VCC = 3.0 to 5.5 V	I _{OL}	-	-	20.0	mA
	Ports P100 to P115, P201 to P204, P300 to P307, P500 to P503, P600 to P603, P608 to P610, P808, P809 (total 41 pins)	Low drive*1	I _{OH}	-	-	-4.0	mA
			I _{OL}	-	-	4.0	mA
		Middle drive*2	I _{OH}	-	-	-4.0	mA
	, ,		I _{OL}	-	-	8.0	mA
	Ports P914, P915	-	I _{OH}	-	-	-4.0	mA
			I _{OL}	-	-	4.0	mA
	Other output pin*3	Low drive*1	I _{OH}	-	-	-4.0	mA
			I _{OL}	-	-	4.0	mA
		Middle drive*2	I _{OH}	-	-	-8.0	mA
			I _{OL}	-	-	8.0	mA
Permissible output current	Total of ports P000 to P008, P01	0 to P015	ΣI _{OH (max)}	-	-	-30	mA
(max value total pins)			ΣI _{OL (max)}	-	-	30	mA
	Ports P914, P915	Ports P914, P915			-	-2.0	mA
			ΣI _{OL (min)}	-	-	2.0	mA
	Total of all output pin*5	ΣI _{OH (max)}	-	-	-60	mA	
			ΣI _{OL (max)}	-	-	60	mA

To protect the reliability of the MCU, the output current values should not exceed the values in this table. The Caution: average output current indicates the average value of current measured during 100 μ s.

- Note 1. This is the value when low driving ability is selected with the Port Drive Capability bit in PmnPFS register.
- Note 2. This is the value when middle driving ability is selected with the Port Drive Capability bit in PmnPFS register.
- Except for ports P200, P214, P215, which are input ports. Note 3.
- Note 4. This is the value when middle driving ability for IIC Fast-mode is selected with the Port Drive Capability bit in PmnPFS register.
- Note 5. For details on the permissible output current used with CTSU, see section 2.11, CTSU Characteristics.

2.2.4 I/O V_{OH}, V_{OL}, and Other Characteristics

Table 2.7 I/O V_{OH} , V_{OL} (1) Conditions: VCC = AVCC0 = VCC_USB = VCC_USB_LDO = 4.0 to 5.5 V

Parameter			Symbol	Min	Тур	Max	Unit	Test conditions
Output voltage	IIC*1	IIC*1		-	-	0.4	V	I _{OL} = 3.0 mA
				-	-	0.6		I _{OL} = 6.0 mA
	Ports P408, P409*2,	*3	V _{OH}	VCC - 1.0	-	-		I _{OH} = -20 mA
			V _{OL}	-	-	1.0		I _{OL} = 20 mA
	Ports P000 to P008, P010 to P015	Low drive	V _{OH}	AVCC0 - 0.8	-	-		I _{OH} = -2.0 mA
			V _{OL}	-	-	0.8		I _{OL} = 2.0 mA
		Middle drive	V _{OH}	AVCC0 - 0.8	-	-		I _{OH} = -4.0 mA
			V _{OL}	-	-	0.8		I _{OL} = 4.0 mA
	Ports P914, P915	Ports P914, P915		VCC_USB - 0.8	-	-		I _{OH} = -2.0 mA
			V _{OL}	-	-	0.8		I _{OL} = 2.0 mA
	Other output pins*4	Low drive	V _{OH}	VCC - 0.8	-	-		I _{OH} = -2.0 mA
			V _{OL}	-	-	0.8		I _{OL} = 2.0 mA
		drivo*6	V _{OH}	VCC - 0.8	-	-		I _{OH} = -4.0 mA
			V _{OL}	-	-	0.8		I _{OL} = 4.0 mA

- Note 1. P100, P101, P204, P205, P206, P400, P401, P407, P408 (total 9 pins).
- Note 2. This is the value when middle driving ability is selected with the Port Drive Capability bit in PmnPFS register.
- Note 3. Based on characterization data, not tested in production.
- Note 4. Except for ports P200, P214, P215, which are input ports.
- Note 5. This is the value when middle driving ability for IIC is selected in the Port Drive Capability bit in PmnPFS register for P408.
- Note 6. Except for P212, P213.

Table 2.8 I/O V_{OH} , V_{OL} (2) Conditions: VCC = AVCC0 = VCC_USB = VCC_USB_LDO = 2.7 to 4.0 V

Parameter			Symbol	Min	Тур	Max	Unit	Test conditions
Output voltage	IIC*1		V _{OL}	-	-	0.4	V	I _{OL} = 3.0 mA
			V _{OL} *2,*5	-	-	0.6		I _{OL} = 6.0 mA
	Ports P408, P409*2, *	3	V _{OH}	VCC - 1.0	-	-		I _{OH} = -20 mA VCC = 3.3 V
			V _{OL}	-	-	1.0		I _{OL} = 20 mA VCC = 3.3 V
	Ports P000 to P008,	Low drive	V _{OH}	AVCC0 - 0.5	-	-		I _{OH} = -1.0 mA
	P010 to P015		V _{OL}	-	-	0.5		I _{OL} = 1.0 mA
		Middle drive	V _{OH}	AVCC0 - 0.5	-	-		I _{OH} = -2.0 mA
			V _{OL}	-	-	0.5		I _{OL} = 2.0 mA
	Ports P914, P915	•	V _{OH}	VCC_USB - 0.5	-	-		I _{OH} = -1.0 mA
			V _{OL}	-	-	0.5		I _{OL} = 1.0 mA
	Other output pins*4	Low drive	V _{OH}	VCC - 0.5	-	-		I _{OH} = -1.0 mA
			V _{OL}	-	-	0.5		I _{OL} = 1.0 mA
		Middle	V _{OH}	VCC - 0.5	-	-		I _{OH} = -2.0 mA
		drive*6	V _{OL}	-	-	0.5		I _{OL} = 2.0 mA

- Note 1. P100, P101, P204, P205, P206, P400, P401, P407, P408 (total 9 pins).
- Note 2. This is the value when middle driving ability is selected with the Port Drive Capability bit in PmnPFS register.
- Note 3. Based on characterization data, not tested in production.
- Note 4. Except for ports P200, P214, P215, which are input ports.
- Note 5. This is the value when middle driving ability for IIC is selected in the Port Drive Capability bit in PmnPFS register for P408.
- Note 6. Except for P212, P213.

Table 2.9 I/O V_{OH} , V_{OL} (3) Conditions: VCC = AVCC0 = VCC_USB = VCC_USB_LDO = 1.6 to 2.7 V

Parameter			Symbol	Min	Тур	Max	Unit	Test conditions
Output voltage	Ports P000 to P015	Low drive	V _{OH}	AVCC0 - 0.3	-	-	V	I _{OH} = -0.5 mA
			V _{OL}	-	-	0.3		I _{OL} = 0.5 mA
		Middle drive	V _{OH}	AVCC0 - 0.3	-	-		I _{OH} = -1.0 mA
			V _{OL}	-	-	0.3		I _{OL} = 1.0 mA
	Ports P914, P915		V _{OH}	VCC_USB - 0.3	-	-		I _{OH} = -0.5 mA
			V _{OL}	-	-	0.3		I _{OL} = 0.5 mA
	Other output pins*1	Low drive	V _{OH}	VCC - 0.3	-	-		I _{OH} = -0.5 mA
			V _{OL}	-	-	0.3		I _{OL} = 0.5 mA
		drivo*2	V _{OH}	VCC - 0.3	-	-		I _{OH} = -1.0 mA
			V _{OL}	-	-	0.3		I _{OL} = 1.0 mA

Note 1. Except for ports P200, P214, P215, which are input ports.

Note 2. Except for P212, P213.

Table 2.10 I/O other characteristics

Conditions: VCC = AVCC0 = 1.6 to 5.5 V

Parameter	Parameter			Тур	Max	Unit	Test conditions
Input leakage current	RES, P200, P214, P215	I _{in}	-	-	1.0	μА	V _{in} = 0 V V _{in} = VCC
Three-state leakage current (off state)	5 V-tolerant ports	I _{TSI}	-	-	1.0	μА	V _{in} = 0 V V _{in} = 5.8 V
	Other ports (except for ports P200, P214, P215 and 5 V tolerant)		-	-	1.0		V _{in} = 0 V V _{in} = VCC
Input pull-up resistor	All ports (except for ports P200, P214, P215, P914, P915)	R _U	10	20	50	kΩ	V _{in} = 0 V
Input capacitance	P914, P915, P100 to P103, P111, P112, P200	C _{in}	-	-	30	pF	V _{in} = 0 V f = 1 MHz T _a = 25°C
	Other input pins		-	-	15	1	

2.2.5 I/O Pin Output Characteristics of Low Drive Capacity

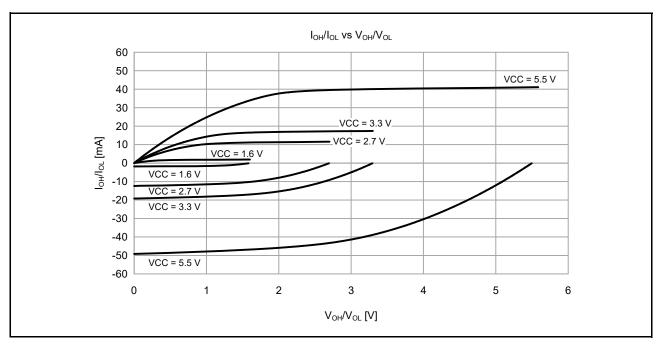


Figure 2.2 V_{OH}/V_{OL} and I_{OH}/I_{OL} Voltage Characteristics at T_a = 25°C when low drive output is selected (reference data)

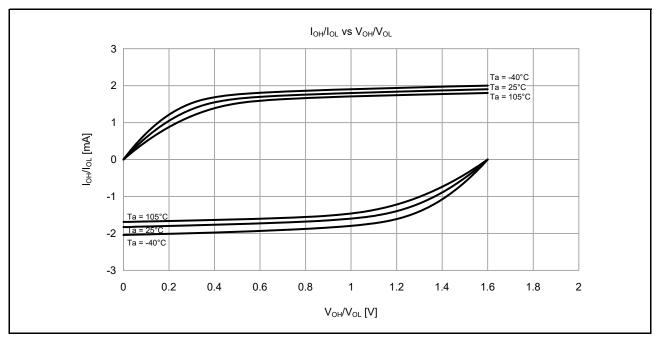


Figure 2.3 V_{OH}/V_{OL} and I_{OH}/I_{OL} temperature characteristics at VCC = 1.6 V when low drive output is selected (reference data)

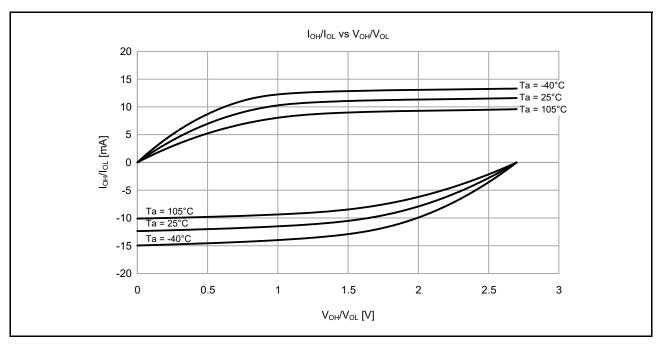


Figure 2.4 V_{OH}/V_{OL} and I_{OH}/I_{OL} temperature characteristics at VCC = 2.7 V when low drive output is selected (reference data)

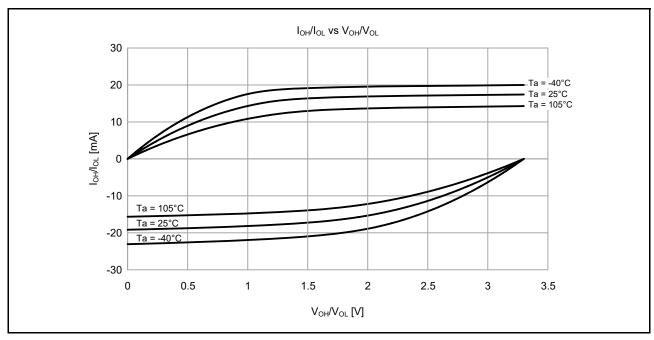


Figure 2.5 V_{OH}/V_{OL} and I_{OH}/I_{OL} temperature characteristics at VCC = 3.3 V when low drive output is selected (reference data)

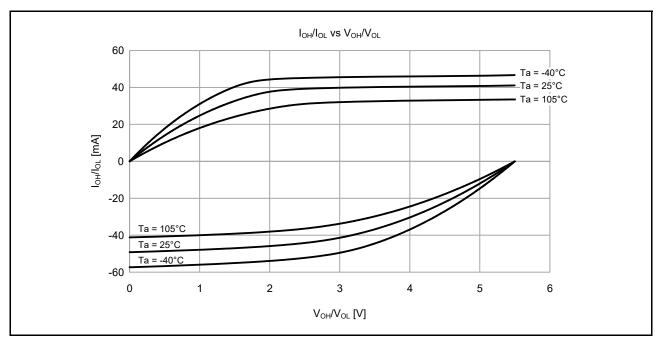


Figure 2.6 V_{OH}/V_{OL} and I_{OH}/I_{OL} temperature characteristics at VCC = 5.5 V when low drive output is selected (reference data)

2.2.6 I/O Pin Output Characteristics of Middle Drive Capacity

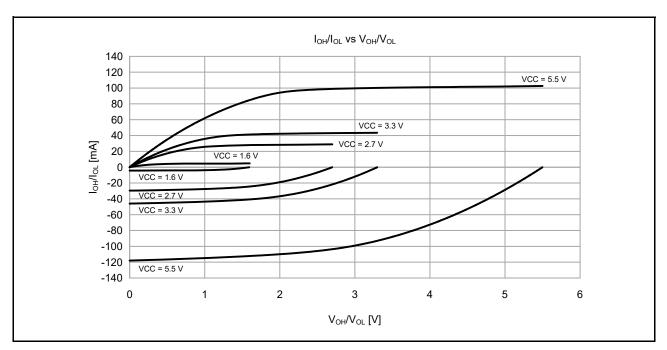


Figure 2.7 V_{OH}/V_{OL} and I_{OH}/I_{OL} voltage characteristics at $T_a = 25^{\circ}$ C when middle drive output is selected (reference data)

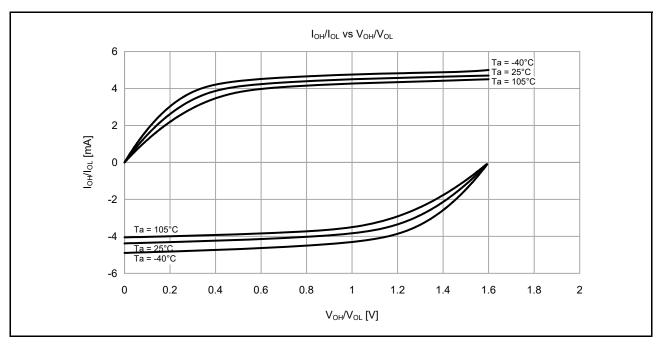


Figure 2.8 V_{OH}/V_{OL} and I_{OH}/I_{OL} temperature characteristics at VCC = 1.6 V when middle drive output is selected (reference data)

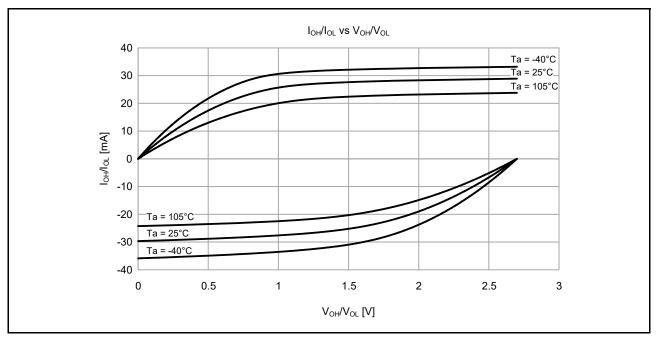


Figure 2.9 V_{OH}/V_{OL} and I_{OH}/I_{OL} temperature characteristics at VCC = 2.7 V when middle drive output is selected (reference data)

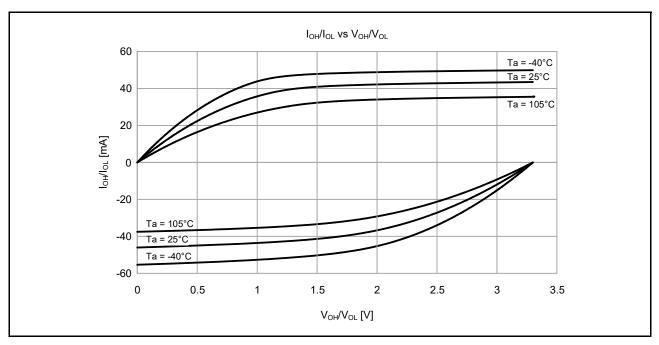


Figure 2.10 V_{OH}/V_{OL} and I_{OH}/I_{OL} temperature characteristics at VCC = 3.3 V when middle drive output is selected (reference data)

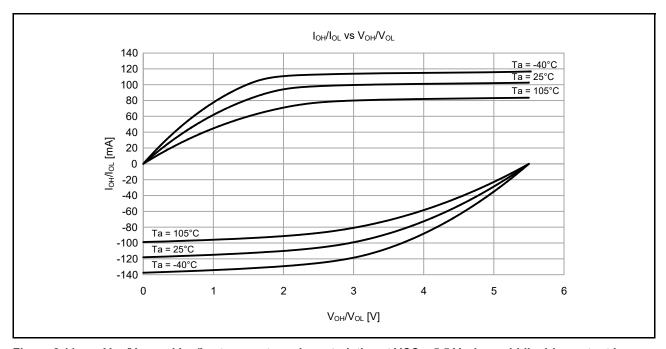


Figure 2.11 V_{OH}/V_{OL} and I_{OH}/I_{OL} temperature characteristics at VCC = 5.5 V when middle drive output is selected (reference data)

2.2.7 P408, P409 I/O Pin Output Characteristics of Middle Drive Capacity

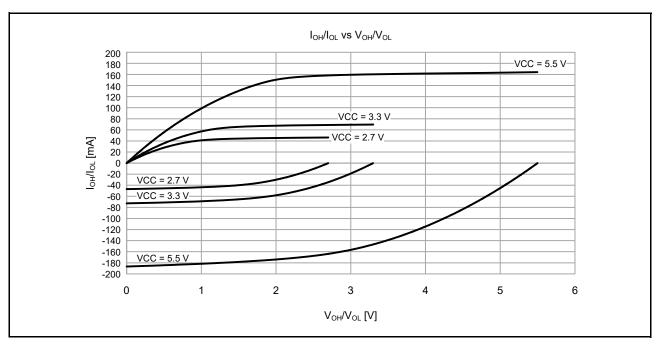


Figure 2.12 V_{OH}/V_{OL} and I_{OH}/I_{OL} voltage characteristics at Ta = 25°C when middle drive output is selected (reference data)

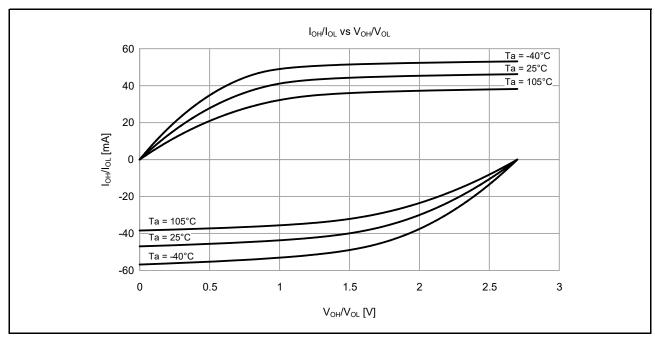


Figure 2.13 V_{OH}/V_{OL} and I_{OH}/I_{OL} temperature characteristics at VCC = 2.7 V when middle drive output is selected (reference data)

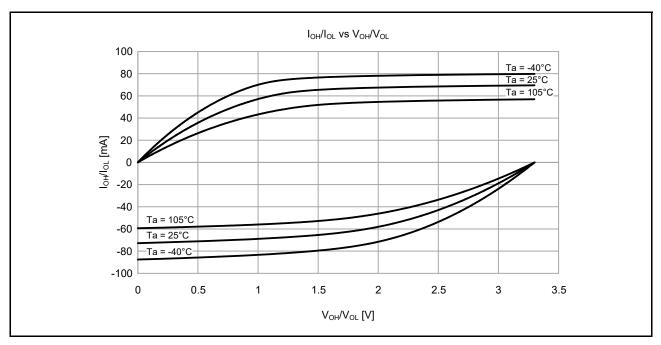


Figure 2.14 V_{OH}/V_{OL} and I_{OH}/I_{OL} temperature characteristics at VCC = 3.3 V when middle drive output is selected (reference data)

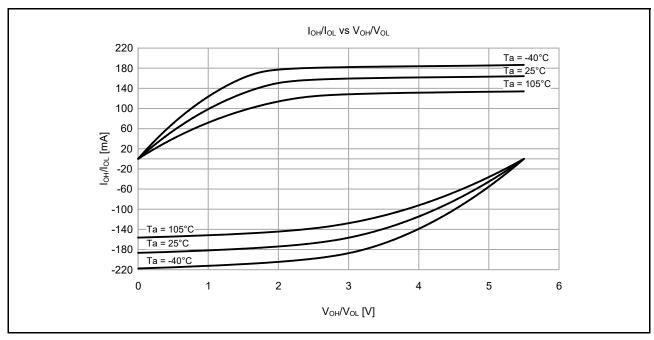


Figure 2.15 V_{OH}/V_{OL} and I_{OH}/I_{OL} temperature characteristics at VCC = 5.5 V when middle drive output is selected (reference data)

2.2.8 IIC I/O Pin Output Characteristics

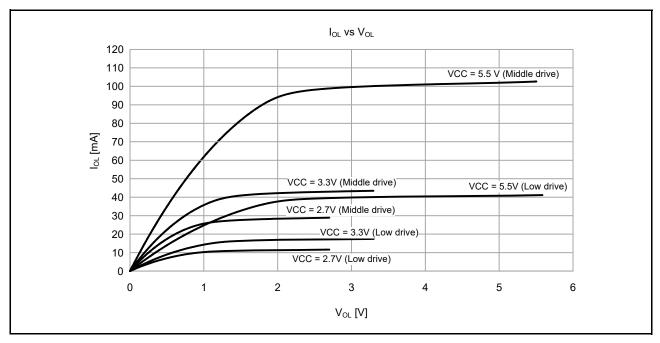


Figure 2.16 V_{OH}/V_{OL} and I_{OH}/I_{OL} voltage characteristics at Ta = 25°C

Operating and Standby Current 2.2.9

Table 2.11 Operating and standby current (1) (1 of 2) Conditions: VCC = AVCC0 = 1.6 to 5.5 V

Parameter					Symbol	Typ*10	Max	Unit	Test condition	
Supply	High-speed	Normal mode	All peripheral clock	ICLK = 48 MHz	I _{CC}	8.3	-	mA	*7	
urrent*1	mode*2		disabled, while (1) code executing from flash*5	ICLK = 32 MHz		5.8	-			
				ICLK = 16 MHz		3.5	-			
				ICLK = 8 MHz		2.2	-			
			All peripheral clock	ICLK = 48 MHz		16.4	-			
			disabled, CoreMark code executing from flash*5	ICLK = 32 MHz		11.3	-			
				ICLK = 16 MHz		6.4	-			
				ICLK = 8 MHz		4.0	-			
			All peripheral clock	ICLK = 48 MHz		18.5	-		*9	
			enabled, while (1) code executing from flash*5	ICLK = 32 MHz		13.8	-		*8	
				ICLK = 16 MHz		7.7	-			
				ICLK = 8 MHz		4.5	-			
			All peripheral clock enabled, code executing from SRAM*5	ICLK = 48 MHz		-	50.0			*9
		Sleep mode	All peripheral clock	ICLK = 48 MHz		3.3	-		*7	
			disabled*5	ICLK = 32 MHz		2.4	-			
				ICLK = 16 MHz		1.8	-			
				ICLK = 8 MHz		1.4	-			
			All peripheral clock	ICLK = 48 MHz		13.4	-		*9	
			enabled* ⁵	ICLK = 32 MHz		10.4	-		*8	
				ICLK = 16 MHz		6.0	-			
				ICLK = 8 MHz		3.6	-			
		Increase during	BGO operation*6	•		2.5	-		-	
	Middle-speed	Normal mode	All peripheral clock	ICLK = 12 MHz	I _{CC}	2.5	-	mA	*7	
	mode*2		disabled, while (1) code executing from flash*5	ICLK = 8 MHz		2.0	-			
			J	ICLK = 1 MHz		0.9	-			
			All peripheral clock	ICLK = 12 MHz		4.7	-			
			disabled, CoreMark code executing from flash*5	ICLK = 8 MHz		3.7	-			
			gg	ICLK = 1 MHz		1.2	-			
			All peripheral clock	ICLK = 12 MHz		5.7	-		*8	
			enabled, while (1) code executing from flash*5	ICLK = 8 MHz		4.3	-			
			J	ICLK = 1 MHz		1.5	-			
			All peripheral clock enabled, code executing from SRAM*5	ICLK = 12 MHz		-	20.0	=		
		Sleep mode	All peripheral clock	ICLK = 12 MHz		1.2	-		*7	
			disabled*5	ICLK = 8 MHz		1.2	-			
				ICLK = 1 MHz		0.8	-			
			All peripheral clock	ICLK = 12 MHz		4.4	-		*8	
			enabled* ⁵	ICLK = 8 MHz		3.4	-			
				ICLK = 1 MHz		1.4	-	1		
		Increase during	BGO operation*6		\dashv	2.5	-	1	_	

Table 2.11 Operating and standby current (1) (2 of 2)

Conditions: VCC = AVCC0 = 1.6 to 5.5 V

Parameter					Symbol	Typ*10	Max	Unit	Test conditions
Supply current* ¹	Low-speed mode*3	Normal mode	All peripheral clock disabled, while (1) code executing from flash*5	ICLK = 1 MHz	I _{CC}	0.4	-	mA	*7
			All peripheral clock disabled, CoreMark code executing from flash*5	ICLK = 1 MHz		0.6	-		
			All peripheral clock enabled, while (1) code executing from flash*5	ICLK = 1 MHz		1.0	-		*8
			All peripheral clock enabled, code executing from SRAM*5	ICLK = 1 MHz		-	2.2		
		Sleep mode	All peripheral clock disabled*5	ICLK = 1 MHz		0.3	-		*7
			All peripheral clock enabled*5	ICLK = 1 MHz		0.9	-		*8
	Low-voltage mode* ³	Normal mode	All peripheral clock disabled, while (1) code executing from flash*5	ICLK = 4 MHz	I _{CC}	1.7	-	mA	*7
			All peripheral clock disabled, CoreMark code executing from flash*5	ICLK = 4 MHz		2.8	-	_	
			All peripheral clock enabled, while (1) code executing from flash*5	ICLK = 4 MHz		3.0	-		*8
			All peripheral clock enabled, code executing from SRAM*5	ICLK = 4 MHz		-	8.0		
		Sleep mode	All peripheral clock disabled*5	ICLK = 4 MHz		1.3	-		*7
			All peripheral clock enabled*5	ICLK = 4 MHz		2.5	-		*8
	Subosc- speed mode*4	Normal mode	All peripheral clock disabled, while (1) code executing from flash*5	ICLK = 32.768 kHz	Icc	8.5	-	μА	*8
			All peripheral clock enabled, while (1) code executing from flash*5	ICLK = 32.768 kHz		14.9	-		
			All peripheral clock enabled, code executing from SRAM*5	ICLK = 32.768 kHz		-	83.0		
		Sleep mode	All peripheral clock disabled*5	ICLK = 32.768 kHz		5.0	-		
			All peripheral clock enabled*5	ICLK = 32.768 kHz		11.4	-		

Note 1. Supply current values do not include output charge/discharge current from all pins. The values apply when internal pull-up MOSs are in the off state.

Note 2. The clock source is HOCO.

Note 3. The clock source is MOCO.

Note 4. The clock source is the sub-clock oscillator.

Note 5. This does not include BGO operation.

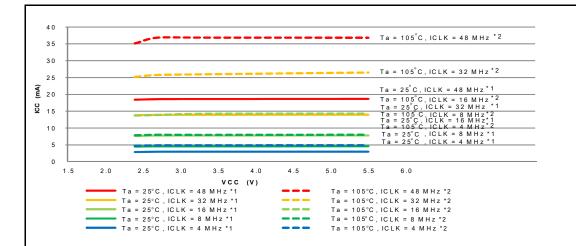
Note 6. This is the increase for programming or erasure of the flash memory for data storage during program execution.

Note 7. FCLK, PCLKB, PCLKC, and PCLKD are set to divided by 64.

Note 8. FCLK, PCLKB, PCLKC, and PCLKD are the same frequency as that of ICLK.

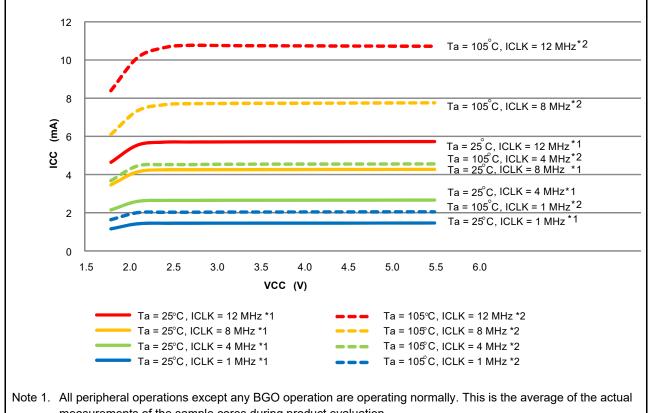
Note 9. FCLK and PCLKB are set to divided by 2 and PCLKD, and PCLKD are the same frequency as that of ICLK.

Note 10. VCC = 3.3 V.



- Note 1. All peripheral operations except any BGO operation are operating normally. This is the average of the actual measurements of the sample cores during product evaluation.
- Note 2. All peripheral operations except any BGO operation are operating at maximum. This is the average of the actual measurements for the upper limit samples during product evaluation.

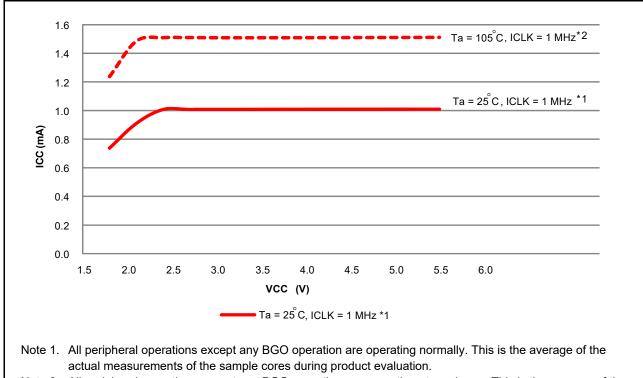
Figure 2.17 Voltage dependency in high-speed operating mode (reference data)



measurements of the sample cores during product evaluation.

Note 2. All peripheral operations except any BGO operation are operating at maximum. This is the average of the actual measurements for the upper limit samples during product evaluation.

Figure 2.18 Voltage dependency in middle-speed operating mode (reference data)



Note 2. All peripheral operations except any BGO operation are operating at maximum. This is the average of the

actual measurements for the upper limit samples during product evaluation.

Figure 2.19 Voltage dependency in Low-speed mode (reference data)

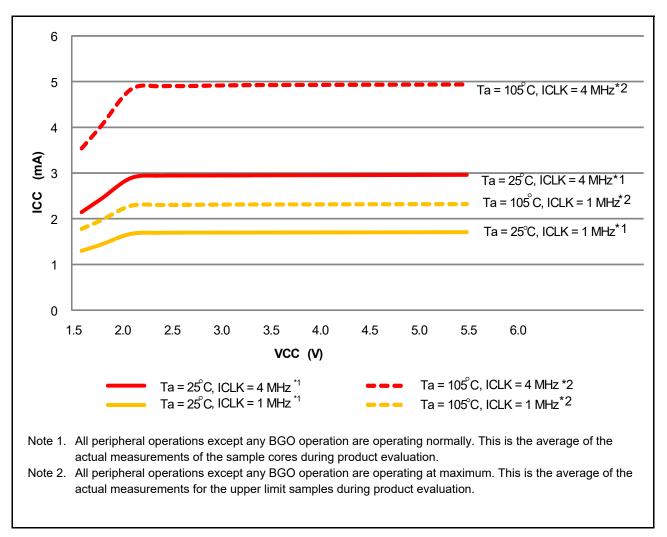
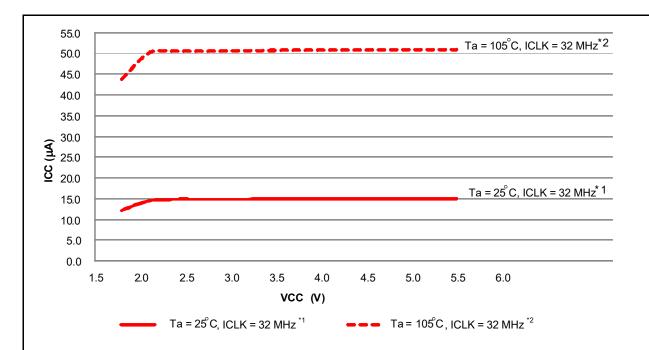


Figure 2.20 Voltage dependency in low-voltage mode (reference data)



- Note 1. All peripheral operations except any BGO operation are operating normally. This is the average of the actual measurements of the sample cores during product evaluation.
- Note 2. All peripheral operations except any BGO operation are operating at maximum. This is the average of the actual measurements for the upper limit samples during product evaluation.

Figure 2.21 Voltage dependency in Subosc-speed mode (reference data)

Table 2.12 Operating and standby current (2)

Conditions: VCC = AVCC0 = 1.6 to 5.5 V

Parameter			Symbol	Typ*4	Max	Unit	Test conditions
Supply	Software Standby	T _a = 25°C	I _{CC}	0.8	4.5	μΑ	-
current*1	mode*2	T _a = 55°C		1.3	7.1		
		T _a = 85°C		3.5	20.2		
		T _a = 105°C		8.7	53.7		
	Increment for RTC low-speed on-chip	•		0.5	-		-
	Increment for RTC sub-clock oscillator	•		0.4	-		SOMCR.SODRV[1:0] are 11b (Low power mode 3)
				1.2	-		SOMCR.SODRV[1:0] are 00b (Normal mode)

- Note 1. Supply current values do not include output charge/discharge current from all pins. The values apply when internal pull-up MOSs are in the off state.
- Note 2. The IWDT and LVD are not operating.
- Note 3. Includes the current of sub-oscillation circuit or low-speed on-chip oscillator.
- Note 4. VCC = 3.3 V.

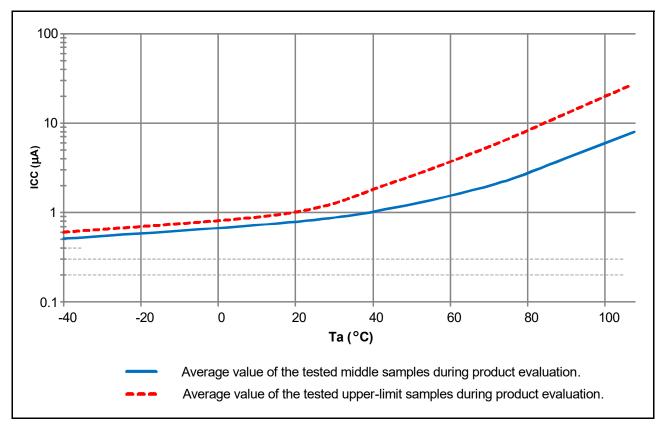


Figure 2.22 Temperature dependency in Software Standby mode all SRAM (reference data)

Table 2.13 Operating and standby current (3)
Conditions: VCC = AVCC0 = 0V, VBATT = 1.6 to 3.6 V, VSS = AVSS0 = 0V

Parameter	•		Symbol	Тур	Max	Unit	Test conditions			
Supply	RTC operation	T _a = 25°C	I _{CC}	0.8	-	μA	VBATT = 2.0 V			
current*1	when VCC is off	T _a = 55°C		0.9	-		SOMCR.SORDRV[1:0] = 11b (Low power mode 3)			
		T _a = 85°C		1.0	-		(Low power mode o)			
		T _a = 105°C		1.1	-					
		T _a = 25°C		0.9	-		VBATT = 3.3 V SOMCR.SORDRV[1:0] = 11b (Low power mode 3)			
		T _a = 55°C		1.0	-					
		T _a = 85°C		1.1	-					
		T _a = 105°C		1.2	-					
		T _a = 25°C		1.5	-		VBATT = 2.0 V			
		T _a = 55°C		1.7	-		SOMCR.SORDRV[1:0] = 00b (Normal mode)			
		T _a = 85°C		2.0	-		(Normal mode)			
		T _a = 105°C		2.2	-					
		T _a = 25°C		1.6	-		VBATT = 3.3 V			
		T _a = 55°C		1.8	-		SOMCR.SORDRV[1:0] = 00b (Normal mode)			
		T _a = 85°C		2.1	-		(
		T _a = 105°C		2.3	-					

Note 1. Supply current values do not include output charge/discharge current from all pins. The values apply when internal pull-up MOSs are in the off state.

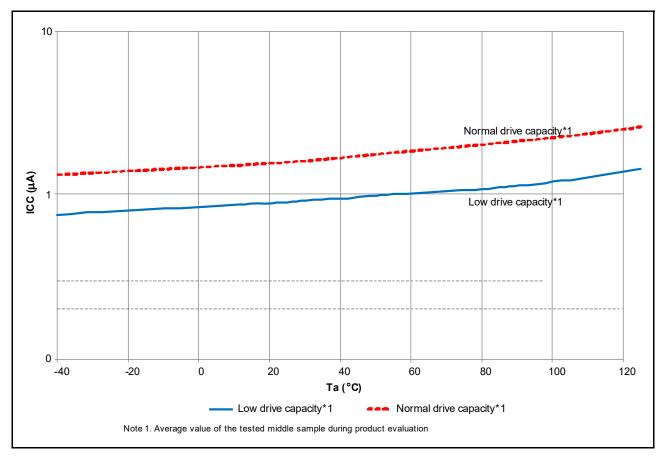


Figure 2.23 Temperature dependency of RTC operation with VCC off (reference data)

Table 2.14 Operating and standby current (4)

Conditions: VCC = AVCC0 = 1.6 to 5.5 V, VREFH0 = 2.7 V to AVCC0

Parameter			Symbol	Min	Тур	Max	Unit	Test conditions
Analog power	During A/D conversion (at	high-speed conversion)	I _{AVCC}	-	-	3.0	mA	-
supply current	During A/D conversion (at	low-power conversion)		-	-	1.0	mA	-
	During D/A conversion (pe	er channel)*1		-	0.4	0.8	mA	-
	Waiting for A/D and D/A co	onversion (all units)*6		-	-	1.0	μA	-
Reference	During A/D conversion		I _{REFH0}	-	-	150	μA	-
power supply current	Waiting for A/D conversion	n (all units)		-	-	60	nA	-
	During D/A conversion		I _{REFH}	-	50	100	μA	-
	Waiting for D/A conversion	n (all units)		-	-	100	μA	-
Temperature sen	sor		I _{TNS}	-	75	-	μΑ	-
Low-Power	Window mode		I _{CMPLP}	-	15	-	μΑ	-
Analog Comparator	Comparator High-speed n	node		-	10	-	μA	-
operating	Comparator Low-speed m	ode		-	2	-	μA	-
current	Comparator Low-speed m	ode using DAC8		-	820	-	μA	-
Operational	Low power mode	1 unit operating	I _{AMP}	-	2.5	4.0	μA	-
Amplifier operating		2 units operating		-	4.5	8.0	μA	-
current		3 units operating		-	6.5	11.0	μA	-
		4 units operating		-	8.5	14.0	μA	-
	High-speed mode	1 unit operating		-	140	220	μA	-
		2 units operating	-	-	280	410	μA	-
		3 units operating		-	420	600	μA	-
		4 units operating		-	560	780	μA	-
LCD operating current	External resistance division f _{LCD} = f _{SUB} = 128 Hz, 1/3		I _{LCD1} *5	-	0.34	-	μА	-
	Internal voltage boosting r f _{LCD} = f _{SUB} = 128 Hz, 1/3	nethod (VLCD.VLCD = 04) B bias, and 4-time slice	I _{LCD2} *5	-	0.92	-	μA	-
	Capacitor split method f _{LCD} = f _{SUB} = 128 Hz, 1/3	B bias, and 4-time slice	I _{LCD3} *5	-	0.19	-	μA	-
USB operating current	During USB communication following settings and con Host controller operation Bulk OUT transfer (64 bulk IN transfer (64 but) Connect peripheral devicable from the USB por	ditions: n is set to full-speed mode ytes) × 1, es) × 1 ices via a 1-meter USB	I _{USBH} *2	-	4.3 (VCC) 0.9 (VCC_USB)*4	-	mA	-
	During USB communication following settings and consider the Device controller operated Bulk OUT transfer (64 bulk IN transfer (64 bytes). Connect the host devices from the USB port.	ditions: cion is set to full-speed mode ytes) × 1, es) × 1	I _{USBF} *2	-	3.6 (VCC) 1.1 (VCC_USB)*4	-	mA	-
	During suspended state u and conditions: Device controller operat (pull up the USB_DP pingular standby mode) Connect the host device from the USB port.	ion is set to full-speed mode	I _{SUSP} *3	-	0.35 (VCC) 170 (VCC_USB)*4	-	μΑ	-

Note 1. The reference power supply current is included in the power supply current value for D/A conversion.

Note 2. Current consumed only by the USBFS.

Note 3. Includes the current supplied from the pull-up resistor of the USB_DP pin to the pull-down resistor of the host device, in addition to the current consumed by the MCU during the suspended state.

Note 4. When VCC = VCC_USB = 3.3 V.

Note 5. Current flowing only to the LCD controller. Not including the current that flows through the LCD panel.

Note 6. When the MCU is in Software Standby mode or the MSTPCRD.MSTPD16 (ADC140 module stop bit) is in the module-stop state.

2.2.10 VCC Rise and Fall Gradient and Ripple Frequency

Table 2.15 Rise and fall gradient characteristics

Conditions: VCC = AVCC0 = 0 to 5.5 V

Parameter		Symbol	Min	Тур	Max	Unit	Test conditions
Power-on VCC rising gradient	Voltage monitor 0 reset disabled at startup (normal startup)	SrVCC	0.02	-	2	ms/V	-
	Voltage monitor 0 reset enabled at startup*1		0.02	-	-		
	SCI/USB boot mode*2		0.02	-	2		

Note 1. When OFS1.LVDAS = 0.

Note 2. At boot mode, the reset from voltage monitor 0 is disabled regardless of the value of OFS1.LVDAS bit.

Table 2.16 Rising and falling gradient and ripple frequency characteristics

Conditions: VCC = AVCC0 = VCC USB = 1.6 to 5.5 V

The ripple voltage must meet the allowable ripple frequency $f_{r(VCC)}$ within the range between the VCC upper limit (5.5 V) and lower limit (1.6 V).

When VCC change exceeds VCC ±10%, the allowable voltage change rising/falling gradient dt/dVCC must be met.

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
Allowable ripple frequency	f _{r (VCC)}	-	-	10	kHz	Figure 2.24 V _{r (VCC)} ≤ VCC × 0.2
		-	-	1	MHz	Figure 2.24 V _{r (VCC)} ≤ VCC × 0.08
		-	-	10	MHz	Figure 2.24 V _{r (VCC)} ≤ VCC × 0.06
Allowable voltage change rising and falling gradient	dt/dVCC	1.0	-	-	ms/V	When VCC change exceeds VCC ±10%

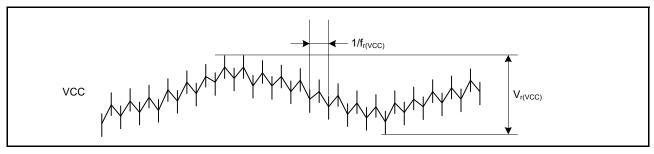


Figure 2.24 Ripple waveform

2.3 AC Characteristics

2.3.1 Frequency

Table 2.17 Operation frequency value in high-speed operating mode

Conditions: VCC = AVCC0 = 2.4 to 5.5 V

Parameter			Symbol	Min	Тур	Max*5	Unit
Operation frequency	System clock (ICLK)*4	2.7 to 5.5 V	f	0.032768	-	48	MHz
frequency		2.4 to 2.7 V		0.032768	-	16	
	Flash interface clock (FCLK)*1, *2, *4	2.7 to 5.5 V		0.032768	-	32	
		2.4 to 2.7 V		0.032768	-	16	
	Peripheral module clock (PCLKA)*4	2.7 to 5.5 V		-	-	48	
		2.4 to 2.7 V		-	-	16	
	Peripheral module clock (PCLKB)*4	2.7 to 5.5 V		-	-	32	
		2.4 to 2.7 V		-	-	16	
	Peripheral module clock (PCLKC)*3, *4	2.7 to 5.5 V		-	-	64	
		2.4 to 2.7 V		-	-	16	
	Peripheral module clock (PCLKD)*4	2.7 to 5.5 V		-	-	64	
		2.4 to 2.7 V		-	-	16	

- Note 1. The lower-limit frequency of FCLK is 1 MHz while programming or erasing the flash memory. When using FCLK for programming or erasing the flash memory at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.
- Note 2. The frequency accuracy of FCLK must be ±3.5% while programming or erasing the flash memory. Confirm the frequency accuracy of the clock source.
- Note 3. The lower-limit frequency of PCLKC is 4 MHz at 2.4 V or above and 1 MHz at below 2.4 V when the 14-bit A/D converter is in use.
- Note 4. See section 8, Clock Generation Circuit in User's Manual for the relationship of frequencies between ICLK, PCLKA, PCLKB, PCLKC, PCLKD, and FCLK.
- Note 5. The maximum value of operation frequency does not include internal oscillator errors. For details on the range of guaranteed operation, see Table 2.22, Clock timing.

Table 2.18 Operation frequency value in middle-speed operating mode

Conditions: VCC = AVCC0 = 1.8 to 5.5 V

Parameter			Symbol	Min	Тур	Max*5	Unit
Operation	System clock (ICLK)*4	2.7 to 5.5 V	f	0.032768	-	12	MHz
frequency		2.4 to 2.7 V		0.032768	-	12	
		1.8 to 2.4 V	1	0.032768	-	8	
	Flash interface clock (FCLK)*1, *2, *4	2.7 to 5.5 V	1	0.032768	-	12	
		2.4 to 2.7 V	1	0.032768	-	12	
		1.8 to 2.4 V		0.032768	-	8	
	Peripheral module clock (PCLKA)*4	2.7 to 5.5 V	1	-	-	12	
		2.4 to 2.7 V	1	-	-	12	
		1.8 to 2.4 V	1	-	-	8	
	Peripheral module clock (PCLKB)*4	2.7 to 5.5 V	1	-	-	12	
		2.4 to 2.7 V	1	-	-	12	
		1.8 to 2.4 V	1	-	-	8	
	Peripheral module clock (PCLKC)*3, *4	2.7 to 5.5 V	1	-	-	12	
		2.4 to 2.7 V	1	-	-	12	
		1.8 to 2.4 V	1	-	-	8	
	Peripheral module clock (PCLKD)*4	2.7 to 5.5 V	1	-	-	12	
		2.4 to 2.7 V	1	-	-	12	
		1.8 to 2.4 V		-	-	8	

Note 1. The lower-limit frequency of FCLK is 1 MHz while programming or erasing the flash memory. When using FCLK for programming or erasing the flash memory at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.

- Note 2. The frequency accuracy of FCLK must be ±3.5% while programming or erasing the flash memory. Confirm the frequency accuracy of the clock source.
- Note 3. The lower-limit frequency of PCLKC is 4 MHz at 2.4 V or above and 1 MHz at below 2.4 V when the 14-bit A/D converter is in use.
- Note 4. See section 8, Clock Generation Circuit in User's Manual for the relationship of frequencies between ICLK, PCLKA, PCLKB, PCLKC, PCLKD, FCLK.
- Note 5. The maximum value of operation frequency does not include internal oscillator errors. For details on the range of guaranteed operation, see Table 2.22, Clock timing.

Table 2.19 Operation frequency value in low-speed operating mode

Conditions: VCC = AVCC0 = 1.8 to 5.5 V

Parameter			Symbol	Min	Тур	Max*4	Unit
Operation	System clock (ICLK)*3	1.8 to 5.5 V	f	0.032768	-	1	MHz
frequency	Flash interface clock (FCLK)*1, *3	1.8 to 5.5 V		0.032768	-	1	
	Peripheral module clock (PCLKA)*3	1.8 to 5.5 V		-	-	1	
	Peripheral module clock (PCLKB)*3	1.8 to 5.5 V		-	-	1	
	Peripheral module clock (PCLKC)*2, *3	1.8 to 5.5 V		-	-	1	
	Peripheral module clock (PCLKD)*3	1.8 to 5.5 V		-	-	1	1

- Note 1. The lower-limit frequency of FCLK is 1 MHz while programming or erasing the flash memory.
- Note 2. The lower-limit frequency of PCLKC is 1 MHz when the A/D converter is in use.
- Note 3. See section 8, Clock Generation Circuit in User's Manual for the relationship of frequencies between ICLK, PCLKA, PCLKB, PCLKC, PCLKD, FCLK.
- Note 4. The maximum value of operation frequency does not include internal oscillator errors. For details on the range of guaranteed operation, see Table 2.22, Clock timing.

Table 2.20 Operation frequency value in low-voltage operating mode

Conditions: VCC = AVCC0 = 1.6 to 5.5 V

Parameter			Symbol	Min	Тур	Max*5	Unit
Operation	System clock (ICLK)*4	1.6 to 5.5 V	f	0.032768	-	4	MHz
frequency	Flash interface clock (FCLK)*1, *2, *4	1.6 to 5.5 V		0.032768	-	4	
	Peripheral module clock (PCLKA)*4	1.6 to 5.5 V		-	-	4	
	Peripheral module clock (PCLKB)*4	1.6 to 5.5 V		-	-	4	
	Peripheral module clock (PCLKC)*3, *4	1.6 to 5.5 V		-	-	4	
	Peripheral module clock (PCLKD)*4	1.6 to 5.5 V		-	-	4	

- Note 1. The lower-limit frequency of FCLK is 1 MHz while programming or erasing the flash memory. When using FCLK for programming or erasing the flash memory at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.
- Note 2. The frequency accuracy of FCLK must be ±3.5% while programming or erasing the flash memory. Confirm the frequency accuracy of the clock source.
- Note 3. The lower-limit frequency of PCLKC is 4 MHz at 2.4 V or above and 1 MHz at below 2.4 V when the 14-Bit A/D converter is in use
- Note 4. See section 8, Clock Generation Circuit in User's Manual for the relationship of frequencies between ICLK, PCLKA, PCLKB, PCLKC, PCLKD, FCLK.
- Note 5. The maximum value of operation frequency does not include internal oscillator errors. For details on the range of guaranteed operation, see Table 2.22, Clock timing.

Table 2.21 Operation frequency value in Subosc-speed operating mode

Conditions: VCC = AVCC0 = 1.8 to 5.5 V

Parameter			Symbol	Min	Тур	Max	Unit
Operation	System clock (ICLK)*3	1.8 to 5.5 V	f	27.8528	32.768	37.6832	kHz
frequency	Flash interface clock (FCLK)*1, *3	1.8 to 5.5 V		27.8528	32.768	37.6832	
	Peripheral module clock (PCLKA)*3	1.8 to 5.5 V		-	-	37.6832	
	Peripheral module clock (PCLKB)*3	1.8 to 5.5 V		-	-	37.6832	
	Peripheral module clock (PCLKC)*2, *3	1.8 to 5.5 V		-	-	37.6832	
	Peripheral module clock (PCLKD)*3	1.8 to 5.5 V		-	-	37.6832	

Note 1. Programming and erasing the flash memory is not possible.

2.3.2 Clock Timing

Table 2.22 Clock timing (1 of 2)

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
EXTAL external clock input cycle time	t _{Xcyc}	50	-	-	ns	Figure 2.25
EXTAL external clock input high pulse width	t _{XH}	20	-	-	ns	
EXTAL external clock input low pulse width	t _{XL}	20	-	-	ns	
EXTAL external clock rising time	t _{Xr}	-	-	5	ns	
EXTAL external clock falling time	t _{Xf}	-	-	5	ns	
EXTAL external clock input wait time*1	t _{EXWT}	0.3	-	-	μs	-
EXTAL external clock input frequency	f _{EXTAL}	-	-	20	MHz	2.4 ≤ VCC ≤ 5.5
		-	-	8		1.8 ≤ VCC < 2.4
		-	-	1		1.6 ≤ VCC < 1.8
Main clock oscillator oscillation frequency	f _{MAIN}	1	-	20	MHz	2.4 ≤ VCC ≤ 5.5
		1	-	8		1.8 ≤ VCC < 2.4
		1	-	4		1.6 ≤ VCC < 1.8
Main clock oscillation stabilization wait time (crystal)*9	t _{MAINOSCWT}	-	-	_*9	ms	-
LOCO clock oscillation frequency	fLOCO	27.8528	32.768	37.6832	kHz	-
LOCO clock oscillation stabilization time	t _{LOCO}	-	-	100	μs	Figure 2.26
IWDT-dedicated clock oscillation frequency	f _{ILOCO}	12.75	15	17.25	kHz	-
MOCO clock oscillation frequency	f _{MOCO}	6.8	8	9.2	MHz	-
MOCO clock oscillation stabilization time	t _{MOCO}	-	-	1	μs	-

Note 2. The 14-bit A/D converter cannot be used.

Note 3. See section 8, Clock Generation Circuit in User's Manual for the relationship of frequencies between ICLK, PCLKA, PCLKB, PCLKC, PCLKD, FCLK.

Table 2.22 Clock timing (2 of 2)

Parameter		Symbol	Min	Тур	Max	Unit	Test conditions
HOCO clock oscillation frequency		f _{HOCO24}	23.64	24	24.36	MHz	$T_a = -40 \text{ to } -20^{\circ}\text{C}$ 1.8 \le VCC \le 5.5
			22.68	24	25.32		$T_a = -40 \text{ to } 85^{\circ}\text{C}$ 1.6 \le VCC < 1.8
			23.76	24	24.24		$T_a = -20 \text{ to } 85^{\circ}\text{C}$ 1.8 \le VCC \le 5.5
			23.52	24	24.48		$T_a = 85 \text{ to } 105^{\circ}\text{C}$ 2.4 \le VCC \le 5.5
		fHOCO32	31.52	32	32.48		$T_a = -40 \text{ to } -20^{\circ}\text{C}$ 1.8 \le VCC \le 5.5
			30.24	32	33.76		$T_a = -40 \text{ to } 85^{\circ}\text{C}$ 1.6 \le VCC < 1.8
			31.68	32	32.32		$T_a = -20 \text{ to } 85^{\circ}\text{C}$ 1.8 \le VCC \le 5.5
			31.36	32	32.64		$T_a = 85 \text{ to } 105^{\circ}\text{C}$ 2.4 \le VCC \le 5.5
		fHOCO48*4	47.28	48	48.72		$T_a = -40 \text{ to } -20^{\circ}\text{C}$ 1.8 \le VCC \le 5.5
			47.52	48	48.48		$T_a = -20 \text{ to } 85^{\circ}\text{C}$ 1.8 \le VCC \le 5.5
			47.04	48	48.96		$T_a = 85 \text{ to } 105^{\circ}\text{C}$ 2.4 \le VCC \le 5.5
		f _{HOCO64} *5	63.04	64	64.96		$T_a = -40 \text{ to } -20^{\circ}\text{C}$ 2.4 \le VCC \le 5.5
			63.36	64	64.64		$T_a = -20 \text{ to } 85^{\circ}\text{C}$ 2.4 \le VCC \le 5.5
			62.72	64	65.28		$T_a = 85 \text{ to } 105^{\circ}\text{C}$ 2.4 \le VCC \le 5.5
HOCO clock oscillation stabilization time*6, *7	Except Low-Voltage mode	t _{HOCO24} t _{HOCO32}	-	-	37.1	μs	Figure 2.27
		t _{HOCO48}	-	-	43.3		
		t _{HOCO64}	-	-	80.6		
	Low-Voltage mode	thoco24 thoco32 thoco48 thoco64	-	-	100.9		
PLL input frequency*2		f _{PLLIN}	4	-	12.5	MHz	-
LL circuit oscillation frequency*2		f _{PLL}	24	-	64	MHz	-
PLL clock oscillation stabilization	time*8	t _{PLL}	-	-	55.5	μs	Figure 2.29
PLL free-running oscillation frequency	ency	f _{PLLFR}	-	8	-	MHz	-
Sub-clock oscillator oscillation fre	quency	f _{SUB}	-	32.768	-	kHz	-
Sub-clock oscillation stabilization	time*3	tSUBOSC	-	-	_*3	s	Figure 2.30

- Note 1. Time until the clock can be used after the Main Clock Oscillator Stop bit (MOSCCR.MOSTP) is set to 0 (operating) when the external clock is stable.
- Note 2. The VCC range that the PLL can be used is 2.4 to 5.5 V.
- Note 3. After changing the setting of the SOSCCR.SOSTP bit so that the sub-clock oscillator operates, only start using the sub-clock after the sub-clock oscillation stabilization wait time elapses, that is greater than or equal to the value recommended by the oscillator manufacturer.
- Note 4. The 48-MHz HOCO can be used within a VCC range of 1.8 V to 5.5 V.
- Note 5. The 64-MHz HOCO can be used within a VCC range of 2.4 V to 5.5 V.
- Note 6. This is a characteristic when HOCOCR.HCSTP bit is set to 0 (oscillation) in MOCO stop state.

 When HOCOCR.HCSTP bit is set to 0 (oscillation) during MOCO oscillation, this specification is shortened by 1 µs.
- Note 7. Whether stabilization time has elapsed can be confirmed by OSCSF.HOCOSF.
- Note 8. This is a characteristic when PLLCR.PLLSTP bit is set to 0 (operation) in MOCO stop state.
 - When PLLCR.PLLSTP bit is set to 0 (operation) during MOCO oscillation, this specification is shortened by 1 µs.
- Note 9. When setting up the main clock, ask the oscillator manufacturer for an oscillation evaluation and use the results as the recommended oscillation stabilization time. Set the MOSCWTCR register to a value equal to or greater than the recommended stabilization time. After changing the setting of the MOSCCR.MOSTP bit so that the main clock oscillator operates, read the OSCSF.MOSCSF flag to confirm that it is 1, then start using the main clock.

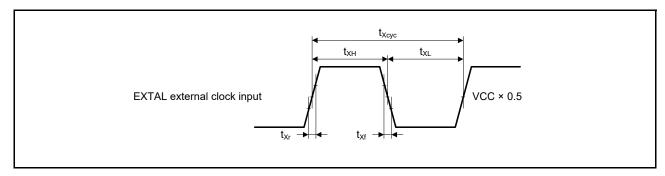


Figure 2.25 EXTAL external clock input timing

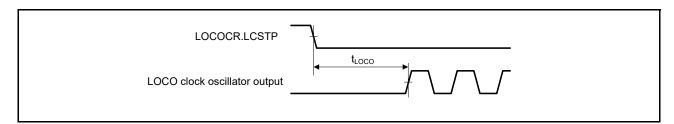


Figure 2.26 LOCO clock oscillation start timing

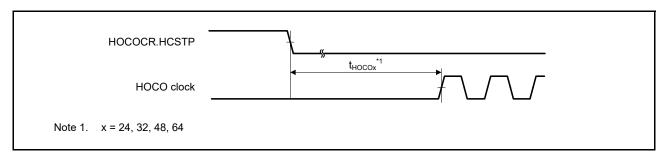


Figure 2.27 HOCO clock oscillation start timing (started by setting HOCOCR.HCSTP bit)

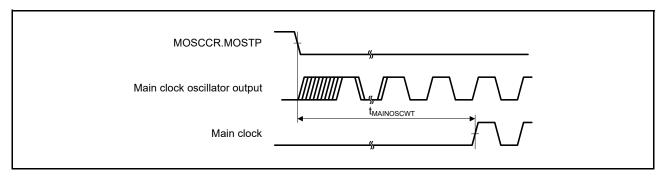


Figure 2.28 Main clock oscillation start timing

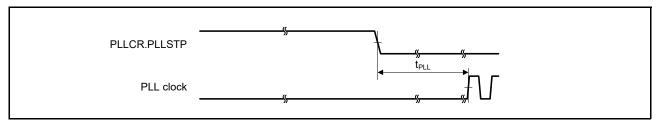


Figure 2.29 PLL clock oscillation start timing (PLL is operated after main clock oscillation has settled)

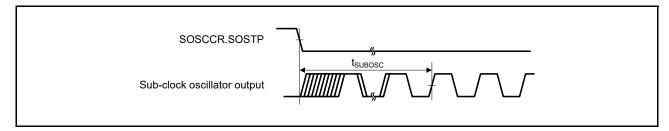


Figure 2.30 Sub-clock oscillation start timing

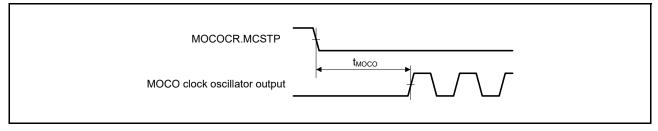


Figure 2.31 MOCO clock oscillation start timing

2.3.3 Reset Timing

Table 2.23 Reset timing

Parameter		Symbol	Min	Тур	Max	Unit	Test conditions
RES pulse width	At power-on	t _{RESWP}	3	-	-	ms	Figure 2.32
	Other than above	t _{RESW}	30	-	-	μs	Figure 2.33
Wait time after RES cancellation	LVD0: enable*1	t _{RESWT}	-	0.7	-	ms	Figure 2.32
(at power-on)	LVD0: disable*2		-	0.3	-		
Wait time after RES cancellation	LVD0: enable*1	t _{RESWT2}	-	0.5	-	ms	Figure 2.33
(during powered-on state)	LVD0: disable*2		-	0.05	-		
Internal reset cancellation time (Watchdog	LVD0: enable*1	t _{RESWT3}	-	0.6	-	ms	-
timer reset, SRAM parity error reset, SRAM ECC error reset, Bus master MPU error reset, Bus slave MPU error reset, Stack pointer error reset, Software reset)	LVD0: disable*2		-	0.15	-	1	

Note 1. When OFS1.LVDAS = 0. Note 2. When OFS1.LVDAS = 1.

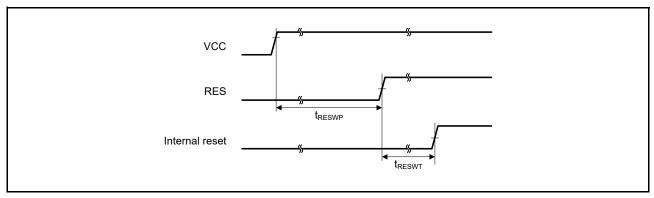


Figure 2.32 Reset input timing at power-on

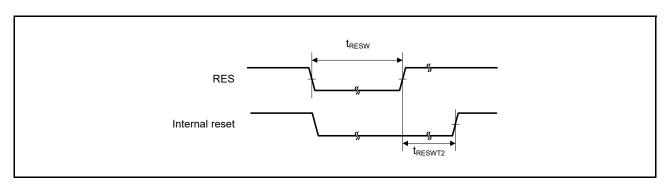


Figure 2.33 Reset input timing

2.3.4 Wakeup Time

Table 2.24 Timing of recovery from low power modes (1)

Parameter				Symbol	Min	Тур	Max	Unit	Test conditions
Recovery time from Software Standby mode*1	High-speed mode	Crystal resonator connected to	System clock source is main clock oscillator (20 MHz)*2	t _{SBYMC}	-	2	3	ms	Figure 2.34
		oscillator PLL (48	System clock source is PLL (48 MHz) with main clock oscillator*2	t _{SBYPC}	-	2	3	ms	
		External clock input to main clock oscillator (20 MHz)*3		t _{SBYEX}	-	14	25	μs	
			System clock source is PLL (48 MHz) with main clock oscillator*3	t _{SBYPE}	-	53	76	μs	
		System clock source is HOCO*4 (HOCO clock is 32 MHz) System clock source is HOCO*4 (HOCO clock is 48 MHz)		t _{SBYHO}	-	43	52	μs	
				t _{SBYHO}	-	44	52	μs	
		System clock so (HOCO clock is 6		t _{SBYHO}	-	82	110	μs	
		System clock so	urce is MOCO	t _{SBYMO}	-	16	25	μs	

Note 1. The division ratio of ICK, FCK, and PCKx is the minimum division ratio within the allowable frequency range. The recovery time is determined by the system clock source.

Table 2.25 Timing of recovery from low power modes (2)

Parameter				Symbol	Min	Тур	Max	Unit	Test conditions
Recovery time from Software Standby mode*1	1 ' 1 ' 1 '		System clock source is main clock oscillator (12 MHz)*2	t _{SBYMC}	-	2	3	ms	Figure 2.34
		main clock oscillator	System clock source is PLL (24 MHz) with main clock oscillator*2	t _{SBYPC}	-	2	3	ms	
		External clock input to main clock oscillator	System clock source is main clock oscillator (12 MHz)*3	t _{SBYEX}	-	2.9	10	μs	
			System clock source is PLL (24 MHz) with main clock oscillator*3	t _{SBYPE}	-	49	76	μs	
		System clock sou	urce is HOCO (24 MHz)	t _{SBYHO}	-	38	50	μs	
		System clock sou	urce is MOCO	t _{SBYMO}		3.5	5.5	μs	

Note 1. The division ratio of ICK, FCK, and PCKx is the minimum division ratio within the allowable frequency range. The recovery time is determined by the system clock source.

Note 2. The Main Clock Oscillator Wait Control Register (MOSCWTCR) is set to 05h.

Note 3. The Main Clock Oscillator Wait Control Register (MOSCWTCR) is set to 00h.

Note 4. The HOCO Clock Wait Control Register (HOCOWTCR) is set to 05h.

Note 5. The HOCO Clock Wait Control Register (HOCOWTCR) is set to 06h.

Note 2. The Main Clock Oscillator Wait Control Register (MOSCWTCR) is set to 05h.

Note 3. The Main Clock Oscillator Wait Control Register (MOSCWTCR) is set to 00h.

Table 2.26 Timing of recovery from low power modes (3)

Parameter						Тур	Max	Unit	Test conditions
Recovery time from Software Standby mode*1	Low-speed mode	Crystal resonator connected to main clock oscillator	System clock source is main clock oscillator (1 MHz)*2	tsвумс	-	2	3	ms	Figure 2.34
		External clock input to main clock oscillator	System clock source is main clock oscillator (1 MHz)*3	t _{SBYEX}	-	28	50	μs	
		System clock so	urce is MOCO	t _{SBYMO}	-	25	35	μs	

Note 1. The division ratio of ICK, FCK, and PCKx is the minimum division ratio within the allowable frequency range. The recovery time is determined by the system clock source.

Table 2.27 Timing of recovery from low power modes (4)

Parameter							Max	Unit	Test conditions
Recovery time from Software Standby mode*1	Low-voltage mode	Crystal resonator connected to main clock oscillator	System clock source is main clock oscillator (4 MHz)*2	t _{SBYMC}	-	2	3	ms	Figure 2.34
		External clock input to main clock oscillator	System clock source is main clock oscillator (4 MHz)*3	t _{SBYEX}	-	108	130	μs	
		System clock sou	ırce is HOCO	t _{SBYHO}	-	108	130	μs	

Note 1. The division ratio of ICK, FCK, and PCKx is the minimum division ratio within the allowable frequency range. The recovery time is determined by the system clock source. When multiple oscillators are active, the recovery time can be determined by the following expression.

Table 2.28 Timing of recovery from low power modes (5)

Parameter						Max	Unit	Test conditions
Recovery time from Software Standby mode*1	Subosc-speed mode	System clock source is sub-clock oscillator (32.768 kHz)	t _{SBYSC}	-	0.85	1	ms	Figure 2.34
		System clock source is LOCO (32.768 kHz)	t _{SBYLO}	-	0.85	1.2	ms	

Note 1. The sub-clock oscillator or LOCO itself continues to oscillate in Software Standby mode during Subosc-speed mode.

Note 2. The Main Clock Oscillator Wait Control Register (MOSCWTCR) is set to 05h.

Note 3. The Main Clock Oscillator Wait Control Register (MOSCWTCR) is set to 00h.

Note 2. The Main Clock Oscillator Wait Control Register (MOSCWTCR) is set to 05h.

Note 3. The Main Clock Oscillator Wait Control Register (MOSCWTCR) is set to 00h.

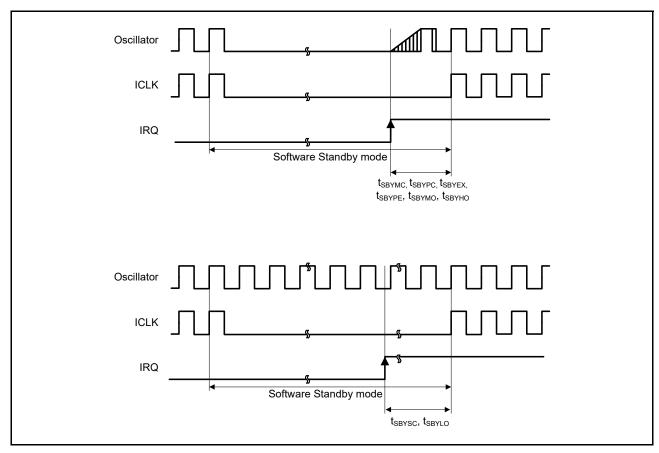


Figure 2.34 Software Standby mode cancellation timing

Table 2.29 Timing of recovery from low power modes (6)

Parameter		Symbol	Min	Тур	Max	Unit	Test conditions
Recovery time from Software Standby	High-speed mode System clock source is HOCO	t _{SNZ}	-	36	45	μs	Figure 2.35
mode to Snooze mode	Middle-speed mode System clock source is MOCO	t _{SNZ}	-	1.3	3.6	μs	
	Low-speed mode System clock source is MOCO	t _{SNZ}	-	10	13	μs	
	Low-voltage mode System clock source is HOCO	t _{SNZ}	-	87	110	μs	

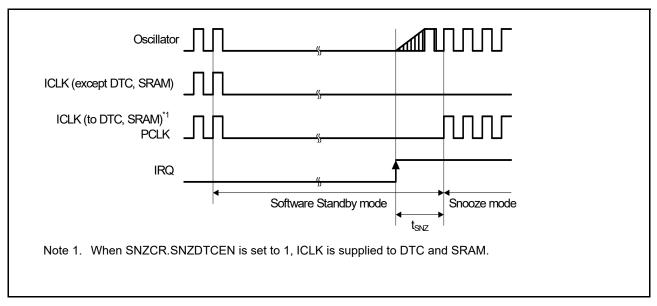


Figure 2.35 Software Standby mode to Snooze mode recovery timing

2.3.5 NMI and IRQ Noise Filter

Table 2.30 NMI and IRQ noise filter

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions				
NMI pulse width	t _{NMIW}	200	-	-	ns	NMI digital filter disabled	t _{Pcyc} × 2 ≤ 200 ns			
		t _{Pcyc} × 2*1	-	-			t _{Pcyc} × 2 > 200 ns			
		200	-	-		NMI digital filter enabled	t _{NMICK} × 3 ≤ 200 ns			
		t _{NMICK} × 3.5*2	-	-			t _{NMICK} × 3 > 200 ns			
IRQ pulse width	t _{IRQW}	200	-	-	ns	IRQ digital filter disabled	t _{Pcyc} × 2 ≤ 200 ns			
		t _{Pcyc} × 2*1	-	-			t _{Pcyc} × 2 > 200 ns			
		200	-	-		IRQ digital filter enabled	t _{IRQCK} × 3 ≤ 200 ns			
		t _{IRQCK} × 3.5*3	-	-			t _{IRQCK} × 3 > 200 ns			

Note: 200 ns minimum in Software Standby mode.

Note: If the clock source is switched, add 4 clock cycles of the switched source.

Note 1. t_{Pcyc} indicates the cycle of PCLKB.

Note 2. t_{NMICK} indicates the cycle of the NMI digital filter sampling clock.

Note 3. t_{IRQCK} indicates the cycle of the IRQi digital filter sampling clock (i = 0 to 12, 14, 15).

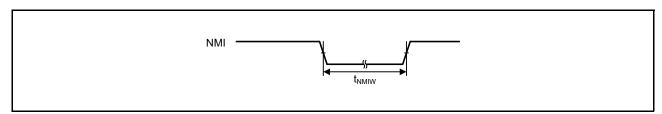


Figure 2.36 NMI interrupt input timing

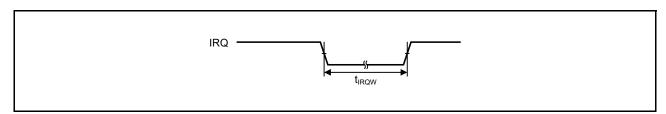


Figure 2.37 IRQ interrupt input timing

2.3.6 I/O Ports, POEG, GPT, AGT, KINT, and ADC14 Trigger Timing

Table 2.31 I/O Ports, POEG, GPT, AGT, KINT, and ADC14 trigger timing

Parameter			Symbol	Min	Max	Unit	Test conditions
I/O ports	Input data pulse width		t _{PRW}	1.5	-	t _{Pcyc}	Figure 2.38
	Input/output data cycle (P002, P00	3, P004, P007)	t _{POcyc}	10	-	us	
POEG	POEG input trigger pulse width		t _{POEW}	3	-	t _{Pcyc}	Figure 2.39
GPT	Input capture pulse width	Single edge	t _{GTICW}	1.5	-	t _{PDcyc}	Figure 2.40
		Dual edge		2.5	-		
AGT	AGTIO, AGTEE input cycle	2.7 V ≤ VCC ≤ 5.5 V	t _{ACYC} *1	250	-	ns	Figure 2.41
		2.4 V ≤ VCC < 2.7 V		500	-	ns	
		1.8 V ≤ VCC < 2.4 V		1000	-	ns]
		1.6 V ≤ VCC < 1.8 V		2000	-	ns	
	AGTIO, AGTEE input high level width, low-level width	2.7 V ≤ VCC ≤ 5.5 V	t _{ACKWH} ,	100	-	ns	1
		2.4 V ≤ VCC < 2.7 V	t _{ACKWL}	200	-	ns	
		1.8 V ≤ VCC < 2.4 V		400	-	ns	
		1.6 V ≤ VCC < 1.8 V		800	-	ns	
	AGTIO, AGTO, AGTOA, AGTOB	2.7 V ≤ VCC ≤ 5.5 V	t _{ACYC2}	62.5	-	ns	Figure 2.41
	output cycle	2.4 V ≤ VCC < 2.7 V		125	-	ns	
		1.8 V ≤ VCC < 2.4 V		250	-	ns	
		1.6 V ≤ VCC < 1.8 V		500	-	ns	
ADC14	14-bit A/D converter trigger input po	ulse width	t _{TRGW}	1.5	-	t _{Pcyc}	Figure 2.42
KINT	KRn (n = 00 to 07) pulse width		t _{KR}	250	-	ns	Figure 2.43

Note 1. Constraints on input cycle:

When not switching the source clock: $t_{\text{Pcyc}} \times 2 < t_{\text{ACYC}}$ should be satisfied.

When switching the source clock: $t_{Pcyc} \times 6 < t_{ACYC}$ should be satisfied.

Note: t_{Pcyc} : PCLKB cycle, t_{PDcyc} : PCLKD cycle

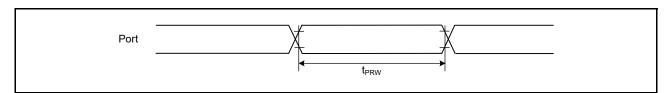


Figure 2.38 I/O ports input timing

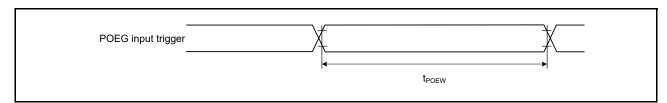


Figure 2.39 POEG input trigger timing

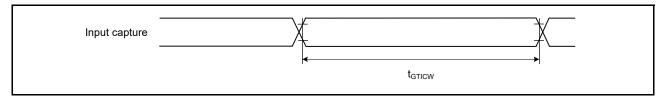


Figure 2.40 GPT input capture timing

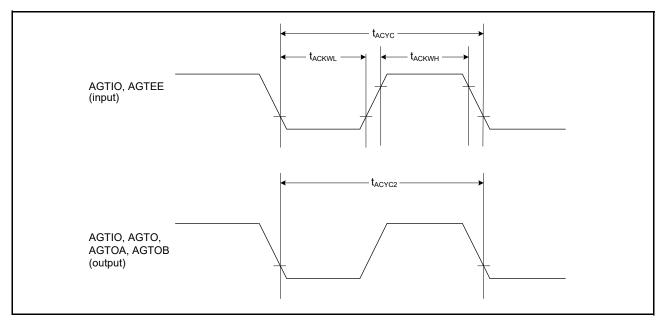


Figure 2.41 AGT I/O timing

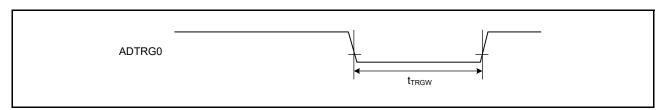


Figure 2.42 ADC14 trigger input timing

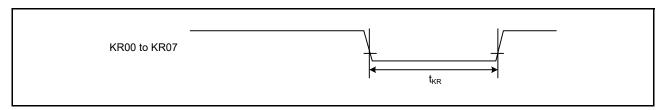


Figure 2.43 Key interrupt input timing

2.3.7 CAC Timing

Table 2.32 CAC timing

Parame	ter		Symbol	Min	Тур	Max	Unit	Test conditions
CAC	CACREF input pulse width	t _{PBcyc} *1 ≤ t _{cac} *2	t _{CACREF}	$4.5 \times t_{cac} + 3 \times t_{PBcyc}^{*1}$	-	-	ns	-
		t _{PBcyc} *1 > t _{cac} *2		$5 \times t_{cac} + 6.5 \times t_{PBcyc}^{*1}$	-	-	ns	

Note 1. t_{PBcyc} : PCLKB cycle.

Note 2. t_{cac}: CAC count clock source cycle.

2.3.8 SCI Timing

Table 2.33 SCI timing (1)

Parameter			Symbol	Min	Max	Unit*1	Test conditions	
SCI	Input clock cycle	Asynchronous		t _{Scyc}	4	-	t _{Pcyc}	Figure 2.44
		Clock synchro	nous	1	6	-		
	Input clock pulse width			t _{SCKW}	0.4	0.6	t _{Scyc}	
	Input clock rise time			t _{SCKr}	-	20	ns	
	Input clock fall time			t _{SCKf}	-	20	ns	
	Output clock cycle	Asynchronous		t _{Scyc}	6	-	t _{Pcyc}	
		Clock synchronous			4	-		
	Output clock pulse w	Output clock pulse width			0.4	0.6	t _{Scyc}	
	Output clock rise time		1.8 V or above	t _{SCKr}	-	20	ns	
					-	30		
	Output clock fall time	Output clock fall time		t _{SCKf}	-	20	ns	
					-	30		
	Transmit data delay (master)	Clock synchronous	1.8 V or above	t _{TXD}	-	40	ns ns	Figure 2.45
			1.6 V or above		-	45		
	Transmit data delay (slave)	Clock synchronous	2.7 V or above		-	55		
			2.4 V or above		-	60		
			1.8 V or above		-	100		
			1.6 V or above		-	125		
	Receive data setup time (master)	Clock synchronous	2.7 V or above	t _{RXS}	45	-	ns	
			2.4 V or above		55	-		
			1.8 V or above		90	-		
			1.6 V or above		110	-		
	Receive data setup	Clock synchronous	2.7 V or above		40	-		
	time (slave)		1.6 V or above		45	-		
	Receive data hold time (master)	Clock synchronous		t _{RXH}	5	-	ns	
	Receive data hold time (slave)	Clock synchronous		t _{RXH}	40	-	ns	

Note 1. t_{Pcyc} : PCLKA cycle.

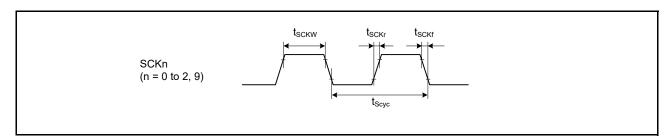


Figure 2.44 SCK clock input timing

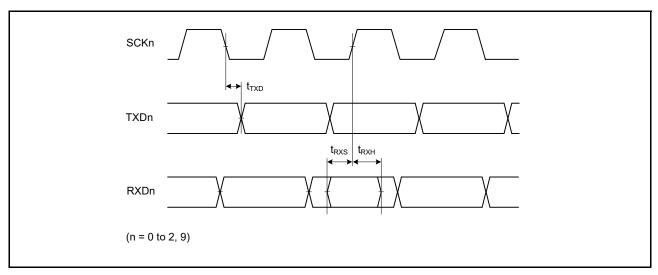


Figure 2.45 SCI input/output timing in clock synchronous mode

Table 2.34 SCI timing (2) (1 of 2)

Parameter				Symbol	Min	Max	Unit	Test conditions
Simple SPI	SCK clock cycle output (master)			t _{SPcyc}	4	65,536	t _{Pcyc}	Figure 2.46
	SCK clock cycle input (slave)				6	65,536		
	SCK clock high pulse width			t _{SPCKWH}	0.4	0.6	t _{SPcyc}	
	SCK clock low pulse width			t _{SPCKWL}	0.4	0.6	t _{SPcyc}	
	SCK clock rise and fall time 1.8 V or above		t _{SPCKr,} t _{SPCKf}	-	20	ns		
	1.6 V or above			-	30			
	Data input setup time	Master	2.7 V or above	- 00 - - -	45	-	ns	Figure 2.47 to Figure 2.50
			2.4 V or above		55	-		
			1.8 V or above		80	-		
			1.6 V or above		110	-		
		Slave	2.7 V or above		40	-		
			1.6 V or above		45	-		
	Data input hold time	ata input hold time Master Slave		t _H	33.3	-	ns	
					40	-		
	SS input setup time			t _{LEAD}	1	-	t _{SPcyc}]
	SS input hold time			t _{LAG}	1	-	t _{SPcyc}	
	Data output delay	Master	1.8 V or above		-	40	ns	
			1.6 V or above		-	50		
		Slave	2.4 V or above		-	65		
			1.8 V or above		-	100		
			1.6 V or above		-	125		
	Data output hold time	Master	2.7 V or above		-10	-	ns	
			2.4 V or above		-20	-		
			1.8 V or above		-30	-		
			1.6 V or above		-40	-		
		Slave			-10	-		
	Data rise and fall time	Master	1.8 V or above	t _{Dr,} t _{Df}	-	20	ns	
			1.6 V or above		-	30		
		Slave	1.8 V or above		-	20		
			1.6 V or above	1	-	30		

Table 2.34 SCI timing (2) (2 of 2)

Parameter		Symbol	Min	Max	Unit	Test conditions
Simple SPI	Slave access time	t _{SA}	-	10 (PCLKA > t _{Pcyc} 32 MHz), 6 (PCLKA ≤ 32 MHz)		Figure 2.49 and Figure 2.50
	Slave output release time	t _{REL}	-	10 (PCLKA > 32 MHz), 6 (PCLKA ≤ 32 MHz)	t _{Pcyc}	

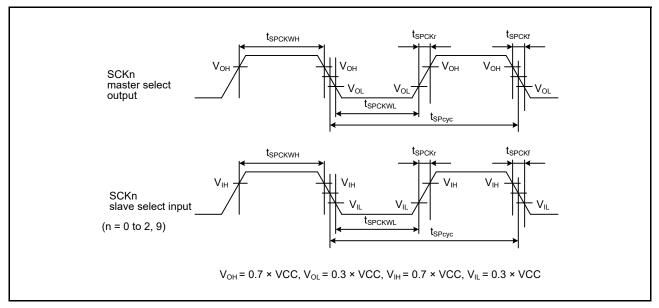


Figure 2.46 SCI simple SPI mode clock timing

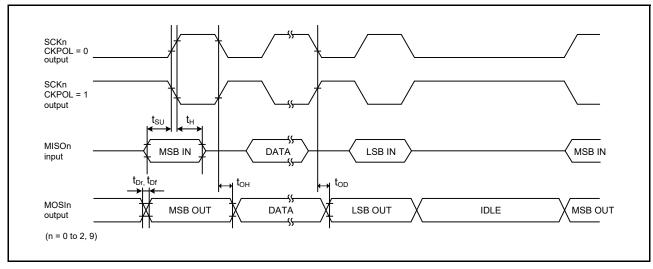


Figure 2.47 SCI simple SPI mode timing for master when CKPH = 1

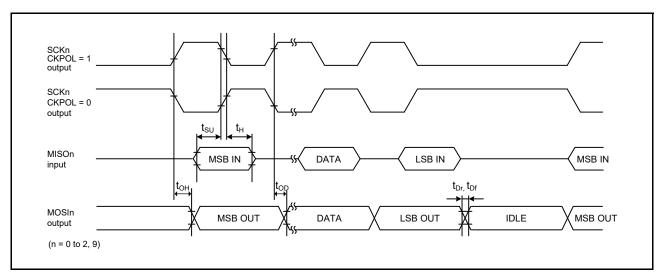


Figure 2.48 SCI simple SPI mode timing for master when CKPH = 0

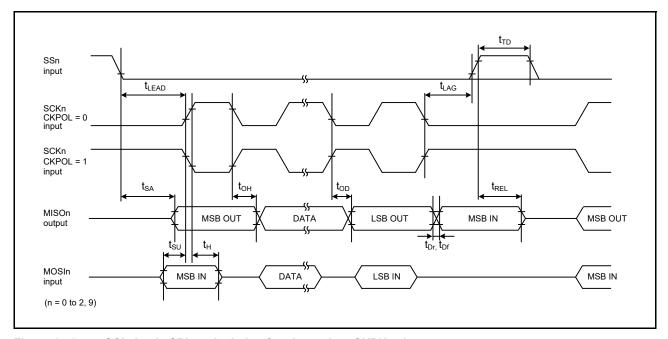


Figure 2.49 SCI simple SPI mode timing for slave when CKPH = 1

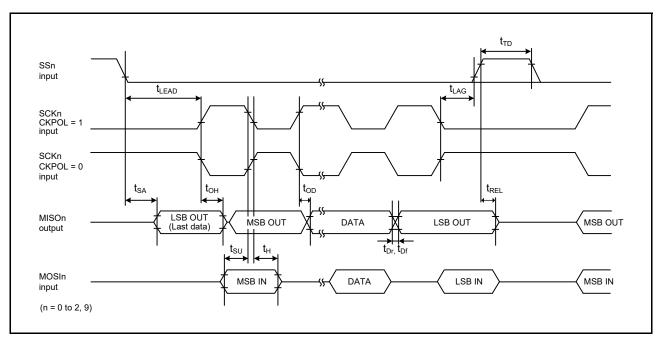


Figure 2.50 SCI simple SPI mode timing for slave when CKPH = 0

Table 2.35 SCI timing (3) Conditions: VCC = 2.7 to 5.5 V

Parameter	Parameter			Max	Unit	Test conditions
Simple I ² C	SDA input rise time	t _{Sr}	t _{Sr} -		ns	Figure 2.51
(Standard mode)	SDA input fall time	t _{Sf}	-	300	ns	
	SDA input spike pulse removal time	t _{SP}	0	4 × t _{IICcyc} *1	ns]
	Data input setup time	t _{SDAS}	250	-	ns]
	Data input hold time	t _{SDAH}	0	-	ns]
	SCL, SDA capacitive load	C _b *2	-	400	pF]
Simple I ² C	SDA input rise time	t _{Sr}	-	300	ns	Figure 2.51
(Fast mode)	SDA input fall time	t _{Sf}	-	300	ns	For all ports except P408, use
	SDA input spike pulse removal time	t _{SP}	0	4 × t _{IICcyc} *1	ns	PmnPFS.DSCR
	Data input setup time	t _{SDAS}	100	-	ns	of middle drive. For port P408,
	Data input hold time	t _{SDAH}	0	-	ns	use
	SCL, SDA capacitive load	C _b *1	-	400	pF	PmnPFS.DSCR1 /DSCR of middle drive for IIC fast-mode.

Note 1. tIICcyc: Clock cycle selected by the SMR.CKS[1:0] bits.

Note 2. Cb indicates the total capacity of the bus line.

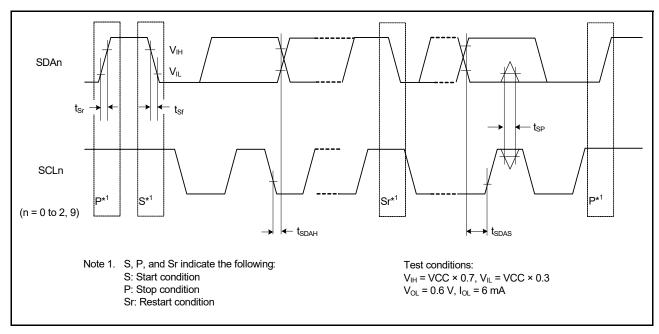


Figure 2.51 SCI simple IIC mode timing

2.3.9 SPI Timing

Table 2.36 SPI timing (1 of 2)
Conditions: Middle drive output is selected in the Port Drive Capability bit in PmnPFS register

Parar	neter			Symbol	Min	Max	Unit*1	Test conditions
SPI	RSPCK clock cycle	Master		t _{SPcyc}	2*4	4096	t _{Pcyc}	Figure 2.52
		Slave			6	4096		
	RSPCK clock high pulse width	ulse width		t _{SPCKWH}	(t _{SPcyc} - t _{SPCKr} - t _{SPCKf}) / 2 - 3	-	ns	
		Slave			3 × t _{Pcyc}	-		
	RSPCK clock low pulse width			t _{SPCKWL}	(t _{SPcyc} - t _{SPCKr} - t _{SPCKf}) / 2 - 3	-	ns	
					3 × t _{Pcyc}	-		
	RSPCK clock rise	Output	2.7 V or above	t _{SPCKr,}	-	10	ns	1
	and fall time		2.4 V or above	t _{SPCKf}	-	15		
			1.8 V or above	Ī	-	20		
			1.6 V or above	Ī	-	30		
		Input			-	1	μs	
	Data input setup time	Master		t _{SU}	10	-	ns	Figure 2.53 to
		Slave	2.4 V or above	1	10	-		Figure 2.58
			1.8 V or above	Ī	15	-		
			1.6 V or above		20	-		
	Data input hold time	Master (RSPCK is PCLKA/2)		t _{HF}	0	-	ns	
		Master (RSPCK is other than above.)		t _H	t _{Pcyc}	-		
		Slave		t _H	20	-		
	SSL setup time	Master	1.8 V or above	t _{LEAD}	-30 + N × t _{Spcyc} *2	-	ns	1
		1.6 V or above			-50 + N × t _{Spcyc} *2	-		
		Slave			6 × t _{Pcyc}	-		
	SSL hold time	Master		t _{LAG}	-30 + N × t _{Spcyc} *3	-		
		Slave			6 × t _{Pcyc}	-		

Table 2.36 SPI timing (2 of 2)

Conditions: Middle drive output is selected in the Port Drive Capability bit in PmnPFS register

meter			Symbol	Min	Max	Unit*1	Test conditions
Data output delay	Master	2.7 V or above	t _{OD}	-	14	ns	Figure 2.53 to
		2.4 V or above	1	-	20		Figure 2.58
		1.8 V or above	1	-	25	1	
		1.6 V or above	1	-	30	1	
	Slave	2.7 V or above	1	-	50	1	
		2.4 V or above	1	-	60	1	
		1.8 V or above	1	-	85	1	
		1.6 V or above	1	-	110	1	
Data output hold time	Master	-	t _{OH}	0	-	ns	
	Slave		1	0	-	1	
Successive transmission delay	Master		t _{TD}	t _{SPcyc} + 2 × t _{Pcyc}	8 × t _{SPcyc} + 2 × t _{Pcyc}	ns	
	Slave		1	6 × t _{Pcyc}	-		
MOSI and MISO rise	I fall time	2.7 V or above	t _{Dr,} t _{Df}	-	10	ns	
and fall time		2.4 V or above		-	15		
		1.8 V or above	1	-	20		
		1.6 V or above	1	-	30		
	Input	Input		-	1	μs	
SSL rise and fall time	Output	2.7 V or above	t _{SSLr,}	-	10	ns	1
		2.4 V or above	t _{SSLf}	-	15		
		1.8 V or above	1	-	20		
		1.6 V or above	1	-	30		
	Input	•		-	1	μs	1
Slave access time	•	2.4 V or above	t _{SA}	-	2 × t _{Pcyc} + 100	ns	Figure 2.57 and
		1.8 V or above		-	2 × t _{Pcyc} + 140	1	Figure 2.58
	1.6 V or above		1	-	2 × t _{Pcyc} + 180	1	
Slave output release	Slave output release time 2.4 V or above 1.8 V or above		t _{REL}	-	2 × t _{Pcyc} + 100	ns	1
			1	-	2 × t _{Pcyc} + 140	1	
		1.6 V or above	1	-	2 × t _{Pcyc} + 180	1	

Note 1. t_{Pcyc}: PCLKA cycle.

Note 2. N is set as an integer from 1 to 8 by the SPCKD register.

Note 3. N is set as an integer from 1 to 8 by the SSLND register.

Note 4. The upper limit of RSPCK is 16 MHz.

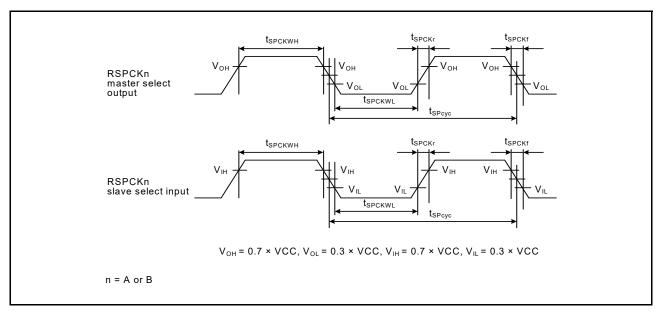


Figure 2.52 SPI clock timing

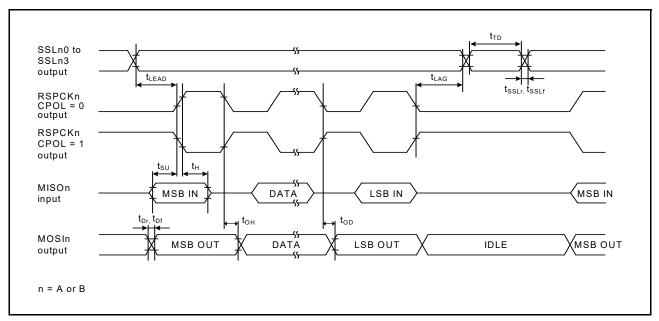


Figure 2.53 SPI timing for master when CPHA = 0 and the bit rate is set to any value other than PCLKA/2

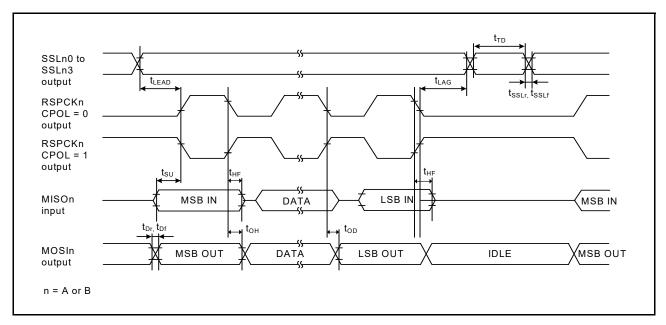


Figure 2.54 SPI timing for master when CPHA = 0 and the bit rate is set to PCLKA/2

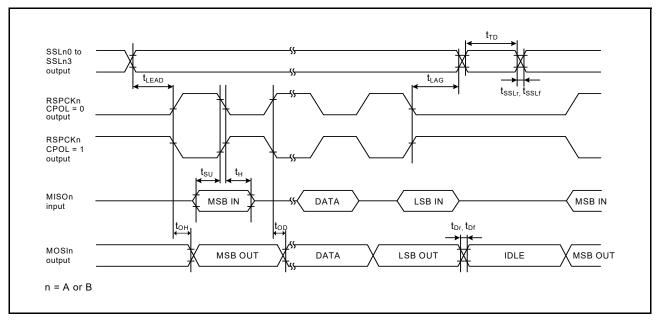


Figure 2.55 SPI timing for master when CPHA = 1 and the bit rate is set to any value other than PCLKA/2

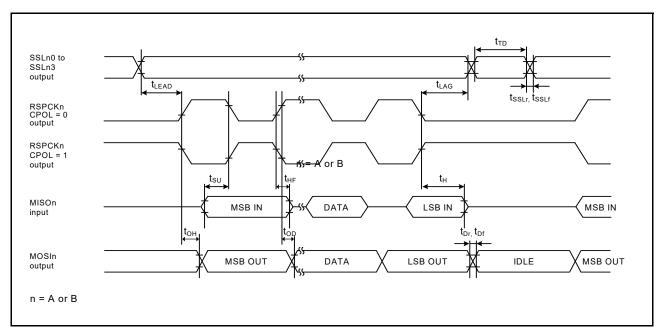


Figure 2.56 SPI timing for master when CPHA = 1 and the bit rate is set to PCLKA/2

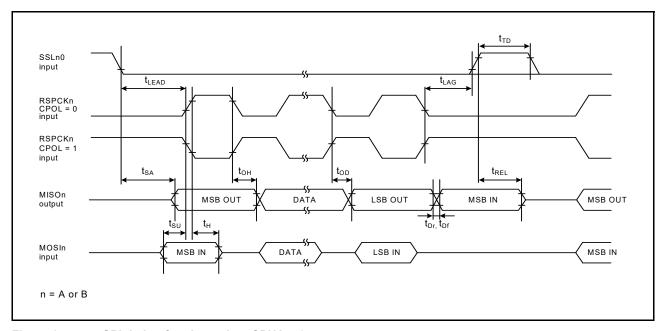


Figure 2.57 SPI timing for slave when CPHA = 0

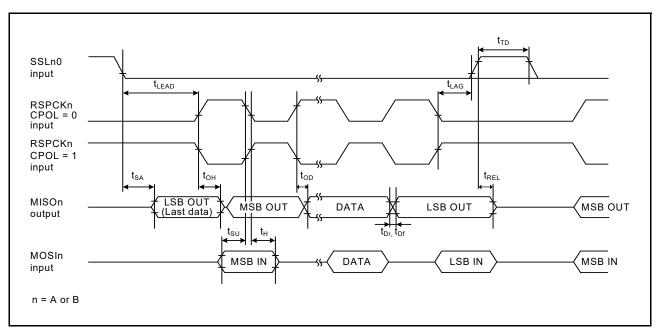


Figure 2.58 SPI timing for slave when CPHA = 1

2.3.10 IIC Timing

Table 2.37 IIC timing (1 of 2) Conditions: VCC = 2.7 to 5.5 V

Parameter		Symbol	Min*1	Max	Unit	Test conditions
IIC (standard mode,	SCL input cycle time	t _{SCL}	6 (12) × t _{IICcyc} + 1300	-	ns	Figure 2.59
SMBus)	SCL input high pulse width	t _{SCLH}	3 (6) × t _{IICcyc} + 300	-	ns	
	SCL input low pulse width	t _{SCLL}	3 (6) × t _{IICcyc} + 300	-	ns	
	SCL, SDA input rise time	t _{Sr}	-	1,000	ns	1
	SCL, SDA input fall time	t _{Sf}	-	300	ns	1
	SCL, SDA input spike pulse removal time	t _{SP}	0	1 (4) × t _{IICcyc}	ns	
	SDA input bus free time (When wakeup function is disabled)	t _{BUF}	3 (6) × t _{IICcyc} + 300	-	ns	
	SDA input bus free time (When wakeup function is enabled)	t _{BUF}	3 (6) × t _{IICcyc} + 4 × t _{Pcyc} + 300	-	ns	
	START condition input hold time (When wakeup function is disabled)	t _{STAH}	t _{IICcyc} + 300	-	ns	
	START condition input hold time (When wakeup function is enabled)	t _{STAH}	1 (5) × t _{IICcyc} + t _{Pcyc} + 300	-	ns	
	Repeated START condition input setup time	t _{STAS}	1,000	-	ns	1
	STOP condition input setup time	t _{STOS}	1,000	-	ns	1
	Data input setup time	t _{SDAS}	t _{IICcyc} + 50	-	ns	
	Data input hold time	t _{SDAH}	0	-	ns	
	SCL, SDA capacitive load	C _b	-	400	pF	

Table 2.37 IIC timing (2 of 2) Conditions: VCC = 2.7 to 5.5 V

Parameter		Symbol	Min*1	Max	Unit	Test conditions
IIC (Fast mode)	SCL input cycle time	t _{SCL}	6 (12) × t _{IICcyc} + 600	-	ns	Figure 2.59 For all ports
	SCL input high pulse width	t _{SCLH}	3 (6) × t _{IICcyc} + 300	-	ns	except P408, use PmnPFS.DSC
	SCL input low pulse width	t _{SCLL}	3 (6) × t _{IICcyc} + 300	-	ns	R of middle drive.
	SCL, SDA input rise time	t _{Sr}	-	300	ns	For port P408, use
	SCL, SDA input fall time	t _{Sf}	-	300	ns	PmnPFS.DSC
	SCL, SDA input spike pulse removal time	t _{SP}	0	1 (4) × t _{IICcyc}	ns	R1/DSCR of middle drive for IIC fast-
	SDA input bus free time (When wakeup function is disabled)	t _{BUF}	3 (6) × t _{IICcyc} + 300	-	ns	mode.
	SDA input bus free time (When wakeup function is enabled)	t _{BUF}	3 (6) × t _{IICcyc} + 4 × t _{Pcyc} + 300	-	ns	
	START condition input hold time (When wakeup function is disabled)	t _{STAH}	t _{IICcyc} + 300	-	ns	
	START condition input hold time (When wakeup function is enabled)	t _{STAH}	1(5) × t _{IICcyc} + t _{Pcyc} + 300	-	ns	
	Repeated START condition input setup time	t _{STAS}	300	-	ns	
	STOP condition input setup time	t _{STOS}	300	-	ns	
	Data input setup time	t _{SDAS}	t _{IICcyc} + 50	-	ns	
	Data input hold time	t _{SDAH}	0	-	ns	
	SCL, SDA capacitive load	C _b	-	400	pF	

Note: t_{IICcyc}: IIC internal reference clock (IICφ) cycle, t_{Pcyc}: PCLKB cycle

Note 1. The value in parentheses apply when ICMR3.NF[1:0] is set to 11b while the digital filter is enabled with ICFER.NFE set to 1.

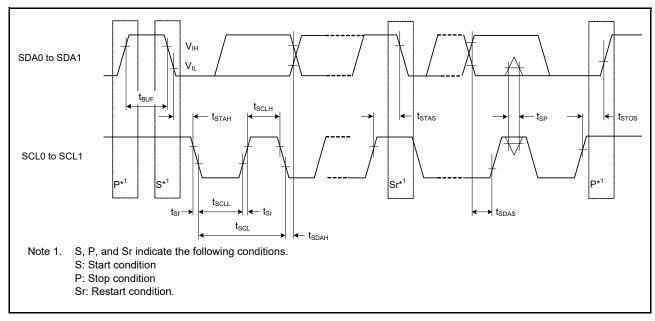


Figure 2.59 IIC bus interface input/output timing

2.3.11 SSIE Timing

Table 2.38 SSIE timing Conditions: VCC = 1.6 to 5.5 V

Paramet	ter		Symbol	Min	Max	Unit	Test conditions
SSIE	AUDIO_CLK input	2.7 V or above	t _{AUDIO}	-	25	MHz	-
	frequency	1.6 V or above		-	4		
	Output clock period	•	t _O	250	-	ns	Figure 2.60
	Input clock period		t _l	250	-	ns	
	Clock high pulse	1.8 V or above	t _{HC}	100	-	ns	
	width	1.6 V or above		200	-		
	Clock low pulse	1.8 V or above	t _{LC}	100	-	ns	1
width		1.6 V or above		200	-		
	Clock rise time		t _{RC}	-	25	ns	
	Data delay	2.7 V or above	t _{DTR}	-	65	ns	Figure 2.61,
		1.8 V or above		-	105		Figure 2.62
		1.6 V or above		-	140		
	Set-up time	2.7 V or above	t _{SR}	65	-	ns	
		1.8 V or above		90	-		
		1.6 V or above		140	-		
Hold time		•	t _{HTR}	40	-	ns	
	SSITXD0 output	1.8 V or above	T _{DTRW}	-	105	ns	Figure 2.63
delay from SSILRCK0/SSIFS0 change time		1.6 V or above		-	140		

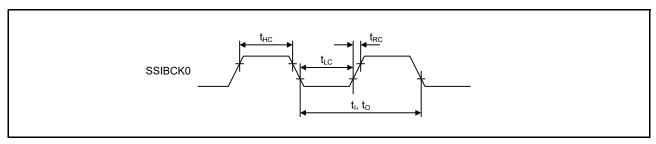


Figure 2.60 SSIE clock input/output timing

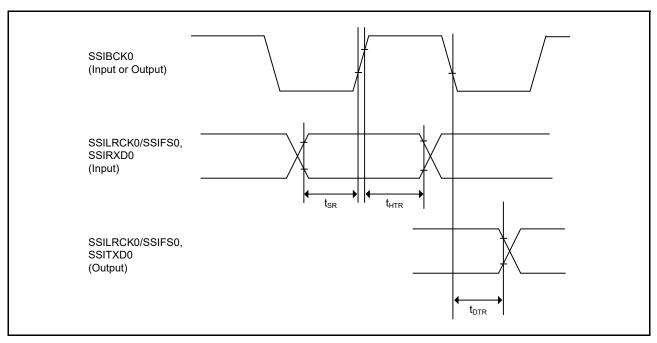


Figure 2.61 SSIE data transmit/receive timing (SSICR.BCKP = 0)

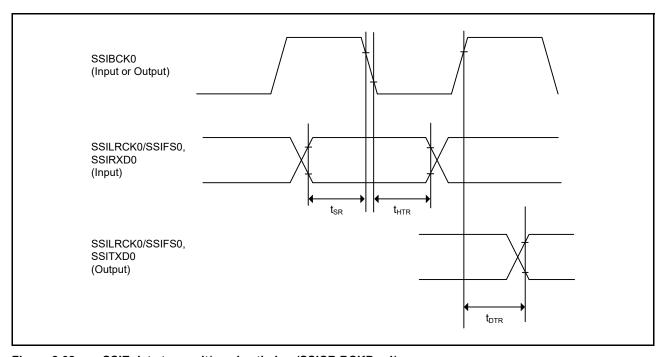


Figure 2.62 SSIE data transmit/receive timing (SSICR.BCKP = 1)

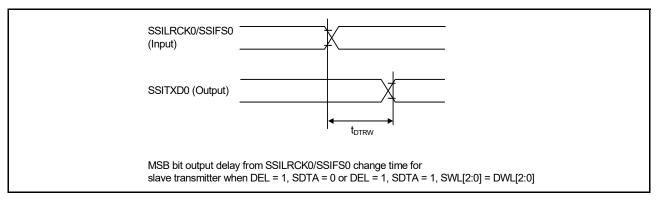


Figure 2.63 SSIE data output delay from SSILRCK0/SSIFS0 change time

2.3.12 CLKOUT Timing

Table 2.39 CLKOUT timing

Parameter			Symbol	Min	Max	Unit*1	Test conditions
CLKOUT	CLKOUT pin output cycle*1	VCC = 2.7 V or above	t _{Ccyc}	62.5	-	ns	Figure 2.64
		VCC = 1.8 V or above		125	-		
		VCC = 1.6 V or above		250	-		
	CLKOUT pin high pulse width*2	VCC = 2.7 V or above	t _{CH}	15	-	ns	
		VCC = 1.8 V or above		30	-		
		VCC = 1.6 V or above		150	-		
	CLKOUT pin low pulse width*2		t _{CL}	15	-	ns	
		VCC = 1.8 V or above		30	-		
		VCC = 1.6 V or above		150	-		
	CLKOUT pin output rise time	VCC = 2.7 V or above	t _{Cr}	-	12	ns	
		VCC = 1.8 V or above		-	25		
		VCC = 1.6 V or above		-	50		
	CLKOUT pin output fall time	VCC = 2.7 V or above	t _{Cf}	-	12	ns]
		VCC = 1.8 V or above		-	25	1	
		VCC = 1.6 V or above		-	50	1	

Note 1. When the EXTAL external clock input or an oscillator is used with division by 1 (the CKOCR.CKOSEL[2:0] bits are 011b and the CKOCR.CKODIV[2:0] bits are 000b) to output from CLKOUT, the above should be satisfied with an input duty cycle of 45 to 55%.

Note 2. When the MOCO is selected as the clock output source (the CKOCR.CKOSEL[2:0] bits are 001b), set the clock output division ratio selection to be divided by 2 (the CKOCR.CKODIV[2:0] bits are 001b).

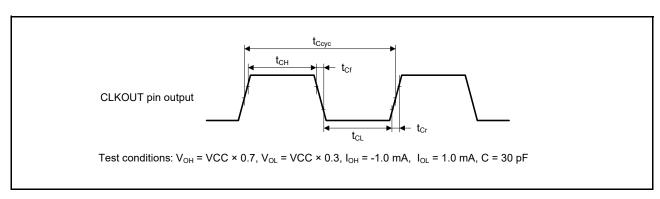


Figure 2.64 CLKOUT output timing

2.4 USB Characteristics

2.4.1 USBFS Timing

Table 2.40 USB characteristics

Conditions: VCC = VCC_USB = 3.0 to 3.6 V, $T_a = -20$ to +85°C (USBCLKSEL = 1), $T_a = -40$ to +105°C (USBCLKSEL = 0)

Parameter			Symbol	Min	Max	Unit	Test conditions
Input	Input high level volt	age	V _{IH}	2.0	-	V	-
characteristics	Input low level volta	ige	V _{IL}	-	0.8	V	-
	Differential input se	Differential input sensitivity		0.2	-	V	USB_DP - USB_DM
	Differential common range	n mode	V _{CM}	0.8	2.5	V	-
Output	Output high level vo	oltage	V _{OH}	2.8	VCC_USB	V	I _{OH} = -200 μA
characteristics	Output low level voltage		V _{OL}	0.0	0.3	V	I _{OL} = 2 mA
	Cross-over voltage		V _{CRS}	1.3	2.0	V	Figure 2.65,
	Rise time	FS	t _r	4	20	ns	Figure 2.66, Figure 2.67
		LS		75	300		ga 2.0.
	Fall time	FS	t _f	4	20	ns	
		LS		75	300		
	Rise/fall time ratio	FS	t _r /t _f	90	111.11	%	1
		LS		80	125		
	Output resistance		Z _{DRV}	28	44	Ω	(Adjusting the resistance of external elements is not necessary.)
VBUS	VBUS input voltage)	V _{IH}	VCC × 0.8	-	V	-
characteristics			V _{IL}	-	VCC × 0.2	V	-
Pull-up,	Pull-down resistor		R _{PD}	14.25	24.80	kΩ	-
pull-down	Pull-up resistor		R _{PUI}	0.9	1.575	kΩ	During idle state
			R _{PUA}	1.425	3.09	kΩ	During reception
Battery Charging	D + sink current		I _{DP_SINK}	25	175	μΑ	-
Specification Ver 1.2	D - sink current		I _{DM_SINK}	25	175	μΑ	-
	DCD source curren	DCD source current		7	13	μΑ	-
	Data detection volta	age	V _{DAT_REF}	0.25	0.4	V	-
	D + source voltage		V _{DP_SRC}	0.5	0.7	V	Output current = 250 μA
	D - source voltage		V _{DM_SRC}	0.5	0.7	V	Output current = 250 μA

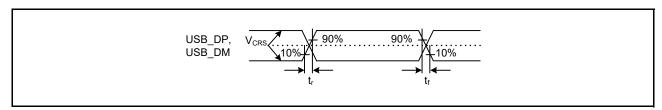


Figure 2.65 USB_DP and USB_DM output timing

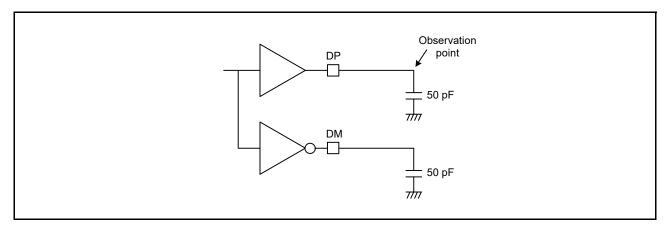


Figure 2.66 Test circuit for Full-Speed (FS) connection

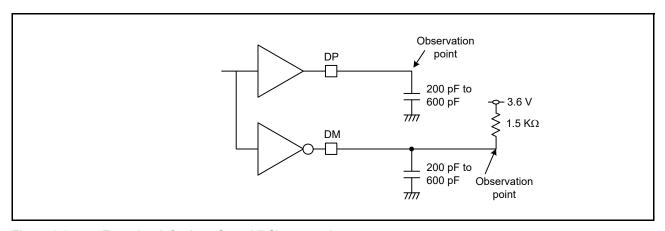


Figure 2.67 Test circuit for Low-Speed (LS) connection

2.4.2 USB External Supply

Table 2.41 USB regulator

Parameter	Min	Тур	Max	Unit	Test conditions	
VCC_USB supply current	VCC_USB_LDO ≥ 3.8V	-	-	50	mA	-
	VCC_USB_LDO ≥ 4.5V	-	-	100	mA	-
VCC_USB supply voltage		3.0	-	3.6	٧	-

2.5 ADC14 Characteristics

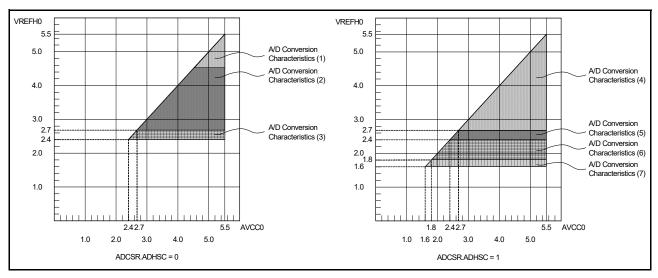


Figure 2.68 AVCC0 to VREFH0 voltage range

Table 2.42 A/D conversion characteristics (1) in high-speed A/D conversion mode (1 of 2)

Conditions: VCC = AVCC0 = 4.5 to 5.5 V, VREFH0 = 4.5 to 5.5 V Reference voltage range applied to the VREFH0 and VREFL0.

Parameter	_		Min	Тур	Max	Unit	Test conditions
Frequency			1	-	64	MHz	-
Analog input capacitano	e*2	Cs	-	-	8 (reference data)	pF	High-precision channel
			-	-	9 (reference data)	pF	Normal-precision channel
Analog input resistance		Rs	-	-	2.5 (reference data)	kΩ	High-precision channel
			-	-	6.7 (reference data)	kΩ	Normal-precision channel
Analog input voltage ran	ige	Ain	0	-	VREFH0	V	-
12-bit mode		· · ·	,	'		·	
Resolution			-	-	12	Bit	-
Conversion time*1 (Operation at PCLKC = 64 MHz)	Operation at source impedance		0.70	-	-	μs	High-precision channel ADCSR.ADHSC = 0 ADSSTRn.SST[7:0] = 0Dh
			1.13	-	-	μs	Normal-precision channel ADCSR.ADHSC = 0 ADSSTRn.SST[7:0] = 28h
Offset error	1		-	±0.5	±4.5	LSB	High-precision channel
					±6.0	LSB	Other than above
Full-scale error			-	±0.75	±4.5	LSB	High-precision channel
					±6.0	LSB	Other than above
Quantization error			-	±0.5	-	LSB	-
Absolute accuracy			-	±1.25	±5.0	LSB	High-precision channel
				±8.0	LSB	Other than above	
DNL differential nonlinearity error		-	±1.0	-	LSB	-	
INL integral nonlinearity error			-	±1.0	±3.0	LSB	-
14-bit mode			<u> </u>		1	ı	1
Resolution			-	-	14	Bit	-

Table 2.42 A/D conversion characteristics (1) in high-speed A/D conversion mode (2 of 2)

Conditions: VCC = AVCC0 = 4.5 to 5.5 V, VREFH0 = 4.5 to 5.5 V Reference voltage range applied to the VREFH0 and VREFL0.

Parameter		Min	Тур	Max	Unit	Test conditions
Conversion time*1 (Operation at PCLKC = 64 MHz)	Permissible signal source impedance Max. = 0.3 kΩ	0.80	-	-	μs	High-precision channel ADCSR.ADHSC = 0 ADSSTRn.SST[7:0] = 0Dh
		1.22	-	-	μs	Normal-precision channel ADCSR.ADHSC = 0 ADSSTRn.SST[7:0] = 28h
Offset error		-	±2.0	±18	LSB	High-precision channel
				±24.0	LSB	Other than above
Full-scale error		-	±3.0	±18	LSB	High-precision channel
				±24.0	LSB	Other than above
Quantization error		-	±0.5	-	LSB	-
Absolute accuracy		-	±5.0	±20	LSB	High-precision channel
				±32.0	LSB	Other than above
DNL differential nonline	earity error	-	±4.0	-	LSB	-
INL integral nonlinearity error		-	±4.0	±12.0	LSB	-

Note: The characteristics apply when no pin functions other than 14-bit A/D converter input are used. Absolute accuracy does not include quantization errors. Offset error, full-scale error, DNL differential nonlinearity error, and INL integral nonlinearity error do not include quantization errors.

Note 1. The conversion time is the sum of the sampling time and the comparison time. The number of sampling states is indicated for the test conditions.

Note 2. Except for I/O input capacitance (Cin), see section 2.2.4, I/O VOH, VOL, and Other Characteristics.

Table 2.43 A/D conversion characteristics (2) in high-speed A/D conversion mode (1 of 2)

Conditions: VCC = AVCC0 = 2.7 to 5.5 V, VREFH0 = 2.7 to 5.5 V Reference voltage range applied to the VREFH0 and VREFL0.

Parameter	_	_	Min	Тур	Max	Unit	Test conditions
Frequency			1	-	48	MHz	-
Analog input capacitar	nce*2	Cs	-	-	8 (reference data)	pF	High-precision channel
			- 9 (reference data)		pF	Normal-precision channel	
Analog input resistance	е	Rs	-	-	2.5 (reference data)	kΩ	High-precision channel
			-	-	6.7 (reference data)	kΩ	Normal-precision channel
Analog input voltage ra	ange	Ain	0	-	VREFH0	V	-
12-bit mode		· · · · · · · · · · · · · · · · · · ·					
Resolution			-	-	12	Bit	-
Conversion time*1 (Operation at PCLKC = 48 MHz)	Operation at source impedal		0.94	-	-	μs	High-precision channel ADCSR.ADHSC = 0 ADSSTRn.SST[7:0] = 0Dh
			1.50	-	-	μs	Normal-precision channel ADCSR.ADHSC = 0 ADSSTRn.SST[7:0] = 28h
Offset error	II.		-	±0.5	±4.5	LSB	High-precision channel
					±6.0	LSB	Other than above
Full-scale error			-	±0.75	±4.5	LSB	High-precision channel
					±6.0	LSB	Other than above
Quantization error	Quantization error		-	±0.5	-	LSB	-
Absolute accuracy			-	±1.25	±5.0	LSB	High-precision channel
				±8.0	LSB	Other than above	
DNL differential nonlinearity error		-	±1.0	-	LSB	-	
INL integral nonlineari	ty error		-	±1.0	±3.0	LSB	-

Table 2.43 A/D conversion characteristics (2) in high-speed A/D conversion mode (2 of 2)

Conditions: VCC = AVCC0 = 2.7 to 5.5 V, VREFH0 = 2.7 to 5.5 V Reference voltage range applied to the VREFH0 and VREFL0.

Parameter	Min	Тур	Max	Unit	Test conditions	
14-bit mode						
Resolution		-	-	14	Bit	-
Conversion time*1 (Operation at PCLKC = 48 MHz)	Permissible signal source impedance Max. = 0.3 kΩ	1.06	-	-	μs	High-precision channel ADCSR.ADHSC = 0 ADSSTRn.SST[7:0] = 0Dh
		1.63	-	-	μs	Normal-precision channel ADCSR.ADHSC = 0 ADSSTRn.SST[7:0] = 28h
Offset error		-	±2.0	±18	LSB	High-precision channel
				±24.0	LSB	Other than above
Full-scale error		-	±3.0	±18	LSB	High-precision channel
				±24.0	LSB	Other than above
Quantization error		-	±0.5	-	LSB	-
Absolute accuracy		-	±5.0	±20	LSB	High-precision channel
				±32.0	LSB	Other than above
DNL differential nonlinearity error		-	±4.0	-	LSB	-
INL integral nonlinear	rity error	-	±4.0	±12.0	LSB	-

Note: The characteristics apply when no pin functions other than 14-bit A/D converter input are used. Absolute accuracy does not include quantization errors. Offset error, full-scale error, DNL differential nonlinearity error, and INL integral nonlinearity error do not include quantization errors.

Note 1. The conversion time is the sum of the sampling time and the comparison time. The number of sampling states is indicated for the test conditions.

Note 2. Except for I/O input capacitance (C_{in}), see section 2.2.4, I/O V_{OH} , V_{OL} , and Other Characteristics.

Table 2.44 A/D conversion characteristics (3) in high-speed A/D conversion mode (1 of 2)

Conditions: VCC = AVCC0 = 2.4 to 5.5 V, VREFH0 = 2.4 to 5.5 V Reference voltage range applied to the VREFH0 and VREFL0.

Parameter		Min	Тур	Max	Unit	Test conditions	
Frequency			1	-	32	MHz	-
Analog input capaci	tance*2	Cs	-	-	8 (reference data)	pF	High-precision channel
			-	-	9 (reference data)	pF	Normal-precision channel
Analog input resista	nce	Rs	-	-	2.5 (reference data)	kΩ	High-precision channel
			-	-	6.7 (reference data)	kΩ	Normal-precision channel
Analog input voltage	e range	Ain	0	-	VREFH0	V	-
12-bit mode		•	•	•	•	•	•
Resolution			-	-	12	Bit	-
		ible signal mpedance 1.3 kΩ	1.41	-	-	μs	High-precision channel ADCSR.ADHSC = 0 ADSSTRn.SST[7:0] = 0Dh
			2.25	-	-	μs	Normal-precision channel ADCSR.ADHSC = 0 ADSSTRn.SST[7:0] = 28h
Offset error	·		-	±0.5	±4.5	LSB	High-precision channel
					±6.0	LSB	Other than above
Full-scale error			-	±0.75	±4.5	LSB	High-precision channel
					±6.0	LSB	Other than above
Quantization error		-	±0.5	-	LSB	-	
Absolute accuracy			-	±1.25	±5.0	LSB	High-precision channel
					±8.0	LSB	Other than above

Table 2.44 A/D conversion characteristics (3) in high-speed A/D conversion mode (2 of 2)

Conditions: VCC = AVCC0 = 2.4 to 5.5 V, VREFH0 = 2.4 to 5.5 V Reference voltage range applied to the VREFH0 and VREFL0.

Parameter		Min	Тур	Max	Unit	Test conditions
DNL differential nonlinearity error		-	±1.0	-	LSB	-
INL integral nonline	arity error	-	±1.0	±3.0	LSB	-
14-bit mode		- II	•	- 1	1	1
Resolution		-	-	14	Bit	-
Conversion time*1 (Operation at PCLKC = 32 MHz)	Permissible signal source impedance Max. = 1.3 kΩ	1.59	-	-	μs	High-precision channel ADCSR.ADHSC = 0 ADSSTRn.SST[7:0] = 0Dh
		2.44	-	-	μs	Normal-precision channel ADCSR.ADHSC = 0 ADSSTRn.SST[7:0] = 28h
Offset error	Offset error		±2.0	±18	LSB	High-precision channel
				±24.0	LSB	Other than above
Full-scale error		-	±3.0	±18	LSB	High-precision channel
				±24.0	LSB	Other than above
Quantization error		-	±0.5	-	LSB	-
Absolute accuracy		-	±5.0	±20	LSB	High-precision channel
				±32.0	LSB	Other than above
DNL differential nonlinearity error		-	±4.0	-	LSB	-
INL integral nonline	arity error	-	±4.0	±12.0	LSB	-

Note: The characteristics apply when no pin functions other than 14-bit A/D converter input are used. Absolute accuracy does not include quantization errors. Offset error, full-scale error, DNL differential nonlinearity error, and INL integral nonlinearity error do not include quantization errors.

Table 2.45 A/D conversion characteristics (4) in low power A/D conversion mode (1 of 2)

Conditions: VCC = AVCC0 = 2.7 to 5.5 V, VREFH0 = 2.7 to 5.5 V Reference voltage range applied to the VREFH0 and VREFL0.

Parameter		Min	Тур	Max	Unit	Test conditions	
Frequency			1 -	-	24	MHz	-
Analog input capaci	tance* ²	Cs	-	-	8 (reference data)	pF	High-precision channel
			-	-	9 (reference data)	pF	Normal-precision channel
Analog input resista	nce	Rs	-	-	2.5 (reference data)	kΩ	High-precision channel
			-	-	6.7 (reference data)	kΩ	Normal-precision channel
Analog input voltage	e range	Ain	0	-	VREFH0	V	-
12-bit mode		•	•	•	•	•	_
Resolution			-	-	12	Bit	-
Conversion time*1 (Operation at PCLKC = 24 MHz)		ource nce Max.	2.25	-	-	μs	High-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 0Dh
= 1.1 kΩ)	3.38	-	-	μs	Normal-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 28h
Offset error	•		-	±0.5	±4.5	LSB	High-precision channel
					±6.0	LSB	Other than above
Full-scale error			-	±0.75	±4.5	LSB	High-precision channel
					±6.0	LSB	Other than above
Quantization error			-	±0.5	-	LSB	-

Note 1. The conversion time is the sum of the sampling time and the comparison time. The number of sampling states is indicated for the test conditions.

Note 2. Except for I/O input capacitance (C_{in}), see section 2.2.4, I/O V_{OH} , V_{OL} , and Other Characteristics.

Table 2.45 A/D conversion characteristics (4) in low power A/D conversion mode (2 of 2)

Conditions: VCC = AVCC0 = 2.7 to 5.5 V, VREFH0 = 2.7 to 5.5 V Reference voltage range applied to the VREFH0 and VREFL0.

Parameter		Min	Тур	Max	Unit	Test conditions
Absolute accuracy		-	±1.25	±5.0	LSB	High-precision channel
				±8.0	LSB	Other than above
DNL differential non	linearity error	-	±1.0	-	LSB	-
INL integral nonline	arity error	-	±1.0	±3.0	LSB	-
14-bit mode						<u> </u>
Resolution		-	-	14	Bit	-
Conversion time*1 (Operation at PCLKC = 24 MHz) Permissible signal source impedance Ma = 1.1 k Ω	signal source impedance Max.	2.50	-	-	μѕ	High-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 0Dh
	= 1.1 kΩ	3.63	-	-	μs	Normal-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 28h
Offset error		-	±2.0	±18	LSB	High-precision channel
				±24.0	LSB	Other than above
Full-scale error		-	±3.0	±18	LSB	High-precision channel
				±24.0	LSB	Other than above
Quantization error		-	±0.5	-	LSB	-
Absolute accuracy		-	±5.0	±20	LSB	High-precision channel
				±32.0	LSB	Other than above
DNL differential non	linearity error	-	±4.0	-	LSB	-
INL integral nonline	arity error	-	±4.0	±12.0	LSB	-

Note: The characteristics apply when no pin functions other than 14-bit A/D converter input are used. Absolute accuracy does not include quantization errors. Offset error, full-scale error, DNL differential nonlinearity error, and INL integral nonlinearity error do not include quantization errors.

Note 1. The conversion time is the sum of the sampling time and the comparison time. The number of sampling states is indicated for the test conditions.

Note 2. Except for I/O input capacitance (C_{in}), see section 2.2.4, I/O V_{OH} , V_{OL} , and Other Characteristics.

Table 2.46 A/D conversion characteristics (5) in low power A/D conversion mode (1 of 2) Conditions: VCC = AVCC0 = 2.4 to 5.5 V, VREFH0 = 2.4 to 5.5 V

Reference voltage range applied to the VREFH0 and VREFL0.

Parameter Frequency		Min	Тур	Max	Unit	Test conditions	
		1	-	16	MHz		
Analog input capacit	ance*2	Cs	-	-	8 (reference data)	pF	High-precision channel
			-	-	9 (reference data)	pF	Normal-precision channel
Analog input resistar	nce	Rs	-	-	2.5 (reference data)	kΩ	High-precision channel
			-	-	6.7 (reference data)	kΩ	Normal-precision channel
Analog input voltage	range	Ain	0	-	VREFH0	V	-
12-bit mode		•		'	•	1	
Resolution			-	-	12	Bit	-
Conversion time*1 (Operation at PCLKC = 16 MHz)		sible signal mpedance 2.2 kΩ	3.38	-	-	μs	High-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 0Dh
			5.06	-	-	μs	Normal-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 28h
Offset error			-	±0.5	±4.5	LSB	High-precision channel
					±6.0	LSB	Other than above

Table 2.46 A/D conversion characteristics (5) in low power A/D conversion mode (2 of 2)

Conditions: VCC = AVCC0 = 2.4 to 5.5 V, VREFH0 = 2.4 to 5.5 V Reference voltage range applied to the VREFH0 and VREFL0.

Parameter		Min	Тур	Max	Unit	Test conditions
Full-scale error		-	±0.75	±4.5	LSB	High-precision channel
				±6.0	LSB	Other than above
Quantization error		-	±0.5	-	LSB	-
Absolute accuracy		-	±1.25	±5.0	LSB	High-precision channel
				±8.0	LSB	Other than above
DNL differential nonli	inearity error	-	±1.0	-	LSB	-
INL integral nonlinea	rity error	-	±1.0	±3.0	LSB	-
14-bit mode			1	1	l	1
Resolution		-	-	14	Bit	-
Conversion time*1 (Operation at PCLKC = 16 MHz)	Permissible signal source impedance Max. = 2.2 kΩ	3.75	-	-	μѕ	High-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 0Dh
		5.44	-	-	μѕ	Normal-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 28h
Offset error	1	-	±2.0	±18	LSB	High-precision channel
				±24.0	LSB	Other than above
Full-scale error		-	±3.0	±18	LSB	High-precision channel
				±24.0	LSB	Other than above
Quantization error		-	±0.5	-	LSB	-
Absolute accuracy		-	±5.0	±20	LSB	High-precision channel
				±32.0	LSB	Other than above
DNL differential nonli	inearity error	-	±4.0	-	LSB	-
INL integral nonlinea	rity error	-	±4.0	±12.0	LSB	-

Note: The characteristics apply when no pin functions other than 14-bit A/D converter input are used. Absolute accuracy does not include quantization errors. Offset error, full-scale error, DNL differential nonlinearity error, and INL integral nonlinearity error do not include quantization errors.

Note 1. The conversion time is the sum of the sampling time and the comparison time. The number of sampling states is indicated for the test conditions.

Note 2. Except for I/O input capacitance (C_{in}), see section 2.2.4, I/O V_{OH} , V_{OL} , and Other Characteristics.

Table 2.47 A/D conversion characteristics (6) in low power A/D conversion mode (1 of 2)

Conditions: VCC = AVCC0 = 1.8 to 5.5 V (AVCC0 = VCC when VCC < 2.0 V), VREFH0 = 1.8 to 5.5 V Reference voltage range applied to the VREFH0 and VREFL0.

Parameter		Min	Тур	Max	Unit	Test conditions
Frequency		1	-	8	MHz	-
Analog input capaci	tance*2 Cs	-	-	8 (reference data)	pF	High-precision channel
		-	-	9 (reference data)	pF	Normal-precision channel
Analog input resista	nce Rs	-	-	3.8 (reference data)	kΩ	High-precision channel
		-	-	8.2 (reference data)	kΩ	Normal-precision channel
Analog input voltage range Ain		0	-	VREFH0	V	-
12-bit mode	•	•	•		•	•
Resolution		-	-	12	Bit	-
Conversion time*1 Permissible signal (Operation at PCLKC = 8 MHz) Permissible signal source impedance Max.		6.75	-	-	μs	High-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 0Dh
	= 5 kΩ	10.13	-	-	μs	Normal-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 28h

Table 2.47 A/D conversion characteristics (6) in low power A/D conversion mode (2 of 2)

Conditions: VCC = AVCC0 = 1.8 to 5.5 V (AVCC0 = VCC when VCC < 2.0 V), VREFH0 = 1.8 to 5.5 V Reference voltage range applied to the VREFH0 and VREFL0.

Parameter		Min	Тур	Max	Unit	Test conditions
Offset error		-	±1.0	±7.5	LSB	High-precision channel
				±10.0	LSB	Other than above
Full-scale error		-	±1.5	±7.5	LSB	High-precision channel
				±10.0	LSB	Other than above
Quantization error		-	±0.5	-	LSB	-
Absolute accuracy		-	±3.0	±8.0	LSB	High-precision channel
				±12.0	LSB	Other than above
DNL differential non	linearity error	-	±1.0	-	LSB	-
INL integral nonlinea	arity error	-	±1.0	±3.0	LSB	-
14-bit mode				1	,	1
Resolution		-	-	14	Bit	-
(Operation at source	impedance Max.	7.50	-	-	μs	High-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 0Dh
	= 5 kΩ	10.88	-	-	μs	Normal-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 28h
Offset error		-	±4.0	±30.0	LSB	High-precision channel
				±40.0	LSB	Other than above
Full-scale error		-	±6.0	±30.0	LSB	High-precision channel
				±40.0	LSB	Other than above
Quantization error		-	±0.5	-	LSB	-
Absolute accuracy		-	±12.0	±32.0	LSB	High-precision channel
				±48.0	LSB	Other than above
DNL differential non	llinearity error	-	±4.0	-	LSB	-
INL integral nonlinea	arity error	-	±4.0	±12.0	LSB	-

Note: The characteristics apply when no pin functions other than 14-bit A/D converter input are used. Absolute accuracy does not include quantization errors. Offset error, full-scale error, DNL differential nonlinearity error, and INL integral nonlinearity error do not include quantization errors.

Note 1. The conversion time is the sum of the sampling time and the comparison time. The number of sampling states is indicated for the test conditions.

Note 2. Except for I/O input capacitance (C_{in}), see section 2.2.4, I/O V_{OH} , V_{OL} , and Other Characteristics.

Table 2.48 A/D conversion characteristics (7) in low power A/D conversion mode (1 of 2)

Conditions: VCC = AVCC0 = 1.6 to 5.5 V (AVCC0 = VCC when VCC < 2.0 V), VREFH0 = 1.6 to 5.5 V Reference voltage range applied to the VREFH0 and VREFL0.

Parameter		Min	Тур	Max	Unit	Test conditions
Frequency		1	-	4	MHz	-
Analog input capacitance*2	Cs	-	-	8 (reference data)	pF	High-precision channel
		-	-	9 (reference data)	pF	Normal-precision channel
Analog input resistance	Rs	-	-	13.1 (reference data)	kΩ	High-precision channel
		-	-	14.3 (reference data)	kΩ	Normal-precision channel
Analog input voltage range	Ain	0	-	VREFH0	V	-
12-bit mode	•	•	•		•	<u> </u>
Resolution		-	-	12	Bit	-

Table 2.48 A/D conversion characteristics (7) in low power A/D conversion mode (2 of 2) Conditions: VCC = AVCC0 = 1.6 to 5.5 V (AVCC0 = VCC when VCC < 2.0 V), VREFH0 = 1.6 to 5.5 V

Reference voltage range applied to the VREFH0 and VREFL0.

Parameter		Min	Тур	Max	Unit	Test conditions
Conversion time*1 (Operation at PCLKC = 4 MHz)	Permissible signal source impedance Max.	13.5	-	-	μѕ	High-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 0Dh
	= 9.9 kΩ	20.25	-	-	μs	Normal-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 28h
Offset error		-	±1.0	±7.5	LSB	High-precision channel
				±10.0	LSB	Other than above
Full-scale error		-	±1.5	±7.5	LSB	High-precision channel
				±10.0	LSB	Other than above
Quantization error		-	±0.5	-	LSB	-
Absolute accuracy		-	±3.0	±8.0	LSB	High-precision channel
				±12.0	LSB	Other than above
DNL differential nonlinearity error		-	±1.0	-	LSB	-
INL integral nonlinearity error		-	±1.0	±3.0	LSB	-
14-bit mode					•	•
Resolution		-	-	14	Bit	-
Conversion time*1 (Operation at PCLKC = 4 MHz)	Permissible signal source impedance Max.	15.0	-	-	μѕ	High-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 0Dh
	= 9.9 kΩ	21.75	-	-	μs	Normal-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 28h
Offset error		-	±4.0	±30.0	LSB	High-precision channel
				±40.0	LSB	Other than above
Full-scale error		-	±6.0	±30.0	LSB	High-precision channel
				±40.0	LSB	Other than above
Quantization error		-	±0.5	-	LSB	-
Absolute accuracy		-	±12.0	±32.0	LSB	High-precision channel
				±48.0	LSB	Other than above
DNL differential non	linearity error	-	±4.0	-	LSB	-
INL integral nonline	arity error	-	±4.0	±12.0	LSB	-

Note: The characteristics apply when no pin functions other than 14-bit A/D converter input are used. Absolute accuracy does not include quantization errors. Offset error, full-scale error, DNL differential nonlinearity error, and INL integral nonlinearity error do not include quantization errors.

Note 1. The conversion time is the sum of the sampling time and the comparison time. The number of sampling states is indicated for the test conditions.

Note 2. Except for I/O input capacitance (C_{in}), see section 2.2.4, I/O V_{OH} , V_{OL} , and Other Characteristics.

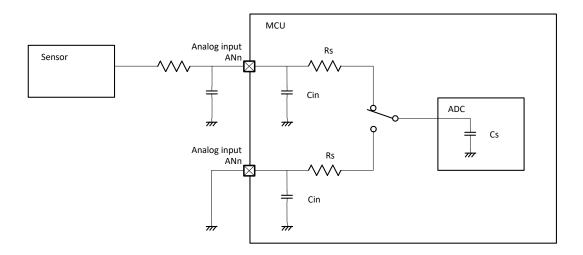


Figure 2.69 Equivalent circuit for analog input

Table 2.49 14-Bit A/D converter channel classification

Classification	Channel	Conditions	Remarks	
High-precision channel	AN000 to AN014	AVCC0 = 1.6 to 5.5 V	Pins AN000 to AN014 cannot be used	
Normal-precision channel	AN016 to AN025		as general I/O, IRQ2, IRQ3 inputs, and TS transmission, when the A/D converter is in use	
Internal reference voltage input channel	Internal reference voltage	AVCC0 = 2.0 to 5.5 V	-	
Temperature sensor input channel	Temperature sensor output	AVCC0 = 2.0 to 5.5 V	-	

Table 2.50 A/D internal reference voltage characteristics

Conditions: VCC = AVCC0 = VREFH0 = 2.0 to 5.5 V*1

Parameter	Min	Тур	Max	Unit	Test conditions
Internal reference voltage input channel*2	1.36	1.43	1.50	V	-
Frequency*3	1	-	2	MHz	-
Sampling time*4	5.0	-	-	μs	-

- Note 1. The internal reference voltage cannot be selected for input channels when AVCC0 < 2.0 V.
- Note 2. The 14-bit A/D internal reference voltage indicates the voltage when the internal reference voltage is input to the 14-bit A/D converter.
- Note 3. This is a parameter for ADC14 when the internal reference voltage is used as the high-potential reference voltage.
- Note 4. This is a parameter for ADC14 when the internal reference voltage is selected for an analog input channel in ADC14.

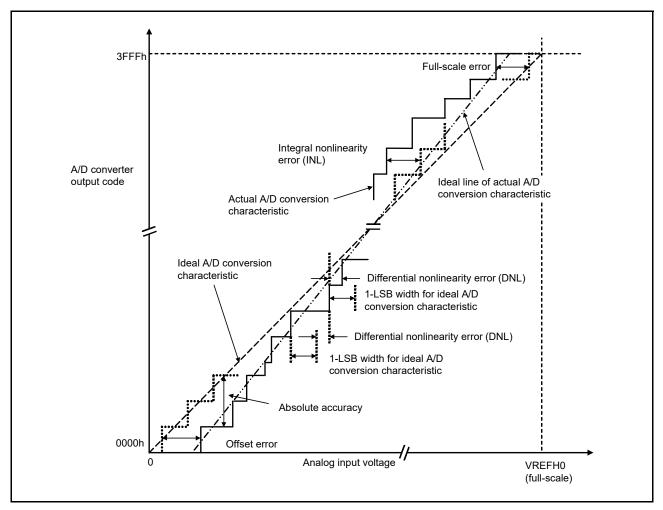


Figure 2.70 Illustration of 14-bit A/D converter characteristic terms

Absolute accuracy

Absolute accuracy is the difference between output code based on the theoretical A/D conversion characteristics, and the actual A/D conversion result. When measuring absolute accuracy, the voltage at the midpoint of the width of analog input voltage (1-LSB width), which can meet the expectation of outputting an equal code based on the theoretical A/D conversion characteristics, is used as the analog input voltage. For example, if 12-bit resolution is used and the reference voltage VREFH0 = 3.072 V, then 1-LSB width becomes 0.75 mV, and 0 mV, 0.75 mV, and 1.5 mV are used as the analog input voltages. If analog input voltage is 6 mV, an absolute accuracy of ± 5 LSB means that the actual A/D conversion result is in the range of 003h to 00Dh, though an output code of 008h can be expected from the theoretical A/D conversion characteristics.

Integral nonlinearity error (INL)

Integral nonlinearity error is the maximum deviation between the ideal line when the measured offset and full-scale errors are zeroed, and the actual output code.

Differential nonlinearity error (DNL)

Differential nonlinearity error is the difference between 1-LSB width based on the ideal A/D conversion characteristics and the width of the actually output code.

Offset error

Offset error is the difference between the transition point of the ideal first output code and the actual first output code.

Full-scale error

Full-scale error is the difference between the transition point of the ideal last output code and the actual last output code.



2.6 DAC12 Characteristics

Table 2.51 D/A conversion characteristics (1)

Conditions: VCC = AVCC0 = 1.8 to 5.5 V Reference voltage = VREFH or VREFL selected

Parameter	Min	Тур	Max	Unit	Test conditions
Resolution	-	-	12	bit	-
Resistive load	30	-	-	kΩ	-
Load capacitance	-	-	50	pF	-
Output voltage range	0.35	-	AVCC0 - 0.47	V	-
DNL differential nonlinearity error	-	±0.5	±1.0	LSB	-
INL integral nonlinearity error	-	±2.0	±8.0	LSB	-
Offset error	-	-	±20	mV	-
Full-scale error	-	-	±20	mV	-
Output impedance	-	5	-	Ω	-
Conversion time	-	-	30	μs	-

Table 2.52 D/A conversion characteristics (2)

Conditions: VCC = AVCC0 = 1.8 to 5.5 V Reference voltage = AVCC0 or AVSS0 selected

Parameter	Min	Тур	Max	Unit	Test conditions
Resolution	-	-	12	bit	-
Resistive load	30	-	-	kΩ	-
Load capacitance	-	-	50	pF	-
Output voltage range	0.35	-	AVCC0 - 0.47	V	-
DNL differential nonlinearity error	-	±0.5	±2.0	LSB	-
INL integral nonlinearity error	-	±2.0	±8.0	LSB	-
Offset error	-	-	±30	mV	-
Full-scale error	-	-	±30	mV	-
Output impedance	-	5	-	Ω	-
Conversion time	-	-	30	μs	-

Table 2.53 D/A conversion characteristics (3)

Conditions: VCC = AVCC0 = 1.8 to 5.5 V

Reference voltage = internal reference voltage selected

Parameter	Min	Тур	Max	Unit	Test conditions
Resolution	-	-	12	bit	-
Internal reference voltage (Vbgr)	1.36	1.43	1.50	V	-
Resistive load	30	-	-	kΩ	-
Load capacitance	-	-	50	pF	-
Output voltage range	0.35	-	Vbgr	V	-
DNL differential nonlinearity error	-	±2.0	±16.0	LSB	-
INL integral nonlinearity error	-	±8.0	±16.0	LSB	-
Offset error	-	-	±30	mV	-
Output impedance	-	5	-	Ω	-
Conversion time	-	-	30	μs	-

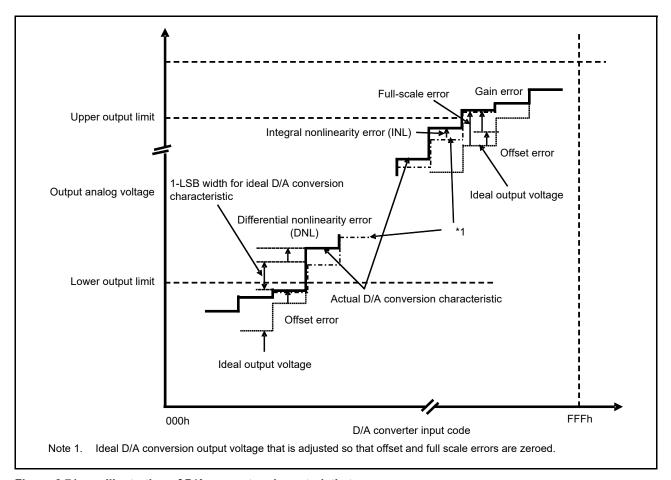


Figure 2.71 Illustration of D/A converter characteristic terms

Integral nonlinearity error (INL)

Integral nonlinearity error is the maximum deviation between the ideal output voltage based on the ideal conversion characteristic when the measured offset and full-scale errors are zeroed, and the actual output voltage.

Differential nonlinearity error (DNL)

Differential nonlinearity error is the difference between 1-LSB voltage width based on the ideal D/A conversion characteristics and the width of the actual output voltage.

Offset error

Offset error is the difference between the highest actual output voltage that falls below the lower output limit and the ideal output voltage based on the input code.

Full-scale error

Full-scale error is the difference between the lowest actual output voltage that exceeds the upper output limit and the ideal output voltage based on the input code.

2.7 TSN Characteristics

Table 2.54 TSN characteristics

Conditions: VCC = AVCC0 = 2.0 to 5.5 V

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
Relative accuracy	-	-	±1.5	-	°C	2.4 V or above
	-	-	±2.0	-	°C	Below 2.4 V
Temperature slope	-	-	-3.65	-	mV/°C	-
Output voltage (at 25°C)	-	-	1.05	-	V	VCC = 3.3 V
Temperature sensor start time	t _{START}	-	-	5	μs	-
Sampling time	-	5	-	-	μs	-

2.8 OSC Stop Detect Characteristics

Table 2.55 Oscillation stop detection circuit characteristics

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
Detection time	t _{dr}	-	-	1	ms	Figure 2.72

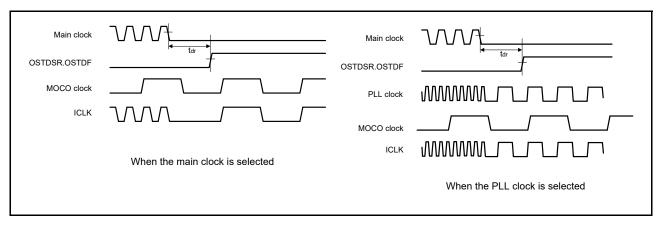


Figure 2.72 Oscillation stop detection timing

2.9 POR and LVD Characteristics

Table 2.56 Power-on reset circuit and voltage detection circuit characteristics (1)

Parameter		Symbol	Min	Тур	Max	Unit	Test conditions
Voltage detection level*1	Power-on reset (POR)	V _{POR}	1.27	1.42	1.57	V	Figure 2.73, Figure 2.74
	Voltage detection circuit (LVD0)*2	V _{det0_0}	3.68	3.85	4.00	V	Figure 2.75
		V _{det0_1}	2.68	2.85	2.96		At falling edge VCC
		V _{det0_2}	2.38	2.53	2.64		100
		V _{det0_3}	1.78	1.90	2.02		
		V _{det0_4}	1.60	1.69	1.82		
	Voltage detection circuit (LVD1)*3	V _{det1_0}	4.13	4.29	4.45	V	Figure 2.76 At falling edge VCC
		V _{det1_1}	3.98	4.16	4.30		
		V _{det1_2}	3.86	4.03	4.18		
		V _{det1_3}	3.68	3.86	4.00		
		V _{det1_4}	2.98	3.10	3.22		
		V _{det1_5}	2.89	3.00	3.11		
		V _{det1_6}	2.79	2.90	3.01		
		V _{det1_7}	2.68	2.79	2.90		
		V _{det1_8}	2.58	2.68	2.78		
		V _{det1_9}	2.48	2.58	2.68		
		V _{det1_A}	2.38	2.48	2.58		
		V _{det1_B}	2.10	2.20	2.30		
		V _{det1_C}	1.84	1.96	2.05		
		V _{det1_D}	1.74	1.86	1.95		
		V _{det1_E}	1.63	1.75	1.84		
		V _{det1_F}	1.60	1.65	1.73		
	Voltage detection circuit (LVD2)*4	V _{det2_0}	4.11	4.31	4.48	V	Figure 2.77
		V _{det2_1}	3.97	4.17	4.34		At falling edge VCC
		V _{det2_2}	3.83	4.03	4.20		
		V _{det2_3}	3.64	3.84	4.01		

Note 1. These characteristics apply when noise is not superimposed on the power supply. When a setting causes this voltage detection level to overlap with that of the voltage detection circuit, it cannot be specified whether LVD1 or LVD2 is used for voltage detection.

Note 2. $\,$ # in the symbol V $_{\rm det0_\#}$ denotes the value of the OFS1.VDSEL1[2:0] bits.

Note 3. # in the symbol V_{det1} denotes the value of the LVDLVLR.LVD1LVL[4:0] bits.

Note 4. # in the symbol V_{det2} # denotes the value of the LVDLVLR.LVD2LVL[2:0] bits.

Table 2.57 Power-on reset circuit and voltage detection circuit characteristics (2)

Parameter		Symbol	Min	Тур	Max	Unit	Test conditions
Wait time after power-on reset cancellation	LVD0:enable	t _{POR}	-	1.7	-	ms	-
reset ourisonation	LVD0:disable	t _{POR}	-	1.3	-	ms	-
Wait time after voltage monitor 0,1,2 reset cancellation	LVD0:enable*1	t _{LVD0,1,2}	-	0.6	-	ms	-
	LVD0:disable*2	t _{LVD1,2}	-	0.2	-	ms	-
Response delay*3	1	t _{det}	-	-	350	μs	Figure 2.73, Figure 2.74
Minimum VCC down time		t _{VOFF}	450	-	-	μs	Figure 2.73, VCC = 1.0 V or above
Power-on reset enable tim	Power-on reset enable time		1	-	-	ms	Figure 2.74, VCC = below 1.0 V
LVD operation stabilization enabled)	time (after LVD is	T _{d (E-A)}	-	-	300	μs	Figure 2.76, Figure 2.77
Hysteresis width (POR)		V _{PORH}	-	110	-	mV	-
Hysteresis width (LVD0, LV	/D1 and LVD2)	V_{LVH}	-	60	-	mV	LVD0 selected
			-	100	-	mV	V _{det1_0} to V _{det1_2} selected.
			-	60	-		V _{det1_3} to V _{det1_9} selected.
			-	50	-		V _{det1_A} or V _{det1_B} selected.
			-	40	-		V _{det1_C} or V _{det1_F} selected.
			-	60	-		LVD2 selected

- Note 1. When OFS1.LVDAS = 0.
- Note 2. When OFS1.LVDAS = 1.
- Note 3. The minimum VCC down time indicates the time when VCC is below the minimum value of voltage detection levels V_{POR} , V_{det0} , V_{det1} , and V_{det2} for the POR/LVD.

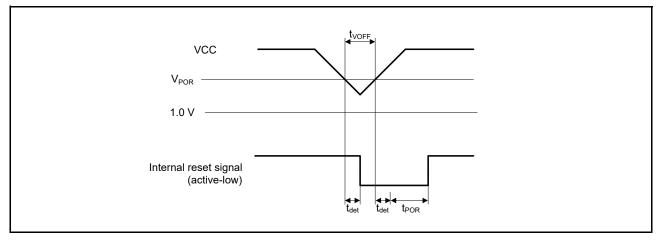


Figure 2.73 Voltage detection reset timing

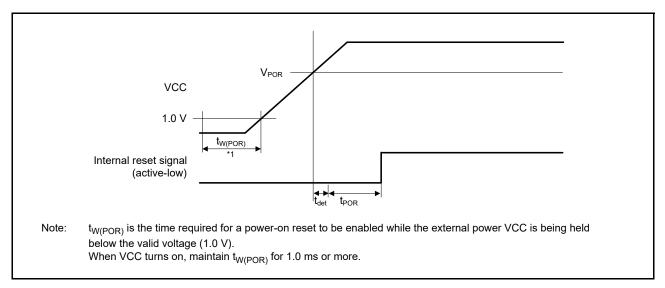


Figure 2.74 Power-on reset timing

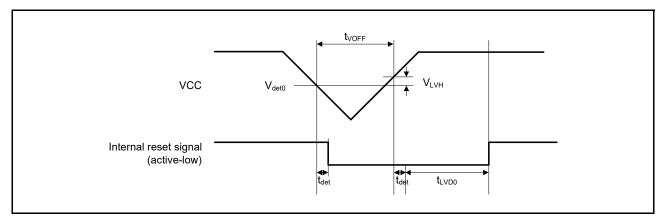


Figure 2.75 Voltage detection circuit timing (V_{det0})

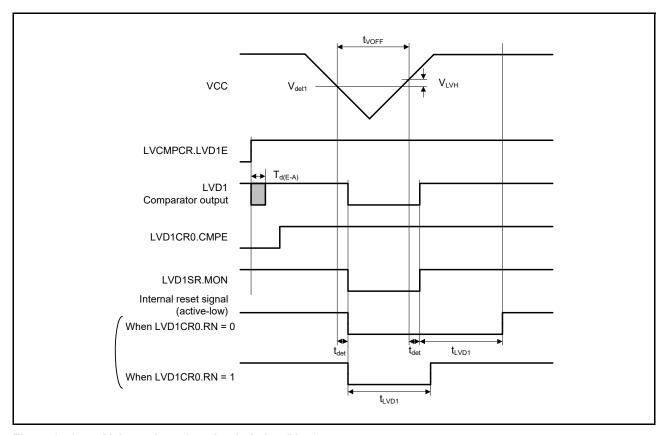


Figure 2.76 Voltage detection circuit timing (V_{det1})

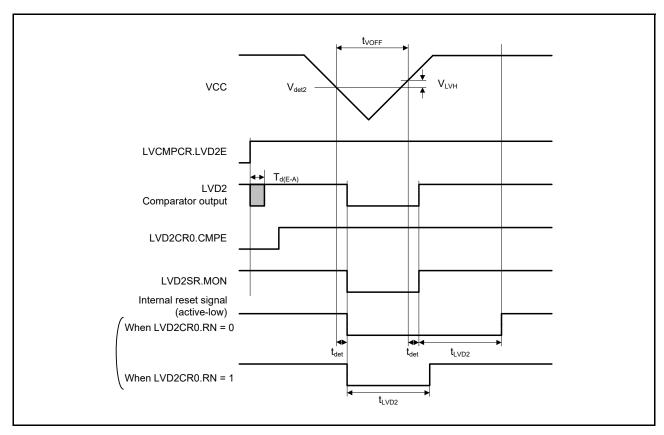


Figure 2.77 Voltage detection circuit timing (V_{det2})

2.10 VBATT Characteristics

Table 2.58 Battery backup function characteristics Conditions: VCC = AVCC0 = 1.6V to 5.5V, VBATT = 1.6 to 3.6 V

Parameter		Symbol	Min	Тур	Max	Unit	Test conditions
Voltage level for switching to battery ba	ckup (falling)	V _{DETBATT}	1.99	2.09	2.19	٧	Figure 2.78,
Hysteresis width for switching to battery back up		V_{VBATTH}	-	100	-	mV	Figure 2.79
VCC-off period for starting power supply	t _{VOFFBATT}	300	-	-	μs	-	
Voltage detection level VBATT_Power-on reset (VBATT_POR)		V _{VBATPOR}	1.30	1.40	1.50	V	Figure 2.78, Figure 2.79
Wait time after VBATT_POR reset time cancellation		t _{VBATPOR}	-	-	3	mS	-
Level for detection of voltage drop on	VBTLVDLVL[1:0] = 10b	V _{DETBATLVD}	2.11	2.2	2.29	V	Figure 2.80
the VBATT pin (falling)	VBTLVDLVL[1:0] = 11b		1.92	2	2.08	٧	
Hysteresis width for VBATT pin LVD		V _{VBATLVDTH}	-	50	-	mV	
VBATT pin LVD operation stabilization t	time	t _{d_vbat}	-	-	300	μs	Figure 2.80
VBATT pin LVD response delay time	t _{det_vbat}	-	-	350	μs		
Allowable voltage change rising/falling gradient		dt/dVCC	1.0	-	-	ms/V	-
VCC voltage level for access to the VB	ATT backup registers	V_BKBATT	1.8	-	-	٧	-

Note: The VCC-off period for starting power supply switching indicates the period in which VCC is below the minimum value of the voltage level for switching to battery backup (V_{DETBATT}).

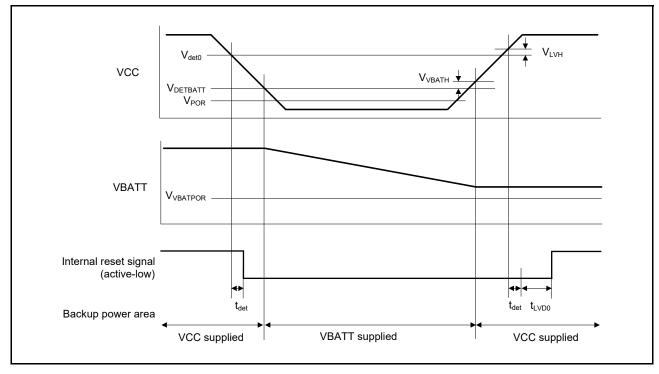


Figure 2.78 Power supply switching and LVD0 reset timing

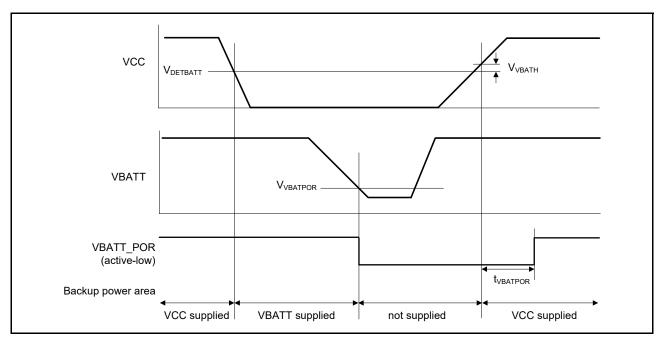


Figure 2.79 VBATT_POR reset timing

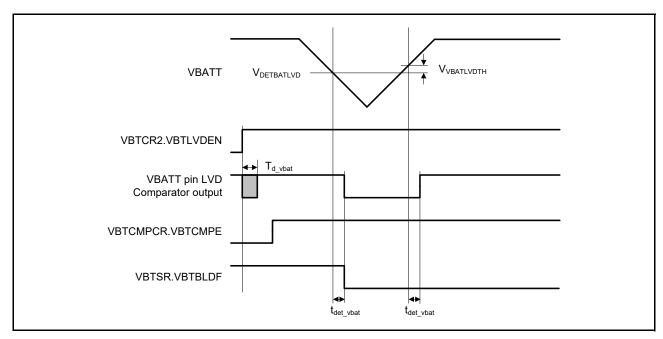


Figure 2.80 VBATT pin voltage detection circuit timing

Table 2.59 VBATT-I/O characteristics

Parameter			Symbol	Min	Тур	Max	Unit	Test conditions
VBATWIOn I/O	VCC > V _{DETBATT}	VCC = 4.0 to 5.5 V	V _{OH}	VCC - 0.8	-	-	V	I _{OH} = -200 μA
output characteristics			V _{OL}	-	-	0.8		I _{OL} = 200 μA
(n = 0 to 2)		VCC = 2.7 to 4.0 V	V _{OH}	VCC - 0.5	-	-		I _{OH} = -100 μA
			V _{OL}	-	-	0.5		I _{OL} = 100 μA
		VCC = V _{DETBATT} to 2.7 V	V _{OH}	VCC - 0.3	-	-		I _{OH} = -50 μA
			V _{OL}	-	-	0.3		I _{OL} = 50 μA
	VCC < V _{DETBATT}	VBATT = 2.7 to 3.6 V	V _{OH}	V _{BATT} - 0.5	-	-		I _{OH} = -100 μA
			V _{OL}	-	-	0.5		I _{OL} = 100 μA
		VBATT = 1.6 to 2.7 V	V _{OH}	V _{BATT} - 0.3	-	-		I _{OH} = -50 μA
			V _{OL}	-	-	0.3		I _{OL} = 50 μA

2.11 CTSU Characteristics

Table 2.60 CTSU characteristics

Conditions: VCC = AVCC0 = 1.8 to 5.5 V

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
External capacitance connected to TSCAP pin	C _{tscap}	9	10	11	nF	-
TS pin capacitive load	C _{base}	-	-	50	pF	-
Permissible output high current	ΣΙοΗ	-	-	-24	mA	When the mutual capacitance method is applied

2.12 Segment LCD Controller Characteristics

2.12.1 Resistance Division Method

[Static Display Mode]

Table 2.61 Resistance division method LCD characteristics (1)

Conditions: VL4 ≤ VCC ≤ 5.5 V

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
LCD drive voltage	V_{L4}	2.0	-	VCC	V	-

[1/2 Bias Method, 1/4 Bias Method]

Table 2.62 Resistance division method LCD characteristics (2)

Conditions: VL4 ≤ VCC ≤ 5.5 V

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
LCD drive voltage	V_{L4}	2.7	-	VCC	٧	-

[1/3 Bias Method]

Table 2.63 Resistance division method LCD characteristics (3)

Conditions: VL4 ≤ VCC ≤ 5.5 V

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
LCD drive voltage	V_{L4}	2.5	-	VCC	V	-

2.12.2 Internal Voltage Boosting Method

[1/3 Bias Method]

Table 2.64 Internal voltage boosting method LCD characteristics

Conditions: VCC = 1.8 V to 5.5 V

Parameter	Symbol	Conditions		Min	Тур	Max	Unit	Test conditions
LCD output voltage	V_{L1}	C1 to C4*1 = 0.47 µF	VLCD = 04h	0.90	1.0	1.08	V	-
variation range			VLCD = 05h	0.95	1.05	1.13	V	-
			VLCD = 06h	1.00	1.10	1.18	V	-
			VLCD = 07h	1.05	1.15	1.23	V	-
			VLCD = 08h	1.10	1.20	1.28	V	-
			VLCD = 09h	1.15	1.25	1.33	V	-
			VLCD = 0Ah	1.20	1.30	1.38	V	-
			VLCD = 0Bh	1.25	1.35	1.43	V	-
			VLCD = 0Ch	1.30	1.40	1.48	V	-
			VLCD = 0Dh	1.35	1.45	1.53	V	-
			VLCD = 0Eh	1.40	1.50	1.58	V	-
			VLCD = 0Fh	1.45	1.55	1.63	V	-
			VLCD = 10h	1.50	1.60	1.68	V	-
			VLCD = 11h	1.55	1.65	1.73	V	-
			VLCD = 12h	1.60	1.70	1.78	V	-
			VLCD = 13h	1.65	1.75	1.83	V	-
Doubler output voltage	V_{L2}	C1 to C4*1 = 0.47 μ F		2 × V _{L1} - 0.1	2 × V _{L1}	2 × V _{L1}	V	-
Tripler output voltage	V_{L4}	C1 to C4*1 = 0.47 μ F		3 × V _{L1} - 0.15	3 × V _{L1}	3 × V _{L1}	V	-
Reference voltage setup time*2	t _{VL1S}			5	-	-	ms	Figure 2.81
LCD output voltage variation range*3	t _{VLWT}	C1 to C4*1 = 0.47 µF		500	•	-	ms	

Note 1. This is a capacitor that is connected between voltage pins used to drive the LCD.

- C1: A capacitor connected between CAPH and CAPL
- C2: A capacitor connected between VL1 and GND
- C3: A capacitor connected between VL2 and GND
- C4: A capacitor connected between VL4 and GND
- $C1 = C2 = C3 = C4 = 0.47 \mu F \pm 30\%$.
- Note 2. This is the time required to wait from when the reference voltage is specified using the VLCD register (or when the internal voltage boosting method is selected (by setting the MDSET[1:0] bits in the LCDM0 register to 01b) if the default value reference voltage is used) until voltage boosting starts (VLCON = 1).
- Note 3. This is the wait time from when voltage boosting is started (VLCON = 1) until display is enabled (LCDON = 1).

[1/4 Bias Method]

Table 2.65 Internal voltage boosting method LCD characteristics Conditions: VCC = 1.8 V to 5.5 V

Parameter	Symbol	Conditions		Min	Тур	Max	Unit	Test conditions
LCD output voltage	V_{L1}	C1 to C5*1 = 0.47 µF	VLCD = 04h	0.90	1.0	1.08	V	-
variation range			VLCD = 05h	0.95	1.05	1.13	V	-
			VLCD = 06h	1.00	1.10	1.18	V	-
			VLCD = 07h	1.05	1.15	1.23	V	-
			VLCD = 08h	1.10	1.20	1.28	V	-
			VLCD = 09h	1.15	1.25	1.33	V	-
			VLCD = 0Ah	1.20	1.30	1.38	V	-
			VLCD = 0Bh	1.25	1.35	1.43	V	-
			VLCD = 0Ch	1.30	1.40	1.48	٧	-
Doubler output voltage	V_{L2}	C1 to C5*1 = 0.47 µF		2V _{L1} - 0.08	2V _{L1}	2V _{L1}	V	-
Tripler output voltage	V_{L3}	C1 to C5*1 = 0.47 µF		3V _{L1} - 0.12	3V _{L1}	3V _{L1}	V	-
Quadruply output voltage	V _{L4} *4	C1 to C5*1 = 0.47 µF		4V _{L1} - 0.16	4V _{L1}	4V _{L1}	V	-
Reference voltage setup time*2	t _{VL1S}			5	-	-	ms	Figure 2.81
LCD output voltage variation range*3	t _{VLWT}	C1 to C5*1 = 0.47 µF		500	-	-	ms	

- Note 1. This is a capacitor that is connected between voltage pins used to drive the LCD.
 - C1: A capacitor connected between CAPH and CAPL
 - C2: A capacitor connected between V_{L1} and GND
 - C3: A capacitor connected between V_{L2} and GND
 - C4: A capacitor connected between V_{L3} and GND
 - C5: A capacitor connected between V_{L4} and GND
 - $C1 = C2 = C3 = C4 = C5 = 0.47 \mu F \pm 30\%$
- Note 2. This is the time required to wait from when the reference voltage is specified by using the VLCD register (or when the internal voltage boosting method is selected (by setting the MDSET1 and MDSET0 bits in the LCDM0 register to 01b) if the default value reference voltage is used) until voltage boosting starts (VLCON = 1).
- Note 3. This is the wait time from when voltage boosting is started (VLCON = 1) until display is enabled (LCDON = 1).
- Note 4. V_{L4} must be 5.5 V or lower.

2.12.3 Capacitor Split Method

[1/3 Bias Method]

Table 2.66 Internal voltage boosting method LCD characteristics

Conditions: VCC = 2.2 V to 5.5 V

Parameter	Symbol	Conditions	Min	Тур	Max	Unit	Test conditions
VL4 voltage*1	V_{L4}	C1 to C4 = 0.47 µF*2	-	VCC	-	V	-
VL2 voltage*1	V_{L2}	C1 to C4 = 0.47 µF*2	2/3 × V _{L4} - 0.07	2/3 × V _{L4}	$2/3 \times V_{L4} + 0.07$	V	-
VL1 voltage*1	V _{L1}	C1 to C4 = 0.47 µF*2	1/3 × V _{L4} - 0.08	1/3 × V _{L4}	1/3 × V _{L4} + 0.08	V	-
Capacitor split wait time*1	t _{WAIT}		100	-	-	ms	Figure 2.81

Note 1. This is the wait time from when voltage bucking is started (VLCON = 1) until display is enabled (LCDON = 1).

Note 2. This is a capacitor that is connected between voltage pins used to drive the LCD.

C1: A capacitor connected between CAPH and CAPL

C2: A capacitor connected between V_{L1} and GND

C3: A capacitor connected between V_{L2} and GND

C4: A capacitor connected between V_{L4} and GND

 $C1 = C2 = C3 = C4 = 0.47 \mu F \pm 30\%$.

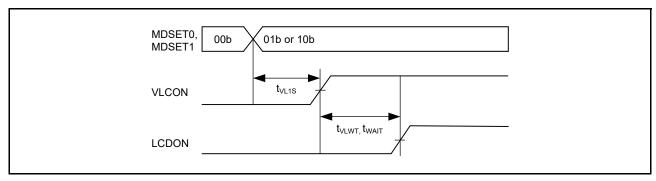


Figure 2.81 LCD reference voltage setup time, voltage boosting wait time, and capacitor split wait time

Comparator Characteristics 2.13

Table 2.67 ACMPLP characteristics

Conditions: VCC = 1.8 to 5.5 V

Parameter			Symbol	Min	Тур	Max	Unit	Test conditions
Reference voltage range	Standard mode	IVREFn (n= 0,1)	VREF	0	-	VCC-1.4	V	-
	Window	IVREF1	VREFH	1.4	-	VCC	V	-
	mode*2	IVREF0	VREFL	0	-	VCC-1.4	٧	-
Input voltage range			VI	0	-	VCC	V	-
Internal reference voltage			-	1.36	1.44	1.50	V	-
Output delay	High-speed	mode	Td	-	-	1.2	μs	VCC = 3.0
	Low-speed	mode		-	-	5	μs	Slew rate of input signal > 50 mV/µs
	Window mo	de		-	-	2	μs	oignar oo mv/µo
Offset voltage*1	High-speed	mode	-	-	-	50	mV	-
	Low-speed mode		-	-	-	40	mV	-
Window mode		-	-	-	60	mV	-	
Operation stabilization wait time		T _{cmp}	100	-	-	μs	-	

Note 1. When 8-bit DAC output is used as the reference voltage, the offset voltage increases up to $2.5 \times VCC/256$. Note 2. In window mode, be sure to satisfy the following condition: IVREF1 - IVREF0 $\geq 0.2 \text{ V}$.

2.14 OPAMP Characteristics

Table 2.68 OPAMP characteristics

Conditions: VCC = AVCC0 = 1.8 to 5.5 V (AVCC0 = VCC when VCC < 2.0 V)

Parameter	Symbol	Conditions		Min	Тур	Max	Unit
Common mode input	Vicm1	Low power mode		0.2	-	AVCC0 - 0.5	V
range	Vicm2	High-speed mode		0.3	-	AVCC0 - 0.6	V
Output voltage range	Vo1	Low power mode		0.1	-	AVCC0 - 0.1	V
	Vo2	High-speed mode		0.1	-	AVCC0 - 0.1	V
Input offset voltage	Vioff	3σ	3σ		-	10	mV
Open gain	Av			60	120	-	dB
Gain-bandwidth (GB)	GBW1	Low power mode		-	0.04	-	MHz
product	GBW2	High-speed mode		-	1.7	-	MHz
Phase margin	PM	CL = 20 pF		50	-	-	deg
Gain margin	GM	CL = 20 pF		10	-	-	dB
Equivalent input noise	Vnoise1	f = 1 kHz	Low power mode	-	230	-	nV/√Hz
	Vnoise2	f = 10 kHz		-	200	-	nV/√Hz
	Vnoise3	f = 1 kHz	High-speed mode	-	90	-	nV/√Hz
	Vnoise4	f = 2 kHz		-	70	-	nV/√Hz
Power supply reduction ratio	PSRR			-	90	-	dB
Common mode signal reduction ratio	CMRR			-	90	-	dB
Stabilization wait time	Tstd1	CL = 20 pF	Low power mode	650	-	-	μs
	Tstd2	Only operational amplifier is activated *1	High-speed mode	13	-	-	μs
	Tstd3	CL = 20 pF	Low power mode	650	-	-	μs
	Tstd4	 Operational amplifier and reference current circuit are activated simultaneously 	High-speed mode	13	-	-	μs
Settling time	Tset1	CL = 20 pF	Low power mode	-	-	750	μs
	Tset2		High-speed mode	-	-	13	μs
Slew rate	Tslew1	CL = 20 pF	Low power mode	-	0.02	-	V/µs
	Tslew2	1	High-speed mode	-	1.1	-	V/µs
Load current	lload1	Low-power mode	1	-100	-	100	μА
	lload2	High-speed mode		-100	-	100	μA
Load capacitance	CL			-	-	20	pF

Note 1. When the operational amplifier reference current circuit is activated in advance.

2.15 Flash Memory Characteristics

2.15.1 Code Flash Memory Characteristics

Table 2.69 Code flash characteristics (1)

Parameter		Symbol	Min	Тур	Max	Unit	Test conditions
Reprogramming/erasure cycle*1		N _{PEC}	1000	-	-	Times	-
Data hold time	After 1000 times of N _{PEC}	t _{DRP}	20*2, *3	-	-	Year	T _a = +85°C

Note 1. The reprogram/erase cycle is the number of erasures for each block. When the reprogram/erase cycle is n times (n = 1,000), erasing can be done n times for each block. For instance, when 8-byte programming is performed 256 times for different addresses in 2-KB blocks, and then the entire block is erased, the reprogram/erase cycle is counted as one. However, programming the same address for several times as one erasure is not enabled (overwriting is prohibited).

Note 2. Characteristic when using the flash memory programmer and the self-programming library provided by Renesas Electronics.

Note 3. This result is obtained from reliability testing.

Table 2.70 Code flash characteristics (2)

High-speed operating mode Conditions: VCC = 2.7 to 5.5 V

				FCLK = 1	MHz		FCLK = 32	MHz	
Parameter		Symbol	Min	Тур	Max	Min	Тур	Max	Unit
Programming time	8-byte	t _{P8}	-	116	998	-	54	506	μs
Erasure time	2-KB	t _{E2K}	-	9.03	287	-	5.67	222	ms
Blank check time	8-byte	t _{BC8}	-	-	56.8	-	-	16.6	μs
	2-KB	t _{BC2K}	-	-	1899	-	-	140	μs
Erase suspended time)	t _{SED}	-	-	22.5	-	-	10.7	μs
Startup area switching	setting time	t _{SAS}	-	21.7	585	-	12.1	447	ms
Access window time		t _{AWS}	-	21.7	585	-	12.1	447	ms
OCD/serial programm	er ID setting time	t _{OSIS}	-	21.7	585	-	12.1	447	ms
Flash memory mode time 1	ransition wait	t _{DIS}	2	-	-	2	-	-	μs
Flash memory mode time 2	ransition wait	t _{MS}	5	-	-	5	-	-	μs

Note: Does not include the time until each operation of the flash memory is started after instructions are executed by software.

Note: The lower-limit frequency of FCLK is 1 MHz during programming or erasing the flash memory. When using FCLK at below

4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.

Note: The frequency accuracy of FCLK must be ±3.5%. Confirm the frequency accuracy of the clock source.

Table 2.71 Code flash characteristics (3)

Middle-speed operating mode

Conditions: VCC = 1.8 to 5.5 V, T_a = -40 to +85°C

				FCLK = 1	MHz		FCLK = 8	MHz	
Parameter		Symbol	Min	Тур	Max	Min	Тур	Max	Unit
Programming time	8-byte	t _{P8}	-	157	1411	-	101	966	μs
Erasure time	2-KB	t _{E2K}	-	9.10	289	-	6.10	228	ms
Blank check time	8-byte	t _{BC8}	-	-	87.7	-	-	52.5	μs
	2-KB	t _{BC2K}	-	-	1930	-	-	414	μs
Erase suspended time	,	t _{SED}	-	-	32.7	-	-	21.6	μs
Startup area switching	setting time	t _{SAS}	-	22.5	592	-	14.0	464	ms
Access window time		t _{AWS}	-	22.5	592	-	14.0	464	ms
OCD/serial programm	er ID setting time	t _{OSIS}	-	22.5	592	-	14.0	464	ms
Flash memory mode to	ransition wait time 1	t _{DIS}	2	-	-	2	-	-	μs
Flash memory mode to	ransition wait time 2	t _{MS}	720	-	-	720	-	-	ns

Note: Does not include the time until each operation of the flash memory is started after instructions are executed by software.

Note: The lower-limit frequency of FCLK is 1 MHz during programming or erasing the flash memory. When using FCLK at below

4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.

Note: The frequency accuracy of FCLK must be ±3.5%. Confirm the frequency accuracy of the clock source.

2.15.2 Data Flash Memory Characteristics

Table 2.72 Data flash characteristics (1)

Parameter		Symbol	Min	Тур	Max	Unit	Test conditions
Reprogramming	erasure cycle*1	N _{DPEC}	100,000	1,000,000	-	Times	-
Data hold time	After 10,000 times of N _{DPEC}	t _{DDRP}	20*2, *3	-	-	Year	T _a = +85°C
	After 100,000 times of N _{DPEC}		5*2, *3	-	-	Year	
	After 1,000,000 times of N _{DPEC}		-	1*2, *3	-	Year	T _a = +25°C

Note 1. The reprogram/erase cycle is the number of erasure for each block. When the reprogram/erase cycle is n times (n = 100,000), erasing can be performed n times for each block. For instance, when 1-byte programming is performed 1,000 times for different addresses in 1-byte blocks, and then the entire block is erased, the reprogram/erase cycle is counted as one. However, programming the same address for several times as one erasure is not enabled. Overwriting is prohibited.

Note 2. Characteristics when using the flash memory programmer and the self-programming library provided by Renesas Electronics.

Note 3. These results are obtained from reliability testing.

Table 2.73 Data flash characteristics (2)

High-speed operating mode Conditions: VCC = 2.7 to 5.5 V

			FCLK = 4 MHz			FCLK = 32 MHz			
Parameter		Symbol	Min	Тур	Max	Min	Тур	Max	Unit
Programming time	1-byte	t _{DP1}	-	52.4	463	-	42.1	387	μs
Erasure time	1-KB	t _{DE1K}	-	8.98	286	-	6.42	237	ms
Blank check time	1-byte	t _{DBC1}	-	-	24.3	-	-	16.6	μs
	1-KB	t _{DBC1K}	-	-	1872	-	-	512	μs
Suspended time durin	g erasing	t _{DSED}	-	-	13.0	-	-	10.7	μs
Data flash STOP reco	very time	t _{DSTOP}	5	-	-	5	-	-	μs

Note: Does not include the time until each operation of the flash memory is started after instructions are executed by software.

Note: The lower-limit frequency of FCLK is 1 MHz during programming or erasing the flash memory. When using FCLK at below

4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.

Note: The frequency accuracy of FCLK must be ±3.5%. Confirm the frequency accuracy of the clock source.

Table 2.74 Data flash characteristics (3)

Middle-speed operating mode

Conditions: VCC = 1.8 to 5.5 V, $T_a = -40$ to +85°C

			FCLK:		MHz		FCLK = 8	MHz	
Parameter		Symbol	Min	Тур	Max	Min	Тур	Max	Unit
Programming time	1-byte	t _{DP1}	-	94.7	886	-	89.3	849	μs
Erasure time	1-KB	t _{DE1K}	-	9.59	299	-	8.29	273	ms
Blank check time	1-byte	t _{DBC1}	-	-	56.2	-	-	52.5	μs
	1-KB	t _{DBC1K}	-	-	2.17	-	-	1.51	ms
Suspended time durir	ng erasing	t _{DSED}	-	-	23.0	-	-	21.7	μs
Data flash STOP reco	overy time	t _{DSTOP}	720	-	-	720	-	-	ns

Note: Does not include the time until each operation of the flash memory is started after instructions are executed by software.

Note: The lower-limit frequency of FCLK is 1 MHz during programming or erasing the flash memory. When using FCLK at below

4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.

Note: The frequency accuracy of FCLK must be ±3.5%. Confirm the frequency accuracy of the clock source.

2.16 Boundary Scan

Table 2.75 Boundary scan

Conditions: VCC = AVCC0 = 2.4 to 5.5 V

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
TCK clock cycle time	t _{TCKcyc}	100	-	-	ns	Figure 2.82
TCK clock high pulse width	t _{TCKH}	45	-	-	ns	
TCK clock low pulse width	t _{TCKL}	45	-	-	ns	
TCK clock rise time	t _{TCKr}	-	-	5	ns	
TCK clock fall time	t _{TCKf}	-	-	5	ns	
TMS setup time	t _{TMSS}	20	-	-	ns	Figure 2.83
TMS hold time	t _{TMSH}	20	-	-	ns	
TDI setup time	t _{TDIS}	20	-	-	ns	
TDI hold time	t _{TDIH}	20	-	-	ns	
TDO data delay	t _{TDOD}	-	-	70	ns	
Boundary Scan circuit start up time*1	t _{BSSTUP}	t _{RESWP}	-	-	-	Figure 2.84

Note 1. Boundary scan does not function until power-on-reset becomes negative.

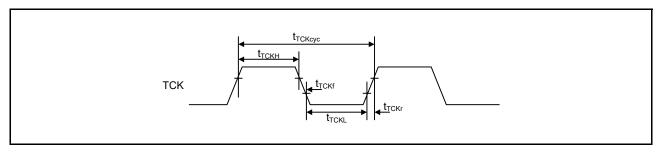


Figure 2.82 Boundary scan TCK timing

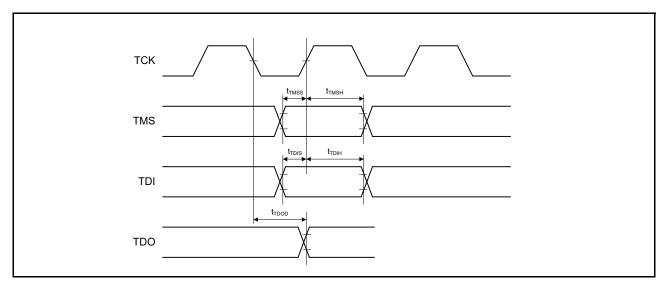


Figure 2.83 Boundary scan input/output timing

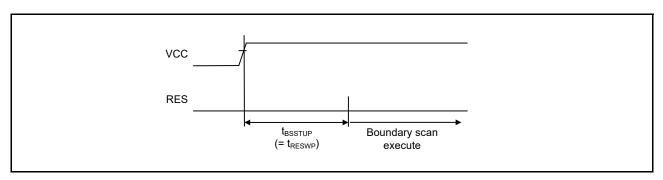


Figure 2.84 Boundary scan circuit start up timing

2.17 Joint Test Action Group (JTAG)

Table 2.76 JTAG (debug) characteristics (1)

Conditions: VCC = 2.4 to 5.5 V

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
TCK clock cycle time	t _{TCKcyc}	80	-	-	ns	Figure 2.85
TCK clock high pulse width	t _{TCKH}	35	-	-	ns	
TCK clock low pulse width	t _{TCKL}	35	-	-	ns	
TCK clock rise time	t _{TCKr}	-	-	5	ns	
TCK clock fall time	t _{TCKf}	-	-	5	ns	
TMS setup time	t _{TMSS}	16	-	-	ns	Figure 2.86
TMS hold time	t _{TMSH}	16	-	-	ns	
TDI setup time	t _{TDIS}	16	-	-	ns	
TDI hold time	t _{TDIH}	16	-	-	ns	
TDO data delay time	t _{TDOD}	-	-	70	ns	

Table 2.77 JTAG (debug) characteristics (2)

Conditions: VCC = 1.6 to 2.4 V

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
TCK clock cycle time	t _{TCKcyc}	250	-	-	ns	Figure 2.85
TCK clock high pulse width	t _{TCKH}	120	-	-	ns	
TCK clock low pulse width	t _{TCKL}	120	-	-	ns	
TCK clock rise time	t _{TCKr}	-	-	5	ns	
TCK clock fall time	t _{TCKf}	-	-	5	ns	
TMS setup time	t _{TMSS}	50	-	-	ns	Figure 2.86
TMS hold time	t _{TMSH}	50	-	-	ns	
TDI setup time	t _{TDIS}	50	-	-	ns	
TDI hold time	t _{TDIH}	50	-	-	ns	
TDO data delay time	t _{TDOD}	-	-	150	ns	

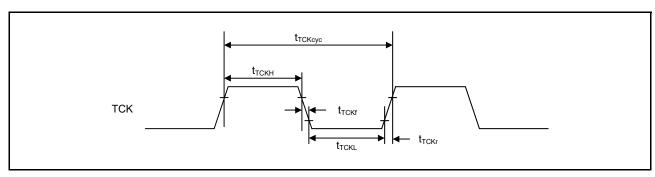


Figure 2.85 JTAG TCK timing

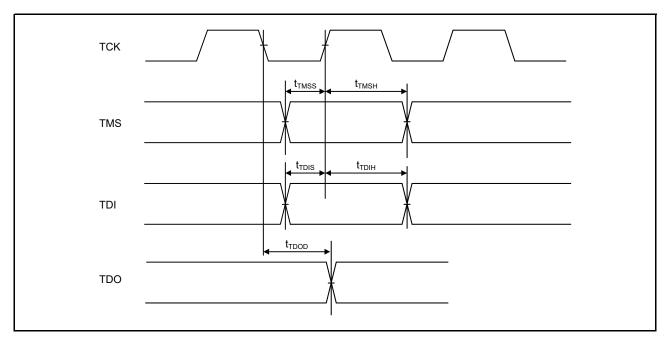


Figure 2.86 JTAG input/output timing

Serial Wire Debug (SWD) 2.17.1

Table 2.78 SWD characteristics (1) Conditions: VCC = 2.4 to 5.5 V

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
SWCLK clock cycle time	tswckcyc	80	-	-	ns	Figure 2.87
SWCLK clock high pulse width	t _{SWCKH}	35	-	-	ns	
SWCLK clock low pulse width	tswckl	35	-	-	ns	
SWCLK clock rise time	tswckr	-	-	5	ns	
SWCLK clock fall time	tswckf	-	-	5	ns	
SWDIO setup time	t _{SWDS}	16	-	-	ns	Figure 2.88
SWDIO hold time	t _{SWDH}	16	-	-	ns	
SWDIO data delay time	t _{SWDD}	2	-	70	ns	

SWD characteristics (2) **Table 2.79**

Conditions: VCC = 1.6 to 2.4 V

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
SWCLK clock cycle time	t _{SWCKcyc}	250	-	-	ns	Figure 2.87
SWCLK clock high pulse width	tswckh	120	-	-	ns	
SWCLK clock low pulse width	t _{SWCKL}	120	-	-	ns	
SWCLK clock rise time	t _{SWCKr}	-	-	5	ns	
SWCLK clock fall time	t _{SWCKf}	-	-	5	ns	
SWDIO setup time	t _{SWDS}	50	-	-	ns	Figure 2.88
SWDIO hold time	t _{SWDH}	50	-	-	ns	
SWDIO data delay time	t _{SWDD}	2	-	150	ns	

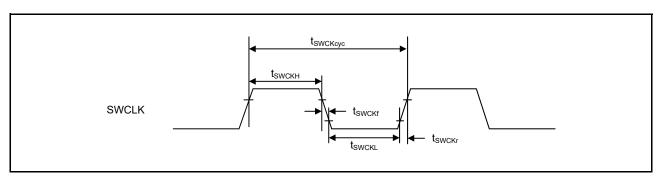


Figure 2.87 **SWD SWCLK timing**

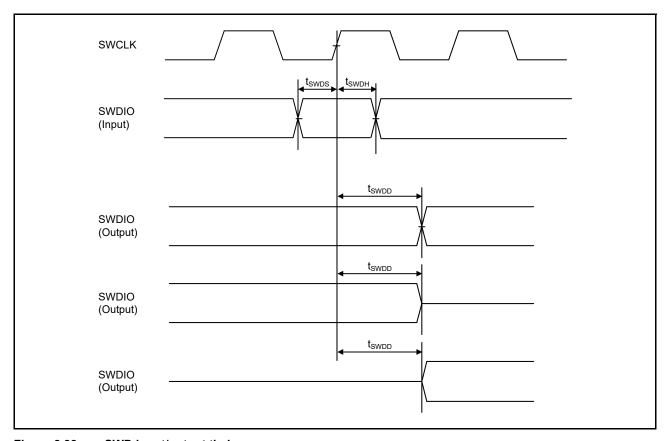


Figure 2.88 SWD input/output timing

Appendix 1.Package Dimensions

Information on the latest version of the package dimensions or mountings is shown in "Packages" on the Renesas Electronics Corporation website.

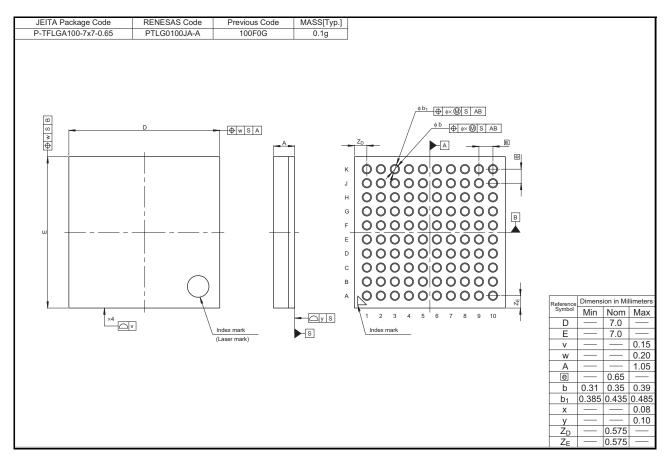


Figure 1.1 100-pin LGA

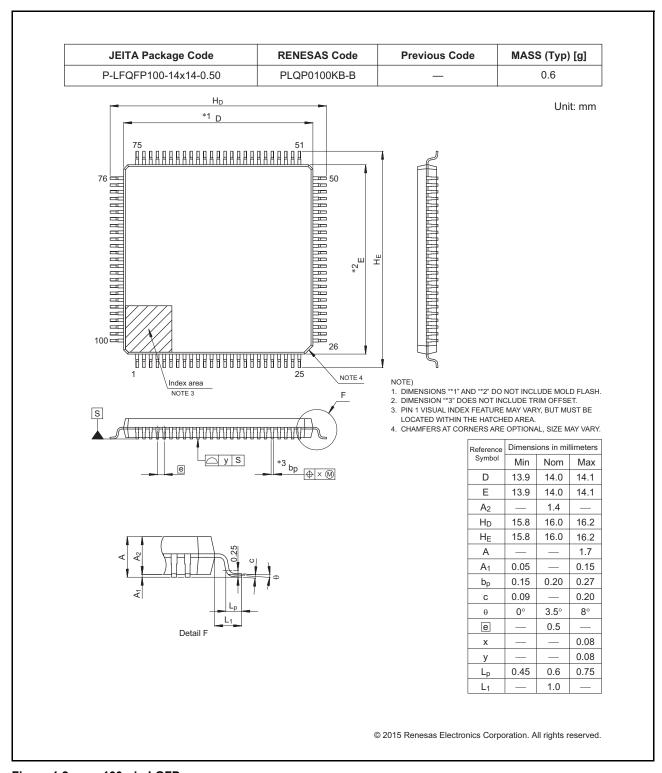


Figure 1.2 100-pin LQFP

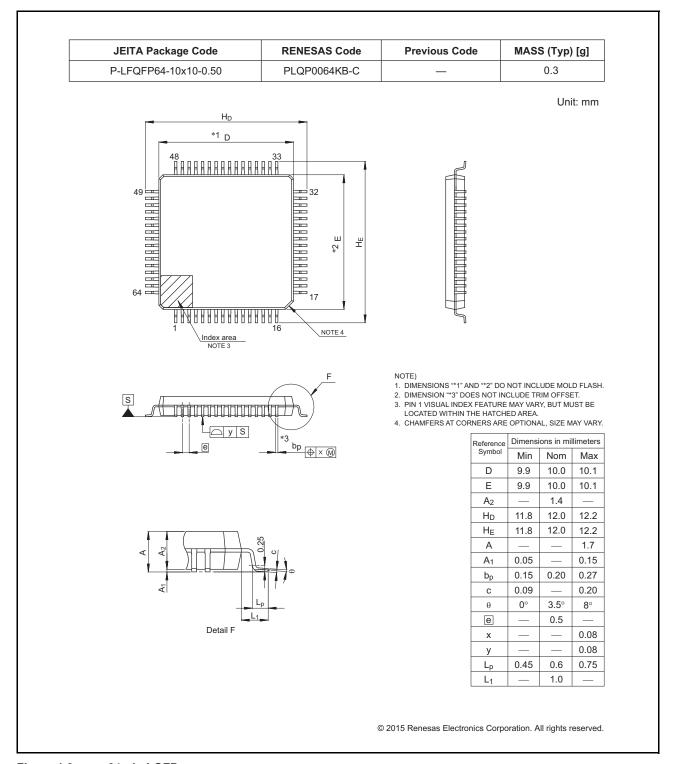


Figure 1.3 64-pin LQFP

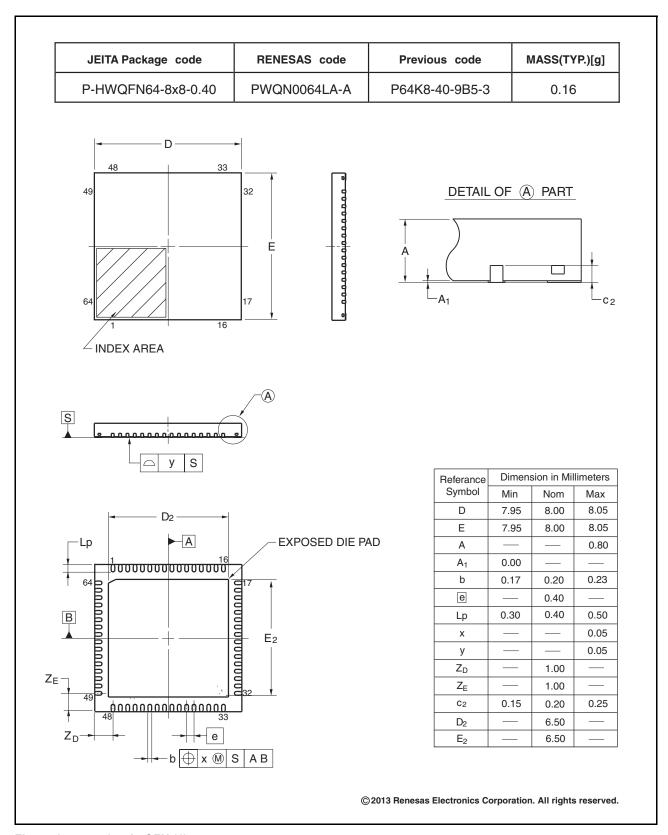


Figure 1.4 64-pin QFN (1)

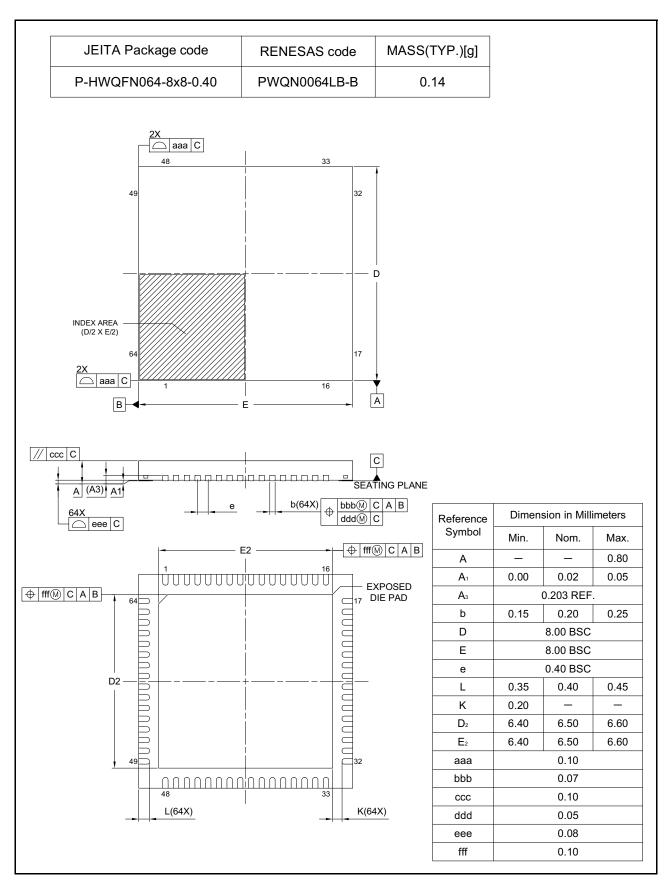


Figure 1.5 64-pin QFN (2)

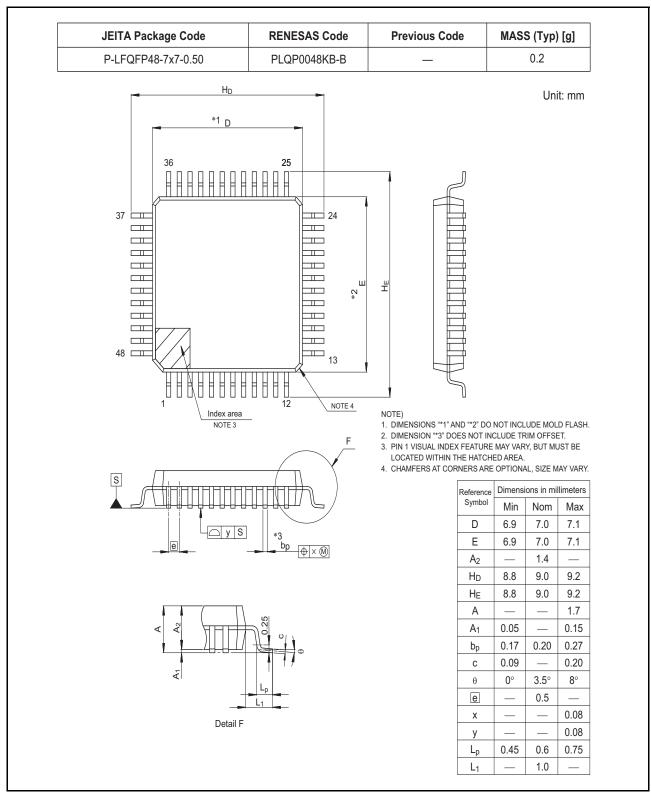


Figure 1.6 48-pin LQFP

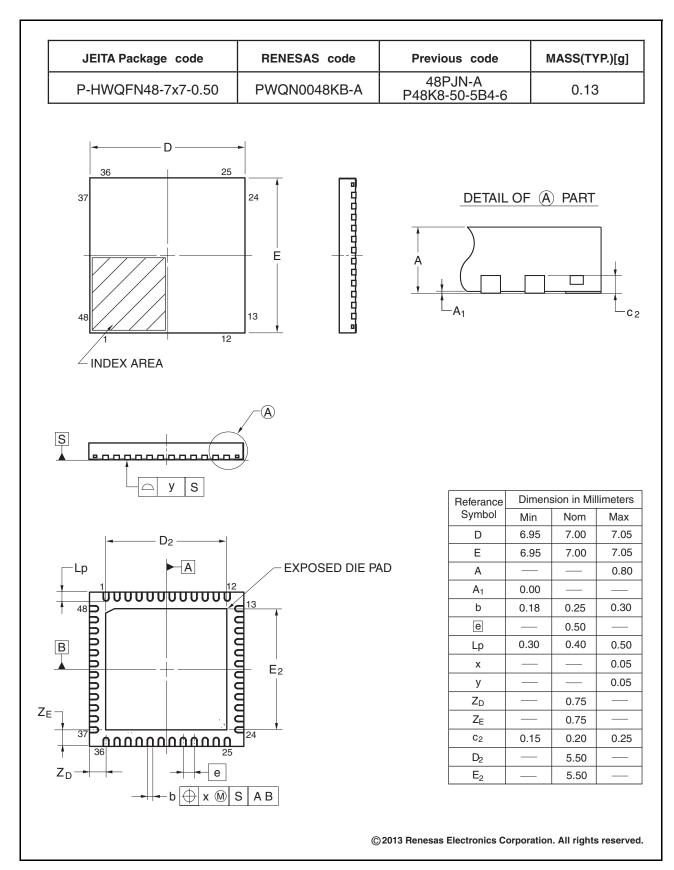


Figure 1.7 48-pin QFN (1)

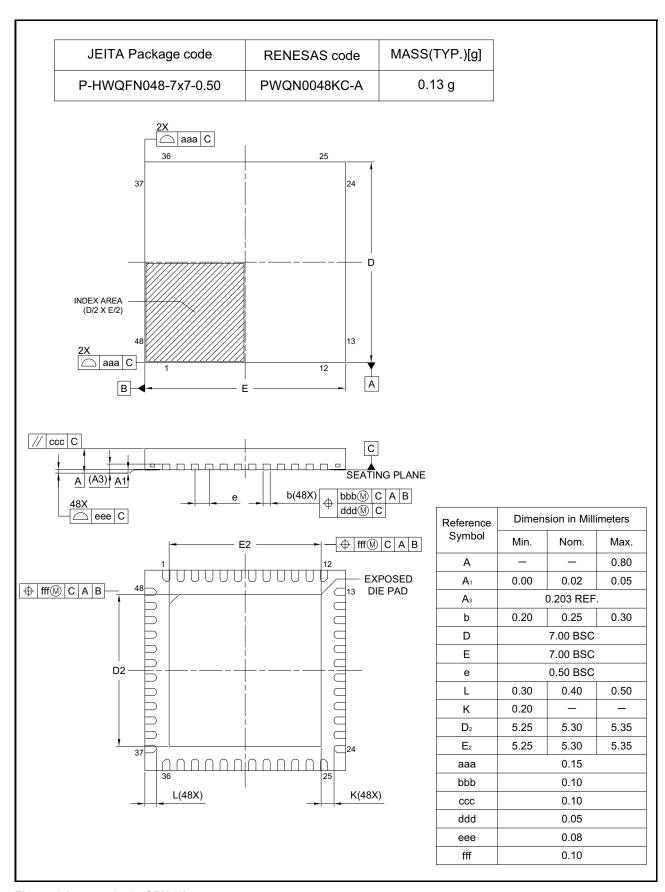


Figure 1.8 48-pin QFN (2)

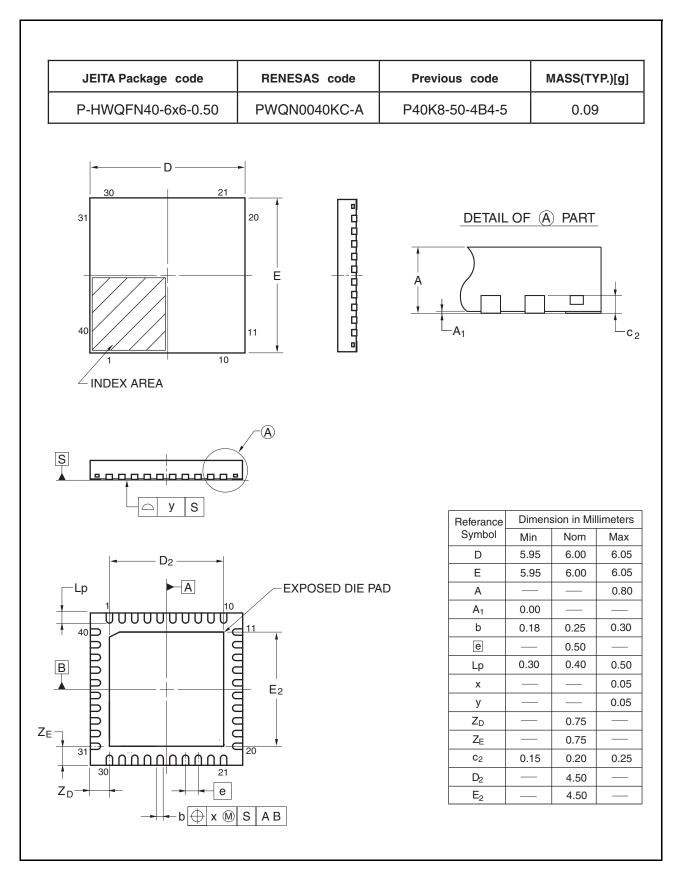


Figure 1.9 40-pin QFN (1)

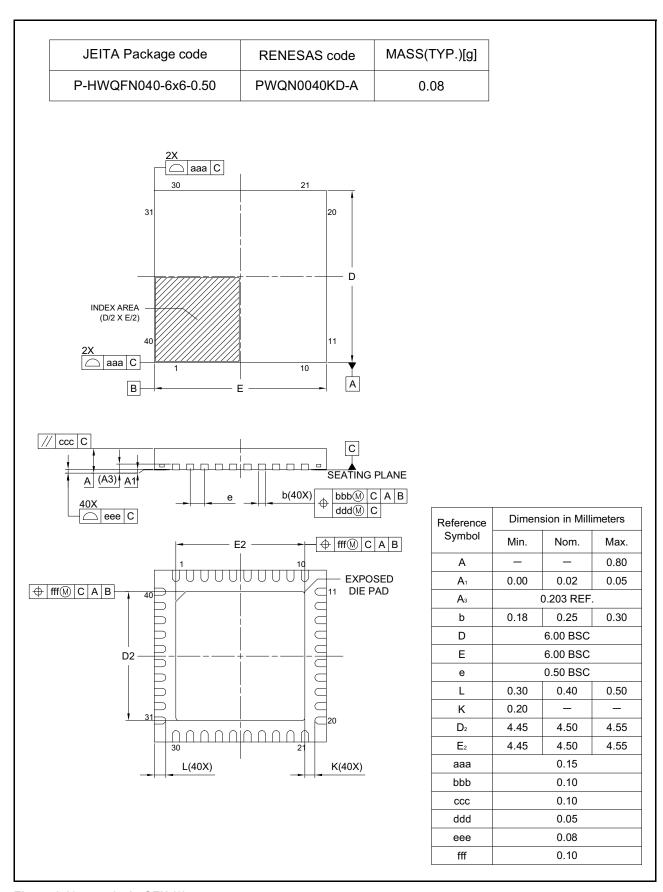


Figure 1.10 40-pin QFN (2)

RA4M1 Group Revision History

Revision History	RA4M1 Group Datasheet
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Rev.	Date	Chapter	Summary
1.00	Oct 8, 2019	_	First Edition issued
1.10	Sep 29, 2023	_	Second Edition issued

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- 1. Precaution against Electrostatic Discharge (ESD)
 - A strong electrical field, when exposed to a CMOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop the generation of static electricity as much as possible, and quickly dissipate it when it occurs. Environmental control must be adequate. When it is dry, a humidifier should be used. This is recommended to avoid using insulators that can easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors must be grounded. The operator must also be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions must be taken for printed circuit boards with mounted semiconductor devices.
- 2. Processing at power-on
 - The state of the product is undefined at the time when power is supplied. The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the time when power is supplied. In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the time when power is supplied until the reset process is completed. In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the time when power is supplied until the power reaches the level at which resetting is specified.
- 3. Input of signal during power-off state
 - Do not input signals or an I/O pull-up power supply while the device is powered off. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Follow the guideline for input signal during power-off state as described in your product documentation.
- 4. Handling of unused pins
 - Handle unused pins in accordance with the directions given under handling of unused pins in the manual. The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of the LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible.
- 5. Clock signals
 - After applying a reset, only release the reset line after the operating clock signal becomes stable. When switching the clock signal during program execution, wait until the target clock signal is stabilized. When the clock signal is generated with an external resonator or from an external oscillator during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Additionally, when switching to a clock signal produced with an external resonator or by an external oscillator while program execution is in progress, wait until the target clock signal is stable.
- 6. Voltage application waveform at input pin
 - Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between V_{IL} (Max.) and V_{IH} (Min.) due to noise, for example, the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between V_{IL} (Max.) and V_{IH} (Min.).
- 7. Prohibition of access to reserved addresses
 - Access to reserved addresses is prohibited. The reserved addresses are provided for possible future expansion of functions. Do not access these addresses as the correct operation of the LSI is not guaranteed.
- 8. Differences between products
 - Before changing from one product to another, for example to a product with a different part number, confirm that the change will not lead to problems. The characteristics of a microprocessing unit or microcontroller unit products in the same group but having a different part number might differ in terms of internal memory capacity, layout pattern, and other factors, which can affect the ranges of electrical characteristics, such as characteristic values, operating margins, immunity to noise, and amount of radiated noise. When changing to a product with a different part number, implement a system-evaluation test for the given product.

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